

**Advance Information**

DSP56364/D  
Rev. 3.2, 08/2003

24-Bit Audio Digital  
Signal Processor



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## Overview

The DSP56364 supports digital audio applications requiring sound field processing, acoustic equalization, and other digital audio algorithms. The DSP56364 uses the high performance, single-clock-per-cycle DSP56300 core family of programmable CMOS digital signal processors (DSPs) combined with the audio signal processing capability of the Motorola Symphony™ DSP family, as shown in Figure 1. This design provides a two-fold performance increase over Motorola's popular Symphony family of DSPs while retaining code compatibility. Significant architectural enhancements include a barrel shifter, 24-bit addressing, instruction cache, and direct memory access (DMA). The DSP56364 offers 100 million instructions per second (MIPS) using an internal 100 MHz clock at 3.3 V.

### Data Sheet Conventions

This data sheet uses the following conventions:

OVERBAR	Used to indicate a signal that is active when pulled low (For example, the RESET pin is active when low.)
"asserted"	Means that a high true (active high) signal is high or that a low true (active low) signal is low
"deasserted"	Means that a high true (active high) signal is low or that a low true (active low) signal is high

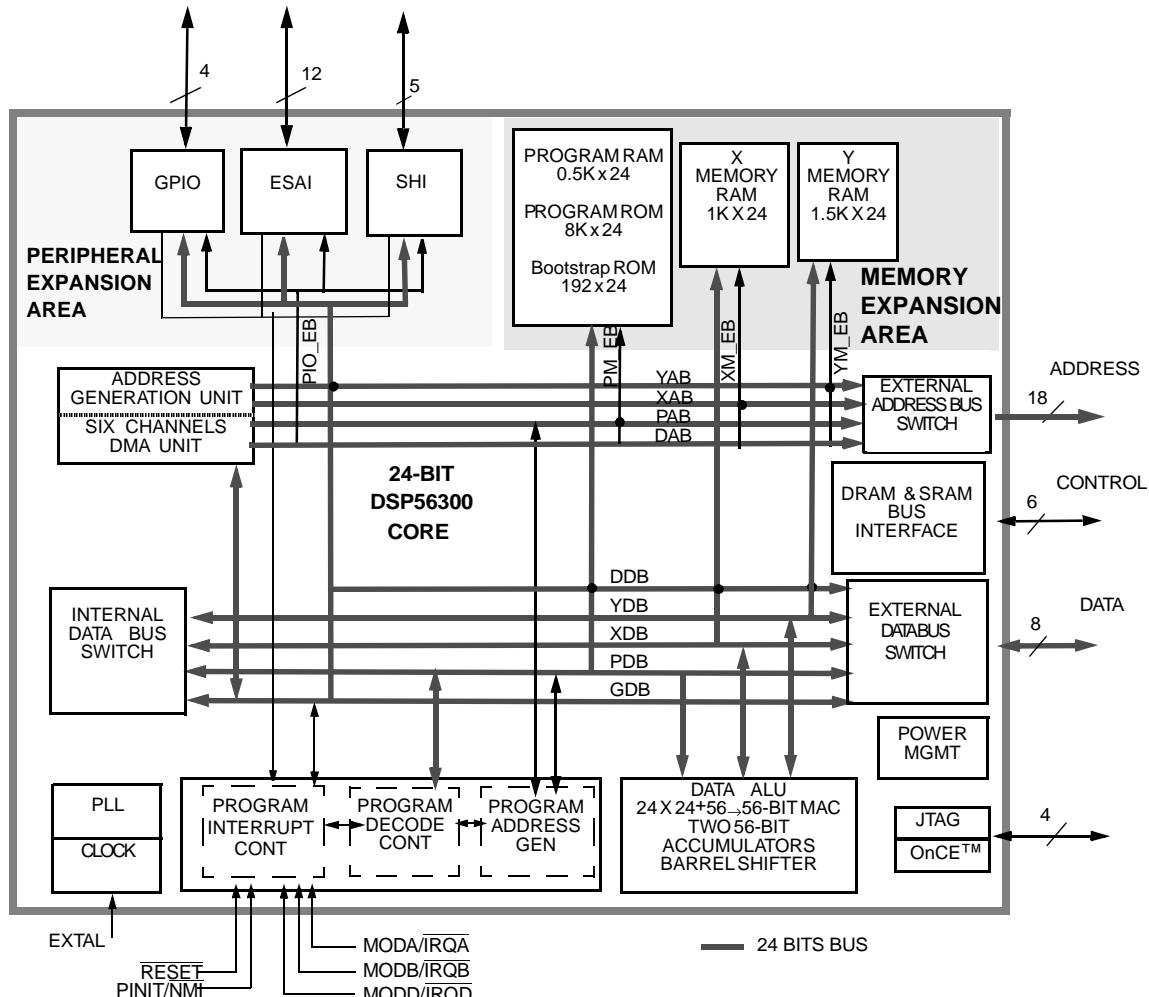
Examples:	Signal/ Symbol	Logic State	Signal State	Voltage*
	$\overline{\text{PIN}}$	True	Asserted	$V_{IL} / V_{OL}$
	$\overline{\overline{\text{PIN}}}$	False	Deasserted	$V_{IH} / V_{OH}$
	$\overline{\text{PIN}}$	True	Asserted	$V_{IH} / V_{OH}$
	$\overline{\overline{\text{PIN}}}$	False	Deasserted	$V_{IL} / V_{OL}$

Note: \*Values for  $V_{IL}$ ,  $V_{OL}$ ,  $V_{IH}$ , and  $V_{OH}$  are defined by individual product specifications.

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## Overview

### Features



**Figure 1** DSP56364 Block Diagram

## 1 Features

### 1.1 Digital Signal Processing Core

- 100 Million Instructions Per Second (MIPS) with an 100 MHz clock at 3.3V.
- Object Code Compatible with the 56000 core.
- Data ALU with a 24 x 24 bit multiplier-accumulator and a 56-bit barrel shifter. 16-bit arithmetic support.
- Program Control with position independent code support and instruction cache support.
- Six-channel DMA controller.
- PLL based clocking with a wide range of frequency multiplications (1 to 4096), predivider factors (1 to 16) and power saving clock divider ( $2^i$ :  $i=0$  to 7). Reduces clock noise.
- Internal address tracing support and OnCE™ for Hardware/Software debugging.

- JTAG port.
- Very low-power CMOS design, fully static design with operating frequencies down to DC.
- STOP and WAIT low-power standby modes.

## **1.2 On-chip Memory Configuration**

- 1.5Kx24 Bit Y-Data RAM.
- 1Kx24 Bit X-Data RAM.
- 8Kx24 Bit Program ROM.
- 0.5Kx24 Bit Program RAM and 192x24 Bit Bootstrap ROM.
- 0.75Kx24 Bit from Y Data RAM can be switched to Program RAM resulting in up to 1.25Kx24 Bit of Program RAM.

## **1.3 Off-chip memory expansion**

- External Memory Expansion Port with 8-bit data bus.
- Off-chip expansion up to 2 x 16M x 8-bit word of Data/Program memory when using DRAM.
- Off-chip expansion up to 2 x 256k x 8-bit word of Data/Program memory when using SRAM.
- Simultaneous glueless interface to SRAM and DRAM.

## **1.4 Peripheral modules**

- Enhanced Serial Audio Interface (ESAI): 6 serial lines, 4 selectable as receive or transmitt and 2 transmitt only, master or slave. I<sup>2</sup>S, Sony, AC97, network and other programmable protocols. Unused pins of ESAI may be used as GPIO lines.
- Serial Host Interface (SHI): SPI and I<sup>2</sup>C protocols, 10-word receive FIFO, support for 8, 16 and 24-bit words.
- Four dedicated GPIO lines.

## **1.5 Packaging**

- 100-pin plastic TQFP package.

## **2 Documentation**

Table 1 lists the documents that provide a complete description of the DSP56364 and are required to design properly with the part. Documentation is available from a local Motorola distributor, a Motorola semiconductor sales office, a Motorola Literature Distribution Center, or through the Motorola DSP home page on the Internet (the source for the latest information).

**Freescale Semiconductor, Inc.****Overview****Documentation****Table 1 DSP56364 Documentation**

Document Name	Description	Order Number
DSP56300 Family Manual	Detailed description of the 56000-family architecture and the 24-bit core processor and instruction set	DSP56300FM/AD
DSP56364 User's Manual	Detailed description of memory, peripherals, and interfaces	DSP56364UM/AD
DSP56364 Technical Data Sheet	Electrical and timing specifications; pin and package descriptions	DSP56364/D
There is also a product brief for this chip.		
DSP56364 Product Brief	Brief description of the chip	DSP56364P/D

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## SECTION 1

### SIGNAL/CONNECTION DESCRIPTIONS

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#### 1.1 SIGNAL GROUPINGS

The input and output signals of the DSP56364 are organized into functional groups, which are listed in Table 1-1 and illustrated in Figure 1-1.

The DSP56364 is operated from a 3.3 V supply; however, some of the inputs can tolerate 5 V. A special notice for this feature is added to the signal descriptions of those inputs.

**Table 1-1 DSP56364 Functional Signal Groupings**

Functional Group	Number of Signals	Detailed Description	
Power ( $V_{CC}$ )	18	Table 1-2	
Ground (GND)	14	Table 1-3	
Clock and PLL	3	Table 1-4	
Address bus	Port A <sup>1</sup>	18	Table 1-5
Data bus		8	Table 1-6
Bus control		6	Table 1-7
Interrupt and mode control	4	Table 1-8	
General Purpose I/O	Port B2	4	Table 1-12
SHI		5	Table 1-9
ESAI	Port C3	12	Table 1-10
JTAG/OnCE Port		4	Table 1-11
Notes:			
1. Port A is the external memory interface port, including the external address bus, data bus, and control signals.			
2. Port B signals are the GPIO signals.			
3. Port C signals are the ESAI port signals multiplexed with the GPIO signals.			

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## Signal/Connection Descriptions

### Signal Groupings

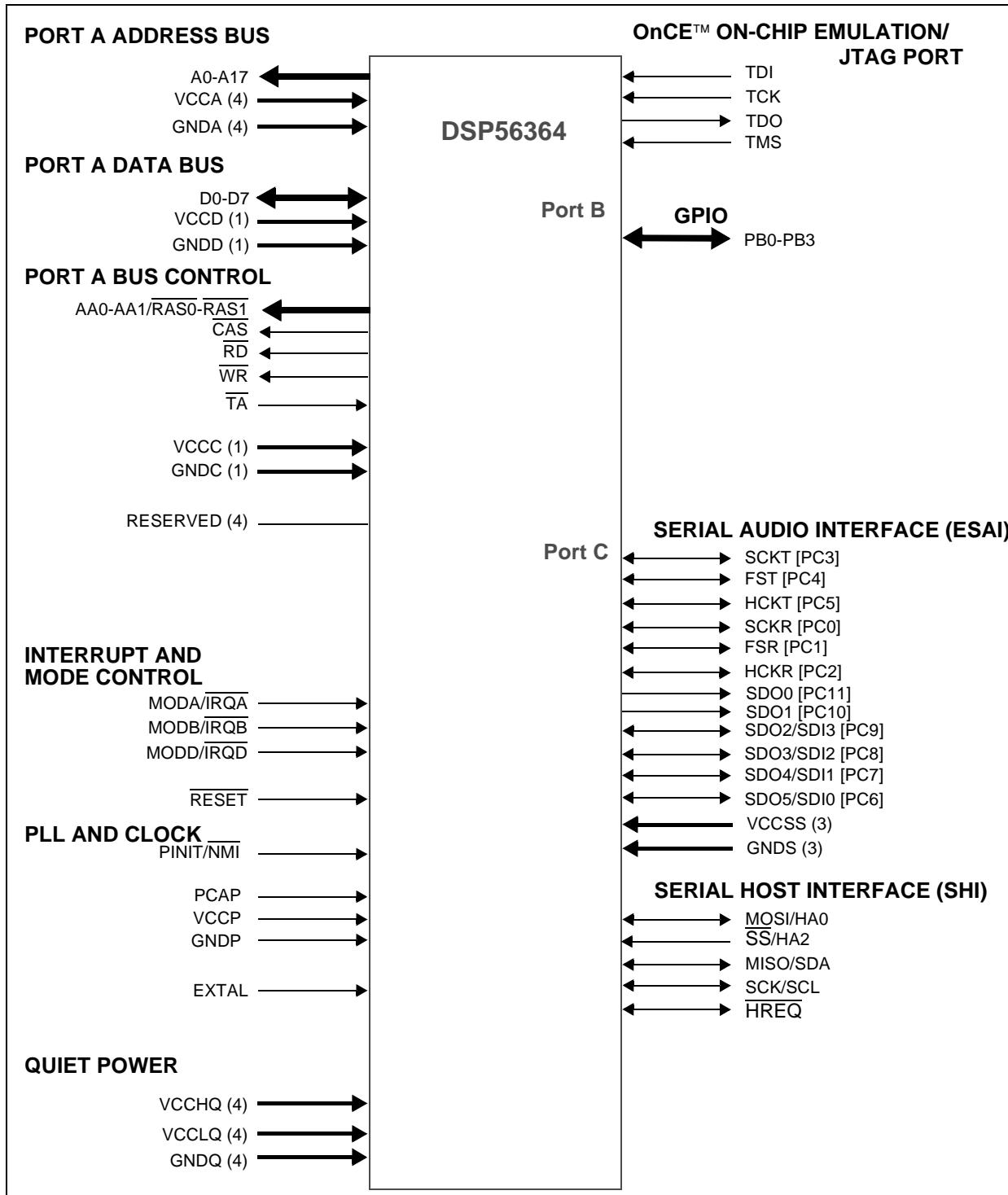


Figure 1-1 Signals Identified by Functional Group

## 1.2 POWER

**Table 1-2 Power Inputs**

Power Name	Description
$V_{CCP}$	<b>PLL Power</b> — $V_{CCP}$ is $V_{CC}$ dedicated for PLL use. The voltage should be well-regulated and the input should be provided with an extremely low impedance path to the $V_{CC}$ power rail. There is one $V_{CCP}$ input.
$V_{CCQL}$ (4)	<b>Quiet Core (Low) Power</b> — $V_{CCQL}$ is an isolated power for the internal processing logic. This input must be tied externally to all other chip power inputs. The user must provide adequate external decoupling capacitors. There are four $V_{CCQL}$ inputs.
$V_{CCQH}$ (4)	<b>Quiet External (High) Power</b> — $V_{CCQH}$ is a quiet power source for I/O lines. This input must be tied externally to all other chip power inputs. The user must provide adequate decoupling capacitors. There are four $V_{CCQH}$ inputs.
$V_{CCA}$ (4)	<b>Address Bus Power</b> — $V_{CCA}$ is an isolated power for sections of the address bus I/O drivers. This input must be tied externally to all other chip power inputs. The user must provide adequate external decoupling capacitors. There are four $V_{CCA}$ inputs.
$V_{CCD}$ (1)	<b>Data Bus Power</b> — $V_{CCD}$ is an isolated power for sections of the data bus I/O drivers. This input must be tied externally to all other chip power inputs. The user must provide adequate external decoupling capacitors. There is one $V_{CCD}$ inputs.
$V_{CCC}$ (1)	<b>Bus Control Power</b> — $V_{CCC}$ is an isolated power for the bus control I/O drivers. This input must be tied externally to all other chip power inputs. The user must provide adequate external decoupling capacitors. There is one $V_{CCC}$ inputs.
$V_{CCS}$ (3)	<b>SHI and ESAI</b> — $V_{CCS}$ is an isolated power for the SHI and ESAI. This input must be tied externally to all other chip power inputs. The user must provide adequate external decoupling capacitors. There are three $V_{CCS}$ inputs.

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## Signal/Connection Descriptions

### Ground

## 1.3 GROUND

**Table 1-3 Grounds**

Ground Name	Description
GND <sub>P</sub>	<b>PLL Ground</b> —GND <sub>P</sub> is ground-dedicated for PLL use. The connection should be provided with an extremely low-impedance path to ground. V <sub>CCP</sub> should be bypassed to GND <sub>P</sub> by a 0.47 $\mu$ F capacitor located as close as possible to the chip package. There is one GND <sub>P</sub> connection.
GND <sub>Q</sub> (4)	<b>Quiet Ground</b> —GND <sub>Q</sub> is an isolated ground for the internal processing logic. This connection must be tied externally to all other chip ground connections. The user must provide adequate external decoupling capacitors. There are four GND <sub>Q</sub> connections.
GND <sub>A</sub> (4)	<b>Address Bus Ground</b> —GND <sub>A</sub> is an isolated ground for sections of the address bus I/O drivers. This connection must be tied externally to all other chip ground connections. The user must provide adequate external decoupling capacitors. There are four GND <sub>A</sub> connections.
GND <sub>D</sub> (1)	<b>Data Bus Ground</b> —GND <sub>D</sub> is an isolated ground for sections of the data bus I/O drivers. This connection must be tied externally to all other chip ground connections. The user must provide adequate external decoupling capacitors. There is one GND <sub>D</sub> connections.
GND <sub>C</sub> (1)	<b>Bus Control Ground</b> —GND <sub>C</sub> is an isolated ground for the bus control I/O drivers. This connection must be tied externally to all other chip ground connections. The user must provide adequate external decoupling capacitors. There is one GND <sub>C</sub> connections.
GND <sub>S</sub> (3)	<b>SHI and ESAI</b> —GND <sub>S</sub> is an isolated ground for the SHI and ESAI. This connection must be tied externally to all other chip ground connections. The user must provide adequate external decoupling capacitors. There are three GND <sub>S</sub> connections.

## 1.4 CLOCK AND PLL

**Table 1-4 Clock and PLL Signals**

Signal Name	Type	State during Reset	Signal Description
EXTAL	Input	Input	<b>External Clock Input</b> —An external clock source must be connected to EXTAL in order to supply the clock to the internal clock generator and PLL.
PCAP	Input	Input	<b>PLL Capacitor</b> —PCAP is an input connecting an off-chip capacitor to the PLL filter. Connect one capacitor terminal to PCAP and the other terminal to V <sub>CCP</sub> . If the PLL is not used, PCAP may be tied to V <sub>CC</sub> , GND, or left floating.
PINIT/NMI	Input	Input	<b>PLL Initial/Nonmaskable Interrupt</b> —During assertion of RESET, the value of PINIT/NMI is written into the PLL Enable (PEN) bit of the PLL control register, determining whether the PLL is enabled or disabled. After RESET de assertion and during normal instruction processing, the PINIT/NMI Schmitt-trigger input is a negative-edge-triggered nonmaskable interrupt (NMI) request internally synchronized to internal system clock. <i>This input is 5 V tolerant.</i>

# Freescale Semiconductor, Inc.

## Signal/Connection Descriptions

### External Memory Expansion Port (Port A)

## 1.5 EXTERNAL MEMORY EXPANSION PORT (PORT A)

When the DSP56364 enters a low-power standby mode (stop or wait), it tri-states the relevant port A signals: D0–D7, AA0, AA1, RD, WR, CAS.

### 1.5.1 External Address Bus

**Table 1-5 External Address Bus Signals**

Signal Name	Type	State during Reset	Signal Description
A0–A17	Output	Keeper active	<b>Address Bus</b> —A0–A17 are active-high outputs that specify the address for external program and data memory accesses. Otherwise, the signals are kept to their previous values by internal weak keepers. To minimize power dissipation, A0–A17 do not change state when external memory spaces are not being accessed.

### 1.5.2 External Data Bus

**Table 1-6 External Data Bus Signals**

Signal Name	Type	State during Reset	Signal Description
D0–D7	Input/Output	Tri-stated	<b>Data Bus</b> —D0–D7 are active-high, bidirectional input/outputs that provide the bidirectional data bus for external program and data memory accesses. D0–D7 are tri-stated during hardware reset and when the DSP is in the stop or wait low-power standby mode.

**Freescale Semiconductor, Inc.**  
**Signal/Connection Descriptions**

**External Memory Expansion Port (Port A)**

### 1.5.3 External Bus Control

**Table 1-7 External Bus Control Signals**

Signal Name	Type	State during Reset	Signal Description
AA0-AA1/ RAS0-RAS1	Output	Tri-stated	<b>Address Attribute or Row Address Strobe</b> —When defined as AA, these signals can be used as chip selects or additional address lines. When defined as RAS, these signals can be used as RAS for DRAM interface. These signals are tri-statable outputs with programmable polarity. These signals are tri-stated during hardware reset and when the DSP is in the stop or wait low-power standby mode.
CAS	Output	Tri-stated	<b>Column Address Strobe</b> —CAS is an active-low output used by DRAM to strobe the column address. This signal is tri-stated during hardware reset and when the DSP is in the stop or wait low-power standby mode.
RD	Output	Tri-stated	<b>Read Enable</b> —RD is an active-low output that is asserted to read external memory on the data bus. This signal is tri-stated during hardware reset and when the DSP is in the stop or wait low-power standby mode.
WR	Output	Tri-stated	<b>Write Enable</b> —WR is an active-low output that is asserted to write external memory on the data bus. This signal is tri-stated during hardware reset and when the DSP is in the stop or wait low-power standby mode.
TA	Input	Ignored Input	<p><b>Transfer Acknowledge</b>—If there is no external bus activity, the TA input is ignored. The TA input is a data transfer acknowledge (DTACK) function that can extend an external bus cycle indefinitely. Any number of wait states (1, 2, . . . infinity) may be added to the wait states inserted by the BCR by keeping TA deasserted. In typical operation, TA is deasserted at the start of a bus cycle, is asserted to enable completion of the bus cycle, and is deasserted before the next bus cycle. The current bus cycle completes one clock period after TA is asserted synchronous to the internal system clock. The number of wait states is determined by the TA input or by the bus control register (BCR), whichever is longer. The BCR can be used to set the minimum number of wait states in external bus cycles.</p> <p>In order to use the TA functionality, the BCR must be programmed to at least one wait state. A zero wait state access cannot be extended by TA deassertion, otherwise improper operation may result. TA can operate synchronously or asynchronously, depending on the setting of the TAS bit in the operating mode register (OMR).</p> <p>TA functionality may not be used while performing DRAM type accesses, otherwise improper operation may result.</p>

# Freescale Semiconductor, Inc.

## Signal/Connection Descriptions

### Interrupt and Mode Control

## 1.6 INTERRUPT AND MODE CONTROL

The interrupt and mode control signals select the chip's operating mode as it comes out of hardware reset. After RESET is deasserted, these inputs are hardware interrupt request lines.

**Table 1-8 Interrupt and Mode Control**

Signal Name	Type	State during Reset	Signal Description
MODA/IRQA	Input	Input	<p><b>Mode Select A/External Interrupt Request A</b>—MODA/IRQA is an active-low Schmitt-trigger input, internally synchronized to the internal system clock. MODA/IRQA selects the initial chip operating mode during hardware reset and becomes a level-sensitive or negative-edge-triggered, maskable interrupt request input during normal instruction processing. MODA, MODB, and MODD select one of 8 initial chip operating modes, latched into the OMR when the RESET signal is deasserted. If IRQA is asserted synchronous to the internal system clock, multiple processors can be re synchronized using the WAIT instruction and asserting IRQA to exit the wait state. If the processor is in the stop standby state and IRQA is asserted, the processor will exit the stop state.</p> <p><i>This input is 5 V tolerant.</i></p>
MODB/IRQB	Input	Input	<p><b>Mode Select B/External Interrupt Request B</b>—MODB/IRQB is an active-low Schmitt-trigger input, internally synchronized to the internal system clock. MODB/IRQB selects the initial chip operating mode during hardware reset and becomes a level-sensitive or negative-edge-triggered, maskable interrupt request input during normal instruction processing. MODA, MODB, and MODD select one of 8 initial chip operating modes, latched into OMR when the RESET signal is deasserted. If IRQB is asserted synchronous to the internal system clock, multiple processors can be re-synchronized using the WAIT instruction and asserting IRQB to exit the wait state.</p> <p><i>This input is 5 V tolerant.</i></p>
MODD/IRQD	Input	Input	<p><b>Mode Select D/External Interrupt Request D</b>—MODD/IRQD is an active-low Schmitt-trigger input, internally synchronized to the internal system clock. MODD/IRQD selects the initial chip operating mode during hardware reset and becomes a level-sensitive or negative-edge-triggered, maskable interrupt request input during normal instruction processing. MODA, MODB, and MODD select one of 8 initial chip operating modes, latched into OMR when the RESET signal is deasserted. If IRQD is asserted synchronous to the internal system clock, multiple processors can be re synchronized using the WAIT instruction and asserting IRQD to exit the wait state.</p> <p><i>This input is 5 V tolerant.</i></p>
RESET	Input	Input	<p><b>Reset</b>—RESET is an active-low, Schmitt-trigger input. When asserted, the chip is placed in the reset state and the internal phase generator is reset. The Schmitt-trigger input allows a slowly rising input (such as a capacitor charging) to reset the chip reliably. When the RESET signal is deasserted, the initial chip operating mode is latched from the MODA, MODB, and MODD inputs. The RESET signal must be asserted during power up. A stable EXTAL signal must be supplied before deassertion of RESET.</p> <p><i>This input is 5 V tolerant.</i></p>

## 1.7 SERIAL HOST INTERFACE

The SHI has five I/O signals that can be configured to allow the SHI to operate in either SPI or I<sup>2</sup>C mode.

**Table 1-9 Serial Host Interface Signals**

Signal Name	Signal Type	State during Reset	Signal Description
SCK	Input or output	Tri-stated	<b>SPI Serial Clock</b> —The SCK signal is an output when the SPI is configured as a master and a Schmitt-trigger input when the SPI is configured as a slave. When the SPI is configured as a master, the SCK signal is derived from the internal SHI clock generator. When the SPI is configured as a slave, the SCK signal is an input, and the clock signal from the external master synchronizes the data transfer. The SCK signal is ignored by the SPI if it is defined as a slave and the slave select (SS) signal is not asserted. In both the master and slave SPI devices, data is shifted on one edge of the SCK signal and is sampled on the opposite edge where data is stable. Edge polarity is determined by the SPI transfer protocol.
SCL	Input or output	Tri-stated	<b>I<sup>2</sup>C Serial Clock</b> —SCL carries the clock for I <sup>2</sup> C bus transactions in the I <sup>2</sup> C mode. SCL is a Schmitt-trigger input when configured as a slave and an open-drain output when configured as a master. SCL should be connected to V <sub>CC</sub> through a pull-up resistor.  This signal is tri-stated during hardware, software, and individual reset. Thus, there is no need for an external pull-up in this state.  This input is 5 V tolerant.
MISO	Input or output	Tri-stated	<b>SPI Master-In-Slave-Out</b> —When the SPI is configured as a master, MISO is the master data input line. The MISO signal is used in conjunction with the MOSI signal for transmitting and receiving serial data. This signal is a Schmitt-trigger input when configured for the SPI Master mode, an output when configured for the SPI Slave mode, and tri-stated if configured for the SPI Slave mode when SS is deasserted. An external pull-up resistor is not required for SPI operation.
SDA	Input or open-drain output	Tri-stated	<b>I<sup>2</sup>C Data and Acknowledge</b> —In I <sup>2</sup> C mode, SDA is a Schmitt-trigger input when receiving and an open-drain output when transmitting. SDA should be connected to V <sub>CC</sub> through a pull-up resistor. SDA carries the data for I <sup>2</sup> C transactions. The data in SDA must be stable during the high period of SCL. The data in SDA is only allowed to change when SCL is low. When the bus is free, SDA is high. The SDA line is only allowed to change during the time SCL is high in the case of start and stop events. A high-to-low transition of the SDA line while SCL is high is a unique situation, and is defined as the start event. A low-to-high transition of SDA while SCL is high is a unique situation defined as the stop event.  This signal is tri-stated during hardware, software, and individual reset. Thus, there is no need for an external pull-up in this state.  This input is 5 V tolerant.

# Freescale Semiconductor, Inc.

## Signal/Connection Descriptions

### Serial Host Interface

**Table 1-9 Serial Host Interface Signals (continued)**

Signal Name	Signal Type	State during Reset	Signal Description
MOSI	Input or output	Tri-stated	<b>SPI Master-Out-Slave-In</b> —When the SPI is configured as a master, MOSI is the master data output line. The MOSI signal is used in conjunction with the MISO signal for transmitting and receiving serial data. MOSI is the slave data input line when the SPI is configured as a slave. This signal is a Schmitt-trigger input when configured for the SPI Slave mode.
HA0	Input	Tri-stated	<b>I<sup>2</sup>C Slave Address 0</b> —This signal uses a Schmitt-trigger input when configured for the I <sup>2</sup> C mode. When configured for I <sup>2</sup> C slave mode, the HA0 signal is used to form the slave device address. HA0 is ignored when configured for the I <sup>2</sup> C master mode.  This signal is tri-stated during hardware, software, and individual reset. Thus, there is no need for an external pull-up in this state.  <i>This input is 5 V tolerant.</i>
SS	Input	Input	<b>SPI Slave Select</b> —This signal is an active low Schmitt-trigger input when configured for the SPI mode. When configured for the SPI Slave mode, this signal is used to enable the SPI slave for transfer. When configured for the SPI master mode, this signal should be kept deasserted (pulled high). If it is asserted while configured as SPI master, a bus error condition is flagged. If SS is deasserted, the SHI ignores SCK clocks and keeps the MISO output signal in the high-impedance state.
HA2	Input	Input	<b>I<sup>2</sup>C Slave Address 2</b> —This signal uses a Schmitt-trigger input when configured for the I <sup>2</sup> C mode. When configured for the I <sup>2</sup> C Slave mode, the HA2 signal is used to form the slave device address. HA2 is ignored in the I <sup>2</sup> C master mode.  This signal is tri-stated during hardware, software, and individual reset. Thus, there is no need for an external pull-up in this state.  <i>This input is 5 V tolerant.</i>
HREQ	Input or Output	Tri-stated	<b>Host Request</b> —This signal is an active low Schmitt-trigger input when configured for the master mode but an active low output when configured for the slave mode.  When configured for the slave mode, HREQ is asserted to indicate that the SHI is ready for the next data word transfer and deasserted at the first clock pulse of the new data word transfer. When configured for the master mode, HREQ is an input. When asserted by the external slave device, it will trigger the start of the data word transfer by the master. After finishing the data word transfer, the master will await the next assertion of HREQ to proceed to the next transfer.  This signal is tri-stated during hardware, software, personal reset, or when the HREQ1–HREQ0 bits in the HCSR are cleared. There is no need for external pull-up in this state.  <i>This input is 5 V tolerant.</i>

## 1.8 ENHANCED SERIAL AUDIO INTERFACE

**Table 1-10 Enhanced Serial Audio Interface Signals**

Signal Name	Signal Type	State during Reset	Signal Description
HCKR	Input or output	GPIO disconnected	<b>High Frequency Clock for Receiver</b> —When programmed as an input, this signal provides a high frequency clock source for the ESAI receiver as an alternate to the DSP core clock. When programmed as an output, this signal can serve as a high-frequency sample clock (e.g., for external digital to analog converters [DACs]) or as an additional system clock.
PC2	Input, output, or disconnected	GPIO disconnected	<b>Port C 2</b> —When the ESAI is configured as GPIO, this signal is individually programmable as input, output, or internally disconnected. The default state after reset is GPIO disconnected. <i>This input is 5 V tolerant.</i>
HCKT	Input or output	GPIO disconnected	<b>High Frequency Clock for Transmitter</b> —When programmed as an input, this signal provides a high frequency clock source for the ESAI transmitter as an alternate to the DSP core clock. When programmed as an output, this signal can serve as a high frequency sample clock (e.g., for external DACs) or as an additional system clock.
PC5	Input, output, or disconnected	GPIO disconnected	<b>Port C 5</b> —When the ESAI is configured as GPIO, this signal is individually programmable as input, output, or internally disconnected. The default state after reset is GPIO disconnected. This input is 5 V tolerant.
FSR	Input or output	GPIO disconnected	<b>Frame Sync for Receiver</b> —This is the receiver frame sync input/output signal. In the asynchronous mode (SYN=0), the FSR pin operates as the frame sync input or output used by all the enabled receivers. In the synchronous mode (SYN=1), it operates as either the serial flag 1 pin (TEBE=0), or as the transmitter external buffer enable control (TEBE=1, RFSD=1).  When this pin is configured as serial flag pin, its direction is determined by the RFSD bit in the RCCR register. When configured as the output flag OF1, this pin will reflect the value of the OF1 bit in the SAICR register, and the data in the OF1 bit will show up at the pin synchronized to the frame sync in normal mode or the slot in network mode. When configured as the input flag IF1, the data value at the pin will be stored in the IF1 bit in the SAISR register, synchronized by the frame sync in normal mode or the slot in network mode.
PC1	Input, output, or disconnected	GPIO disconnected	<b>Port C 1</b> —When the ESAI is configured as GPIO, this signal is individually programmable as input, output, or internally disconnected. The default state after reset is GPIO disconnected. This input is 5 V tolerant.

# Freescale Semiconductor, Inc.

## Signal/Connection Descriptions

### Enhanced Serial Audio Interface

**Table 1-10 Enhanced Serial Audio Interface Signals (continued)**

Signal Name	Signal Type	State during Reset	Signal Description
FST	Input or output	GPIO disconnected	<b>Frame Sync for Transmitter</b> —This is the transmitter frame sync input/output signal. For synchronous mode, this signal is the frame sync for both transmitters and receivers. For asynchronous mode, FST is the frame sync for the transmitters only. The direction is determined by the transmitter frame sync direction (TFSD) bit in the ESAI transmit clock control register (TCCR).
PC4	Input, output, or disconnected	GPIO disconnected	<b>Port C 4</b> —When the ESAI is configured as GPIO, this signal is individually programmable as input, output, or internally disconnected. The default state after reset is GPIO disconnected. This input is 5 V tolerant.
SCKR	Input or output	GPIO disconnected	<b>Receiver Serial Clock</b> —SCKR provides the receiver serial bit clock for the ESAI. The SCKR operates as a clock input or output used by all the enabled receivers in the asynchronous mode (SYN=0), or as serial flag 0 pin in the synchronous mode (SYN=1). When this pin is configured as serial flag pin, its direction is determined by the RCKD bit in the RCCR register. When configured as the output flag OF0, this pin will reflect the value of the OF0 bit in the SAICR register, and the data in the OF0 bit will show up at the pin synchronized to the frame sync in normal mode or the slot in network mode. When configured as the input flag IF0, the data value at the pin will be stored in the IF0 bit in the SAISR register, synchronized by the frame sync in normal mode or the slot in network mode.
PC0	Input, output, or disconnected	GPIO disconnected	<b>Port C 0</b> —When the ESAI is configured as GPIO, this signal is individually programmable as input, output, or internally disconnected. The default state after reset is GPIO disconnected. This input is 5 V tolerant.
SCKT	Input or output	GPIO disconnected	<b>Transmitter Serial Clock</b> —This signal provides the serial bit rate clock for the ESAI. SCKT is a clock input or output used by all enabled transmitters and receivers in synchronous mode, or by all enabled transmitters in asynchronous mode.
PC3	Input, output, or disconnected	GPIO disconnected	<b>Port C 3</b> —When the ESAI is configured as GPIO, this signal is individually programmable as input, output, or internally disconnected. The default state after reset is GPIO disconnected. This input is 5 V tolerant.

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**Signal/Connection Descriptions**

**Enhanced Serial Audio Interface**

**Table 1-10 Enhanced Serial Audio Interface Signals (continued)**

Signal Name	Signal Type	State during Reset	Signal Description
SDO5	Output	GPIO disconnected	<b>Serial Data Output 5</b> —When programmed as a transmitter, SDO5 is used to transmit data from the TX5 serial transmit shift register.
SDI0	Input	GPIO disconnected	<b>Serial Data Input 0</b> —When programmed as a receiver, SDI0 is used to receive serial data into the RX0 serial receive shift register.
PC6	Input, output, or disconnected	GPIO disconnected	<b>Port C 6</b> —When the ESAI is configured as GPIO, this signal is individually programmable as input, output, or internally disconnected. The default state after reset is GPIO disconnected. This input is 5 V tolerant.
SDO4	Output	GPIO disconnected	<b>Serial Data Output 4</b> —When programmed as a transmitter, SDO4 is used to transmit data from the TX4 serial transmit shift register.
SDI1	Input	GPIO disconnected	<b>Serial Data Input 1</b> —When programmed as a receiver, SDI1 is used to receive serial data into the RX1 serial receive shift register.
PC7	Input, output, or disconnected	GPIO disconnected	<b>Port C 7</b> —When the ESAI is configured as GPIO, this signal is individually programmable as input, output, or internally disconnected. The default state after reset is GPIO disconnected. This input is 5 V tolerant.
SDO3	Output	GPIO disconnected	<b>Serial Data Output 3</b> —When programmed as a transmitter, SDO3 is used to transmit data from the TX3 serial transmit shift register.
SDI2	Input	GPIO disconnected	<b>Serial Data Input 2</b> —When programmed as a receiver, SDI2 is used to receive serial data into the RX2 serial receive shift register.
PC8	Input, output, or disconnected	GPIO disconnected	<b>Port C 8</b> —When the ESAI is configured as GPIO, this signal is individually programmable as input, output, or internally disconnected. The default state after reset is GPIO disconnected. This input is 5 V tolerant.
SDO2	Output	GPIO disconnected	<b>Serial Data Output 2</b> —When programmed as a transmitter, SDO2 is used to transmit data from the TX2 serial transmit shift register
SDI3	Input	GPIO disconnected	<b>Serial Data Input 3</b> —When programmed as a receiver, SDI3 is used to receive serial data into the RX3 serial receive shift register.
PC9	Input, output, or disconnected	GPIO disconnected	<b>Port C 9</b> —When the ESAI is configured as GPIO, this signal is individually programmable as input, output, or internally disconnected. The default state after reset is GPIO disconnected. This input is 5 V tolerant.

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## Signal/Connection Descriptions

### Enhanced Serial Audio Interface

**Table 1-10 Enhanced Serial Audio Interface Signals (continued)**

Signal Name	Signal Type	State during Reset	Signal Description
SDO1	Output	GPIO disconnected	<b>Serial Data Output 1</b> —SDO1 is used to transmit data from the TX1 serial transmit shift register.
PC10	Input, output, or disconnected	GPIO disconnected	<b>Port C 10</b> —When the ESAI is configured as GPIO, this signal is individually programmable as input, output, or internally disconnected. The default state after reset is GPIO disconnected. This input is 5 V tolerant.
SDO0	Output	GPIO disconnected	<b>Serial Data Output 0</b> —SDO0 is used to transmit data from the TX0 serial transmit shift register.
PC11	Input, output, or disconnected	GPIO disconnected	<b>Port C 11</b> —When the ESAI is configured as GPIO, this signal is individually programmable as input, output, or internally disconnected. The default state after reset is GPIO disconnected. This input is 5 V tolerant.

## 1.9 JTAG/OnCE INTERFACE

Table 1-11 JTAG/OnCE Interface

Signal Name	Signal Type	State during Reset	Signal Description
TCK	Input	Input	<b>Test Clock</b> —TCK is a test clock input signal used to synchronize the JTAG test logic. It has an internal pull-up resistor. <i>This input is 5 V tolerant.</i>
TDI	Input	Input	<b>Test Data Input</b> —TDI is a test data serial input signal used for test instructions and data. TDI is sampled on the rising edge of TCK and has an internal pull-up resistor. This input is 5 V tolerant.
TDO	Output	Tri-stated	<b>Test Data Output</b> —TDO is a test data serial output signal used for test instructions and data. TDO is tri-statable and is actively driven in the shift-IR and shift-DR controller states. TDO changes on the falling edge of TCK.
TMS	Input	Input	<b>Test Mode Select</b> —TMS is an input signal used to sequence the test controller's state machine. TMS is sampled on the rising edge of TCK and has an internal pull-up resistor. This input is 5 V tolerant.

Table 1-12 GPIO Signals

Signal Name	Signal Type	State during Reset	Signal Description
GPIO0-GPIO3	Input, output or disconnected	Disconnected	GPIO0-3- The General Purpose I/O pins are used for control and handshake functions between the DSP and external circuitry. Each Port B GPIO pin may be individually programmed as an input, output or disconnected

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**Freescale Semiconductor, Inc.****SECTION 2****SPECIFICATIONS****2.1 INTRODUCTION**

The DSP56364 is a high density CMOS device with Transistor-Transistor Logic (TTL) compatible inputs and outputs. The DSP56364 specifications are preliminary and are from design simulations, and may not be fully tested or guaranteed. Finalized specifications will be published after full characterization and device qualifications are complete.

**2.2 MAXIMUM RATINGS****CAUTION**

This device contains circuitry protecting against damage due to high static voltage or electrical fields. However, normal precautions should be taken to avoid exceeding maximum voltage ratings. Reliability of operation is enhanced if unused inputs are pulled to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). The suggested value for a pullup or pulldown resistor is 10 k $\Omega$ .

**Note:** In the calculation of timing requirements, adding a maximum value of one specification to a minimum value of another specification does not yield a reasonable sum. A maximum specification is calculated using a worst case variation of process parameter values in one direction. The minimum specification is calculated using the worst case for the same parameters in the opposite direction. Therefore, a “maximum” value for a specification will never occur in the same device that has a “minimum” value for another specification; adding a maximum to a minimum represents a condition that can never exist.

# Freescale Semiconductor, Inc.

## Specifications

### Thermal Characteristics

**Table 2-1 Maximum Ratings**

Rating <sup>1</sup>	Symbol	Value <sup>1, 2</sup>	Unit
Supply Voltage	V <sub>CC</sub>	-0.3 to +4.0	V
All input voltages excluding "5 V tolerant" inputs <sup>3</sup>	V <sub>IN</sub>	GND -0.3 to V <sub>CC</sub> + 0.3	V
All "5 V tolerant" input voltages <sup>3</sup>	V <sub>IN5</sub>	GND – 0.3 to V <sub>CC</sub> + 3.95	V
Current drain per pin excluding V <sub>CC</sub> and GND	I	10	mA
Operating temperature range	T <sub>J</sub>	-40 to +105	°C
Storage temperature	T <sub>STG</sub>	-55 to +125	°C

Notes:

- 1. GND = 0 V, V<sub>CC</sub> = 3.3 V ± 0.16 V, T<sub>J</sub> = -0°C to +105°C, CL = 50 pF
- 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximum is not guaranteed. Stress beyond the maximum rating may affect device reliability or cause permanent damage to the device.
- 3. **CAUTION:** All "5 V Tolerant" input voltages must not be more than 3.95 V greater than the supply voltage; this restriction applies to "power on", as well as during normal operation. In any case, the input voltages cannot be more than 5.75 V. "5 V Tolerant" inputs are inputs that tolerate 5 V.

## 2.3 THERMAL CHARACTERISTICS

**Table 2-2 Thermal Characteristics**

Characteristic	Symbol	TQFP Value	Unit
Junction-to-ambient thermal resistance <sup>1</sup>	R <sub>θJA</sub> or θ <sub>JA</sub>	49.87	°C/W
Junction-to-case thermal resistance <sup>2</sup>	R <sub>θJC</sub> or θ <sub>JC</sub>	9.26	°C/W
Thermal characterization parameter	Ψ <sub>JT</sub>	2.0	°C/W

Notes:

- 1. Junction-to-ambient thermal resistance is based on measurements on a horizontal single-sided printed circuit board per SEMI G38-87 in natural convection.(SEMI is Semiconductor Equipment and Materials International, 805 East Middlefield Rd., Mountain View, CA 94043, (415) 964-5111.) Measurements were done with parts mounted on thermal test boards conforming to specification EIA/JESD51-3.
- 2. Junction-to-case thermal resistance is based on measurements using a cold plate per SEMI G30-88, with the exception that the cold plate temperature is used for the case temperature.

## 2.4 DC ELECTRICAL CHARACTERISTICS

**Table 2-3 DC Electrical Characteristics<sup>6</sup>**

Characteristics	Symbol	Min	Typ	Max	Unit
Supply voltage	V <sub>CC</sub>	3.14	3.3	3.46	V
Input high voltage • D(0:7), TA	V <sub>IH</sub>	2.0	—	V <sub>CC</sub>	V
• MOD <sup>1</sup> /IRQ <sup>1</sup> , RESET, PINIT/NMI and all JTAG/ESAI/GPIO/SPI mode)pins	V <sub>IHP</sub>	2.0	—	V <sub>CC</sub> + 3.95	
• SHI (I2C mode) pins	V <sub>IHP</sub>	1.5	—	V <sub>CC</sub> + 3.95	
• EXTAL <sup>8</sup>	V <sub>IHX</sub>	0.8 × V <sub>CC</sub>	—	V <sub>CC</sub>	
Input low voltage • D(0:7), TA, MOD <sup>1</sup> /IRQ <sup>1</sup> , RESET, PINIT	V <sub>IL</sub>	-0.3	—	0.8	V
• JTAG/ESAI/GPIO/SPI mode)pins	V <sub>ILP</sub>	-0.3	—	0.8	
• SHI (I2C mode) pins	V <sub>ILP</sub>	-0.3	—	0.3 × V <sub>CC</sub>	
• EXTAL <sup>8</sup>	V <sub>ILX</sub>	-0.3	—	0.2 × V <sub>CC</sub>	
Input leakage current	I <sub>IN</sub>	-10	—	10	µA
High impedance (off-state) input current (@ 2.4 V / 0.4 V)	I <sub>TSI</sub>	-10	—	10	µA
Output high voltage • TTL (I <sub>OH</sub> = -0.4 mA) <sup>5,7</sup>	V <sub>OH</sub>	2.4	—	—	V
• CMOS (I <sub>OH</sub> = -10 µA) <sup>5</sup>		V <sub>CC</sub> - 0.01	—	—	V
Output low voltage • TTL (I <sub>OL</sub> = 3.0 mA, open-drain pins I <sub>OL</sub> = 6.7 mA) <sup>5,7</sup>	V <sub>OL</sub>	—	—	0.4	V
• CMOS (I <sub>OL</sub> = 10 µA) <sup>5</sup>		—	—	0.01	

# Freescale Semiconductor, Inc.

## Specifications

### AC Electrical Characteristics

**Table 2-3 DC Electrical Characteristics<sup>6</sup> (continued)**

Characteristics	Symbol	Min	Typ	Max	Unit
Internal supply current <sup>2</sup> at internal clock of 100Mhz • In Normal mode	I <sub>CC1</sub>	—	127	181	mA
• In Wait mode <sup>3</sup>	I <sub>CCW</sub>	—	7.5	11	mA
• In Stop mode <sup>4</sup>	I <sub>CCS</sub>	—	100	150	μA
PLL supply current		—	1	2.5	mA
Input capacitance <sup>5</sup>	C <sub>IN</sub>	—	—	10	pF

Notes:

- Refers to MODA/IRQA, MODB/IRQB, and MODD/IRQD pins
- Section 4.3, *Power Consumption Considerations* on page 3 provides a formula to compute the estimated current requirements in Normal mode. In order to obtain these results, all inputs must be terminated (i.e., not allowed to float). Measurements are based on synthetic intensive DSP benchmarks. The power consumption numbers in this specification are 90% of the measured results of this benchmark. This reflects typical DSP applications. Typical internal supply current is measured with V<sub>CC</sub> = 3.3 V at T<sub>J</sub> = 105°C. Maximum internal supply current is measured with V<sub>CC</sub> = 3.46 V at T<sub>J</sub> = 105°C.
- In order to obtain these results, all inputs must be terminated (i.e., not allowed to float). PLL signal is disabled during Stop state.
- In order to obtain these results, all inputs, which are not disconnected at Stop mode, must be terminated (i.e., not allowed to float).
- Periodically sampled and not 100% tested
- V<sub>CC</sub> = 3.3 V ± .16 V; T<sub>J</sub> = 0°C to +105°C, C<sub>L</sub> = 50 pF
- This characteristic does not apply to PCAP.
- Driving EXTAL to the low V<sub>IHX</sub> or the high V<sub>ILX</sub> value may cause additional power consumption (DC current). To minimize power consumption, the minimum V<sub>IHX</sub> should be no lower than 0.9 × V<sub>CC</sub> and the maximum V<sub>ILX</sub> should be no higher than 0.1 × V<sub>CC</sub>.

## 2.5 AC ELECTRICAL CHARACTERISTICS

The timing waveforms shown in the AC electrical characteristics section are tested with a V<sub>IL</sub> maximum of 0.3 V and a V<sub>IH</sub> minimum of 2.4 V for all pins except EXTAL, which is tested using the input levels shown in **Note 8** of the previous table. AC timing specifications, which are referenced to a device input signal, are measured in production with respect to the 50% point of the respective input signal's transition. DSP56364 output levels are measured with the production test machine V<sub>OL</sub> and V<sub>OH</sub> reference levels set at 0.4 V and 2.4 V, respectively.

**Note:** Although the minimum value for the frequency of EXTAL is 0 MHz, the device AC test conditions are 15 MHz and rated speed.

## 2.6 INTERNAL CLOCKS

**Table 2-4 Internal Clocks**

Characteristics	Symbol I	Expression <sup>1, 2</sup>		
		Min	Typ	Max
Internal operation frequency with PLL enabled	f	—	$(Ef \times MF) / (PDF \times DF)$	—
Internal operation frequency with PLL disabled	f	—	$Ef/2$	—
Internal clock high period <ul style="list-style-type: none"> <li>• With PLL disabled</li> <li>• With PLL enabled and <math>MF \leq 4</math></li> <li>• With PLL enabled and <math>MF &gt; 4</math></li> </ul>	$T_H$	—	$ET_C$	—
		$0.49 \times ET_C \times PDF \times DF/MF$	—	$0.51 \times ET_C \times PDF \times DF/MF$
		$0.47 \times ET_C \times PDF \times DF/MF$	—	$0.53 \times ET_C \times PDF \times DF/MF$
		—	$ET_C$	—
Internal clock low period <ul style="list-style-type: none"> <li>• With PLL disabled</li> <li>• With PLL enabled and <math>MF \leq 4</math></li> <li>• With PLL enabled and <math>MF &gt; 4</math></li> </ul>	$T_L$	—	$ET_C$	—
		$0.49 \times ET_C \times PDF \times DF/MF$	—	$0.51 \times ET_C \times PDF \times DF/MF$
		$0.47 \times ET_C \times PDF \times DF/MF$	—	$0.53 \times ET_C \times PDF \times DF/MF$
		—	$ET_C \times PDF \times DF/MF$	—
Internal clock cycle time with PLL enabled	$T_C$	—	$2 \times ET_C$	—
Instruction cycle time	$I_{CYC}$	—	$T_C$	—
Notes: <ol style="list-style-type: none"> <li>1. DF = Division Factor  <math>Ef</math> = External frequency  <math>ET_C</math> = External clock cycle  <math>MF</math> = Multiplication Factor  <math>PDF</math> = Predivision Factor  <math>T_C</math> = internal clock cycle</li> <li>2. See the <i>PLL and Clock Generation</i> section in the <i>DSP56300 Family Manual</i> for a detailed discussion of the PLL.</li> </ol>				

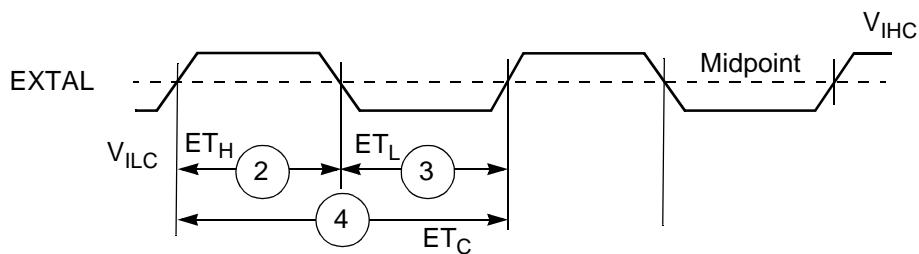
# Freescale Semiconductor, Inc.

## Specifications

### EXTERNAL CLOCK OPERATION

## 2.7 EXTERNAL CLOCK OPERATION

The DSP56364 system clock is an externally supplied square wave voltage source connected to EXTAL(See Figure 2-1).



Note: The midpoint is  $0.5(V_{IHC} + V_{ILC})$ .

**Figure 2-1 External Clock Timing**

**Table 2-5 Clock Operation**

No.	Characteristics	Symbol	Min	Max
1	Frequency of EXTAL (EXTAL Pin Frequency) The rise and fall time of this external clock should be 3 ns maximum.	Ef	0	100.0
2	EXTAL input high <sup>1, 2</sup> <ul style="list-style-type: none"> <li>With PLL disabled (46.7%–53.3% duty cycle<sup>6</sup>)</li> <li>With PLL enabled (42.5%–57.5% duty cycle<sup>6</sup>)</li> </ul>	ET <sub>H</sub>	4.67 ns 4.25 ns	∞ 157.0 μs
3	EXTAL input low <sup>1, 2</sup> <ul style="list-style-type: none"> <li>With PLL disabled (46.7%–53.3% duty cycle<sup>6</sup>)</li> <li>With PLL enabled (42.5%–57.5% duty cycle<sup>6</sup>)</li> </ul>	ET <sub>L</sub>	4.67 ns 4.25 ns	∞ 157.0 μs
4	EXTAL cycle time <sup>2</sup> <ul style="list-style-type: none"> <li>With PLL disabled</li> <li>With PLL enabled</li> </ul>	ET <sub>C</sub>	10.00 ns 10.00 ns	∞ 273.1 μs
Notes: 1. Measured at 50% of the input transition 2. The maximum value for PLL enabled is given for minimum $V_{CO}$ and maximum MF.				

## 2.8 PHASE LOCK LOOP (PLL) CHARACTERISTICS

**Table 2-6 PLL Characteristics**

Characteristics	Min	Max	Unit
$V_{CO}$ frequency when PLL enabled ( $MF \times E_f \times 2/PDF$ )	30	200	MHz
PLL external capacitor (PCAP pin to $V_{CCP}$ ) ( $C_{PCAP}^{(1)}$ )			pF
<ul style="list-style-type: none"> <li>• @ <math>MF \leq 4</math> <math>(MF \times 580) - 100</math> <math>(MF \times 780) - 140</math></li> <li>• @ <math>MF &gt; 4</math> <math>MF \times 830</math> <math>MF \times 1470</math></li> </ul>			
<p>Notes:</p> <ol style="list-style-type: none"> <li>1. <math>C_{PCAP}</math> is the value of the PLL capacitor (connected between the PCAP pin and <math>V_{CCP}</math>). The recommended value in pF for <math>C_{PCAP}</math> can be computed from one of the following equations:  <math>(MF \times 680) - 120</math>, for <math>MF \leq 4</math>, or  <math>MF \times 1100</math>, for <math>MF &gt; 4</math>.</li> </ol>			

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## Specifications

### Reset, Stop, Mode Select, and Interrupt Timing

## 2.9 RESET, STOP, MODE SELECT, AND INTERRUPT TIMING

**Table 2-7 Reset, Stop, Mode Select, and Interrupt Timing<sup>6</sup>**

No.	Characteristics	Expression	Min	Max	Unit
8	Delay from <u>RESET</u> assertion to all pins at reset value <sup>3</sup>	—	—	26.0	ns
9	Required <u>RESET</u> duration <sup>4</sup> <ul style="list-style-type: none"> <li>• Power on, external clock generator, PLL disabled</li> <li>• Power on, external clock generator, PLL enabled</li> <li>• Power on, internal oscillator</li> <li>• During STOP, XTAL disabled (PCTL Bit 16 = 0)</li> <li>• During STOP, XTAL enabled (PCTL Bit 16 = 1)</li> <li>• During normal operation</li> </ul>	$50 \times T_C$ $1000 \times T_C$ $75000 \times T_C$ $75000 \times T_C$ $2.5 \times T_C$ $2.5 \times T_C$	500.0 10.0 0.75 0.75 25.0 25.0	—	ns ns $\mu s$ ms ms ns
10	Delay from asynchronous <u>RESET</u> deassertion to first external address output (internal reset deassertion) <sup>5</sup> <ul style="list-style-type: none"> <li>• Minimum</li> <li>• Maximum</li> </ul>	$3.25 \times T_C + 2.0$ $20.25 T_C + 7.50$	34.5 —	— 211.5	ns ns
13	Mode select setup time		30.0	—	ns
14	Mode select hold time		0.0	—	ns
15	Minimum edge-triggered interrupt request assertion width		6.6	—	ns
16	Minimum edge-triggered interrupt request deassertion width		6.6	—	ns
17	Delay from <u>IRQA</u> , <u>IRQB</u> , <u>IRQD</u> , <u>NMI</u> assertion to external memory access address out valid <ul style="list-style-type: none"> <li>• Caused by first interrupt instruction fetch</li> <li>• Caused by first interrupt instruction execution</li> </ul>	$4.25 \times T_C + 2.0$ $7.25 \times T_C + 2.0$	44.5 74.5	—	ns ns

# Freescale Semiconductor, Inc.

## Specifications

### Reset, Stop, Mode Select, and Interrupt Timing

**Table 2-7 Reset, Stop, Mode Select, and Interrupt Timing<sup>6</sup> (continued)**

No.	Characteristics	Expression	Min	Max	Unit
18	Delay from $\overline{\text{IRQA}}$ , $\overline{\text{IRQB}}$ , $\overline{\text{IRQD}}$ , $\overline{\text{NMI}}$ assertion to general-purpose transfer output valid caused by first interrupt instruction execution	$10 \times T_C + 5.0$	105.0	—	ns
19	Delay from address output valid caused by first interrupt instruction execute to interrupt request deassertion for level sensitive fast interrupts <sup>1</sup>	$3.75 \times T_C + WS \times T_C - 10.94$	—	—	ns
20	Delay from $\overline{\text{RD}}$ assertion to interrupt request deassertion for level sensitive fast interrupts <sup>1</sup>	$3.25 \times T_C + WS \times T_C - 10.94$	—	—	ns
21	Delay from $\overline{\text{WR}}$ assertion to interrupt request deassertion for level sensitive fast interrupts <sup>1</sup> <ul style="list-style-type: none"> <li>• DRAM for all WS</li> <li>• SRAM WS = 1</li> <li>• SRAM WS = 2, 3</li> <li>• SRAM WS <math>\geq 4</math></li> </ul>	( $WS + 3.5$ ) $\times T_C - 10.94$  ( $WS + 3.5$ ) $\times T_C - 10.94$  ( $WS + 3$ ) $\times T_C - 10.94$  ( $WS + 2.5$ ) $\times T_C - 10.94$	— — — —	— — — —	ns
24	Duration for $\overline{\text{IRQA}}$ assertion to recover from Stop state		5.9	—	
25	Delay from $\overline{\text{IRQA}}$ assertion to fetch of first instruction (when exiting Stop) <sup>2, 3</sup> <ul style="list-style-type: none"> <li>• PLL is not active during Stop (PCTL Bit 17 = 0) and Stop delay is enabled (OMR Bit 6 = 0)</li> <li>• PLL is not active during Stop (PCTL Bit 17 = 0) and Stop delay is not enabled (OMR Bit 6 = 1)</li> <li>• PLL is active during Stop (PCTL Bit 17 = 1) (Implies No Stop Delay)</li> </ul>	$PLC \times ET_C \times PDF + (128 K - PLC/2) \times T_C$  $PLC \times ET_C \times PDF + (23.75 \pm 0.5) \times T_C$  $(8.25 \pm 0.5) \times T_C$	1.3 232.5 ns 77.5	13.6 12.3 ms 87.5	ms ns ns

# Freescale Semiconductor, Inc.

## Specifications

### Reset, Stop, Mode Select, and Interrupt Timing

**Table 2-7 Reset, Stop, Mode Select, and Interrupt Timing<sup>6</sup> (continued)**

No.	Characteristics	Expression	Min	Max	Unit
26	<p>Duration of level sensitive <math>\overline{\text{IRQA}}</math> assertion to ensure interrupt service (when exiting Stop)<sup>2, 3</sup></p> <ul style="list-style-type: none"> <li>• PLL is not active during Stop (PCTL Bit 17 = 0) and Stop delay is enabled (OMR Bit 6 = 0)</li> <li>• PLL is not active during Stop (PCTL Bit 17 = 0) and Stop delay is not enabled (OMR Bit 6 = 1)</li> <li>• PLL is active during Stop (PCTL Bit 17 = 1) (implies no Stop delay)</li> </ul>	$\text{PLC} \times \text{ET}_C \times \text{PDF} + (\text{128K} - \text{PLC}/2) \times T_C$ $\text{PLC} \times \text{ET}_C \times \text{PDF} + (20.5 \pm 0.5) \times T_C$ $5.5 \times T_C$	13.6	—	ms
27	<p>Interrupt Requests Rate</p> <ul style="list-style-type: none"> <li>• ESAI, SCI</li> <li>• DMA</li> <li>• <math>\overline{\text{IRQ}}, \overline{\text{NMI}}</math> (edge trigger)</li> <li>• <math>\overline{\text{IRQ}}, \overline{\text{NMI}}</math> (level trigger)</li> </ul>	$12T_C$ $8T_C$ $8T_C$ $12T_C$	—	120.0	ns
28	<p>DMA Requests Rate</p> <ul style="list-style-type: none"> <li>• Data read from ESAI, SCI</li> <li>• Data write to ESAI, SCI</li> <li>• <math>\overline{\text{IRQ}}, \overline{\text{NMI}}</math> (edge trigger)</li> </ul>	$6T_C$ $7T_C$ $3T_C$	—	60.0	ns
			—	70.0	ns
			—	30.0	ns

# Freescale Semiconductor, Inc.

## Specifications

### Reset, Stop, Mode Select, and Interrupt Timing

**Table 2-7 Reset, Stop, Mode Select, and Interrupt Timing<sup>6</sup> (continued)**

No.	Characteristics	Expression	Min	Max	Unit
29	Delay from <u>IRQA</u> , <u>IRQB</u> , <u>IRQD</u> , <u>NMI</u> assertion to external memory (DMA source) access address out valid	$4.25 \times T_C + 2.0$	44.0	—	ns
Notes:					
1. When using fast interrupts and <u>IRQA</u> , <u>IRQB</u> , and <u>IRQD</u> are defined as level-sensitive, timings 19 through 21 apply to prevent multiple interrupt service. To avoid these timing restrictions, the deasserted Edge-triggered mode is recommended when using fast interrupts. Long interrupts are recommended when using Level-sensitive mode.					
2. This timing depends on several settings:  For PLL disable, using internal oscillator (PCTL Bit 16 = 0) and oscillator disabled during Stop (PCTL Bit 17 = 0), a stabilization delay is required to assure the oscillator is stable before executing programs. In that case, resetting the Stop delay (OMR Bit 6 = 0) will provide the proper delay. While it is possible to set OMR Bit 6 = 1, it is not recommended and these specifications do not guarantee timings for that case.  For PLL disable, using internal oscillator (PCTL Bit 16 = 0) and oscillator enabled during Stop (PCTL Bit 17=1), no stabilization delay is required and recovery time will be minimal (OMR Bit 6 setting is ignored).  For PLL disable, using external clock (PCTL Bit 16 = 1), no stabilization delay is required and recovery time will be defined by the PCTL Bit 17 and OMR Bit 6 settings.  For PLL enable, if PCTL Bit 17 is 0, the PLL is shutdown during Stop. Recovering from Stop requires the PLL to get locked. The PLL lock procedure duration, PLL Lock Cycles (PLC), may be in the range of 0 to 1000 cycles. This procedure occurs in parallel with the stop delay counter, and stop recovery will end when the last of these two events occurs. The stop delay counter completes count or PLL lock procedure completion.  PLC value for PLL disable is 0.  The maximum value for $ET_C$ is 4096 (maximum MF) divided by the desired internal frequency (i.e., for 100 MHz it is $4096/100\text{ MHz} = 40\text{ }\mu\text{s}$ ). During the stabilization period, $T_C$ , $T_H$ , and $T_L$ will not be constant, and their width may vary, so timing may vary as well.  3. Periodically sampled and not 100% tested  4. For an external clock generator, <u>RESET</u> duration is measured during the time in which <u>RESET</u> is asserted, $V_{CC}$ is valid, and the EXTAL input is active and valid.  For internal oscillator, <u>RESET</u> duration is measured during the time in which <u>RESET</u> is asserted and $V_{CC}$ is valid. The specified timing reflects the crystal oscillator stabilization time after power-up. This number is affected both by the specifications of the crystal and other components connected to the oscillator and reflects worst case conditions.  When the $V_{CC}$ is valid, but the other “required <u>RESET</u> duration” conditions (as specified above) have not been yet met, the device circuitry will be in an uninitialized state that can result in significant power consumption and heat-up. Designs should minimize this state to the shortest possible duration.					

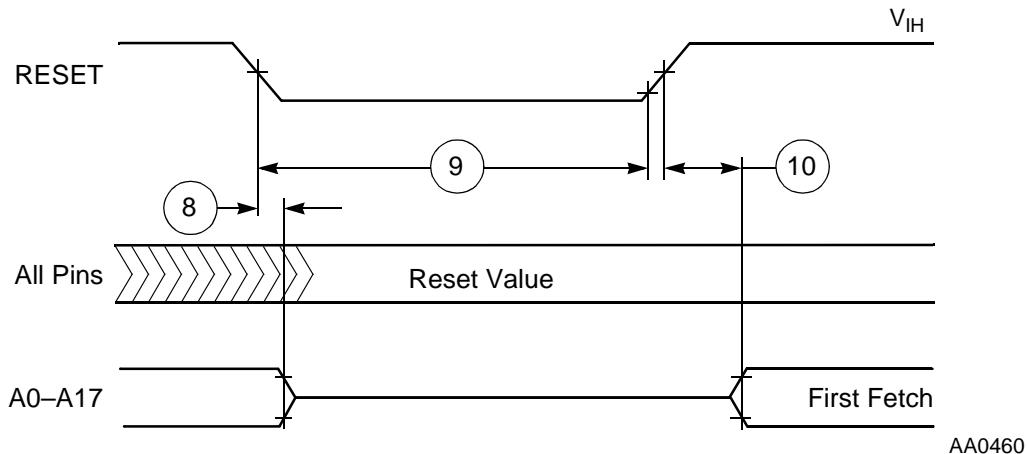
# Freescale Semiconductor, Inc.

## Specifications

### Reset, Stop, Mode Select, and Interrupt Timing

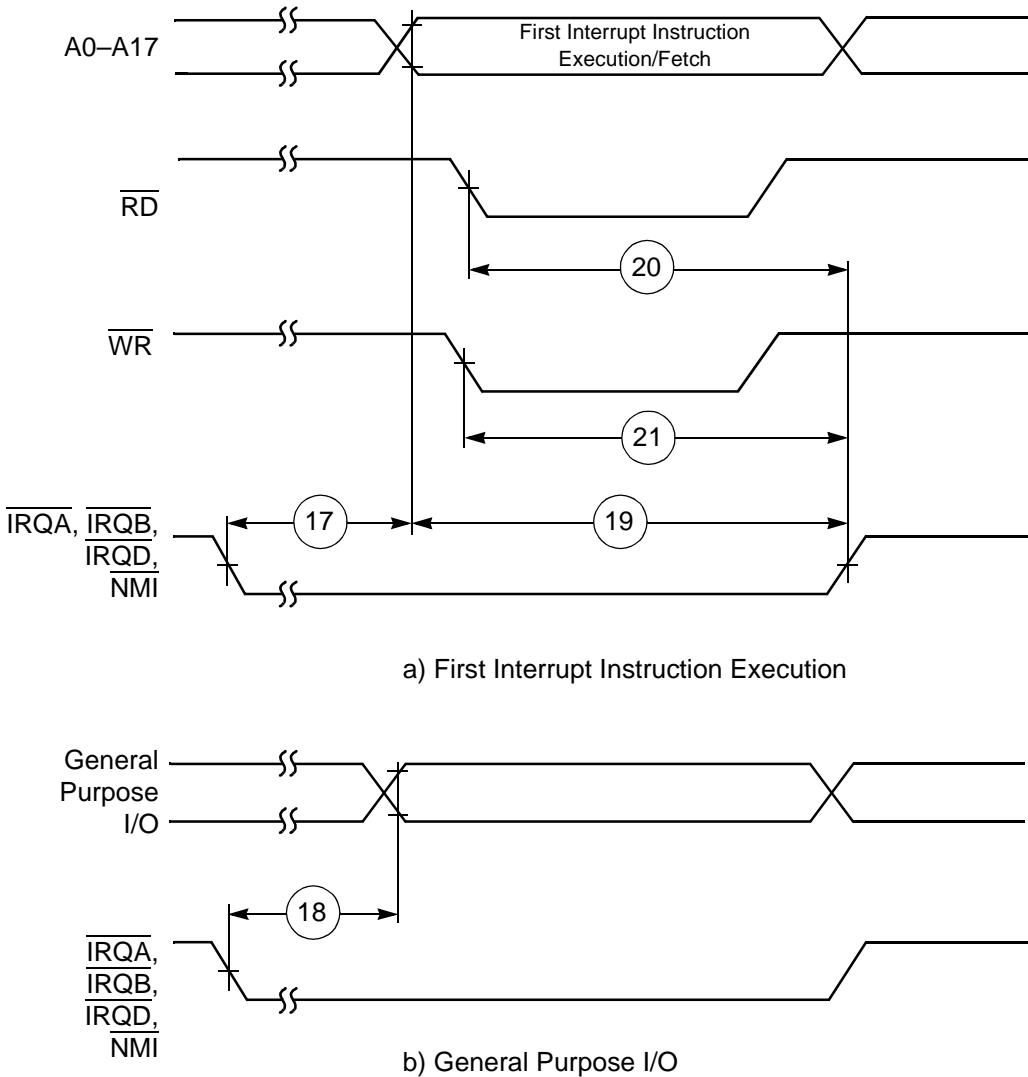
**Table 2-7 Reset, Stop, Mode Select, and Interrupt Timing<sup>6</sup> (continued)**

No.	Characteristics	Expression	Min	Max	Unit
5.	<p>For an external clock generator, <math>\overline{\text{RESET}}</math> duration is measured during the time in which <math>\overline{\text{RESET}}</math> is asserted, <math>V_{CC}</math> is valid, and the EXTAL input is active and valid.</p> <p>For internal oscillator, <math>\overline{\text{RESET}}</math> duration is measured during the time in which <math>\overline{\text{RESET}}</math> is asserted and <math>V_{CC}</math> is valid. The specified timing reflects the crystal oscillator stabilization time after power-up. This number is affected both by the specifications of the crystal and other components connected to the oscillator and reflects worst case conditions.</p> <p>When the <math>V_{CC}</math> is valid, but the other “required <math>\overline{\text{RESET}}</math> duration” conditions (as specified above) have not been yet met, the device circuitry will be in an uninitialized state that can result in significant power consumption and heat-up. Designs should minimize this state to the shortest possible duration.</p> <p>6. If PLL does not lose lock</p> <p>7. <math>V_{CC} = 3.3 \text{ V} \pm 0.16 \text{ V}; T_J = 0^\circ\text{C} \text{ to } +105^\circ\text{C}, C_L = 50 \text{ pF}</math></p> <p>8. WS = number of wait states (measured in clock cycles, number of <math>T_C</math>)</p> <p>9. Use expression to compute maximum value.</p>				



**Figure 2-2 Reset Timing**

### Reset, Stop, Mode Select, and Interrupt Timing



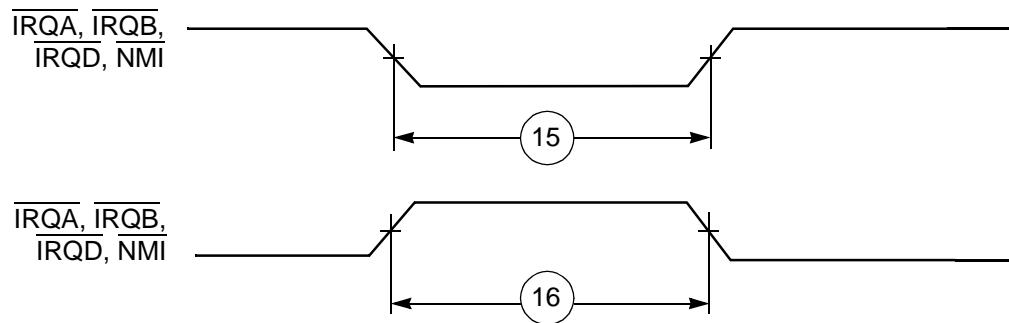
AA0462

**Figure 2-3 External Fast Interrupt Timing**

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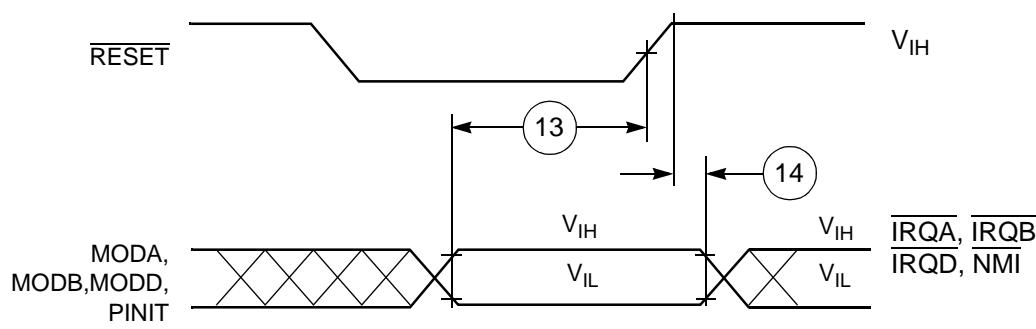
## Specifications

### Reset, Stop, Mode Select, and Interrupt Timing



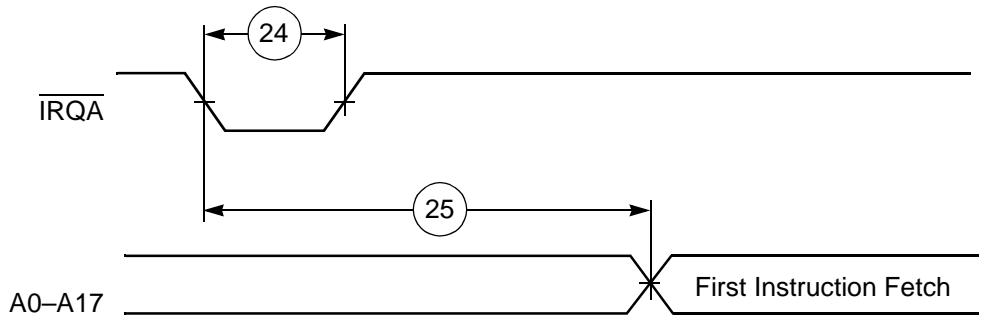
AA0463

**Figure 2-4 External Interrupt Timing (Negative Edge-Triggered)**



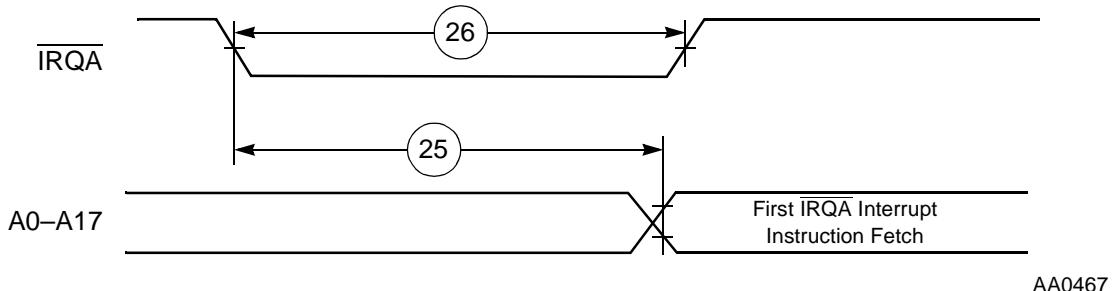
AA0465

**Figure 2-5 Operating Mode Select Timing**

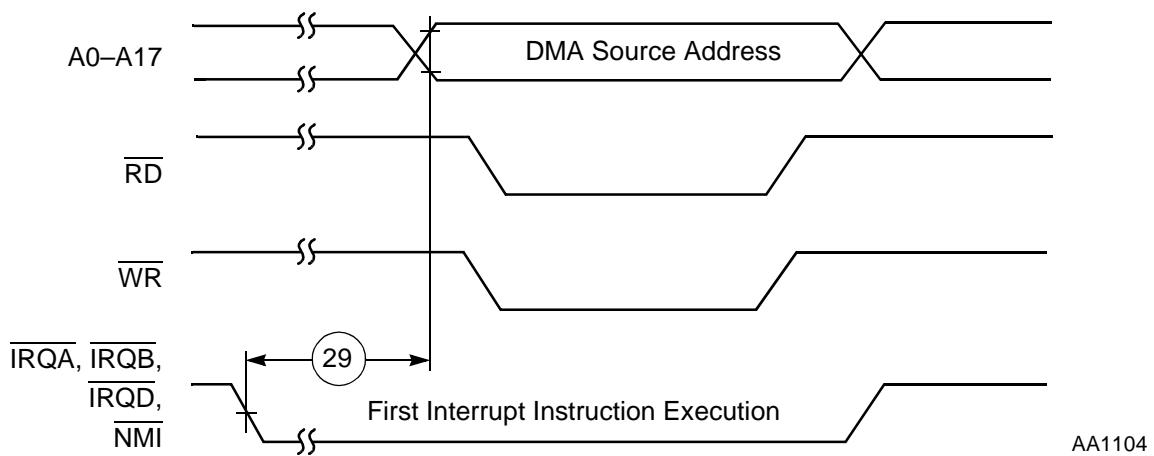


AA0466

**Figure 2-6 Recovery from Stop State Using  $\overline{\text{IRQA}}$**



**Figure 2-7 Recovery from Stop State Using  $\overline{\text{IRQA}}$  Interrupt Service**



**Figure 2-8 External Memory Access (DMA Source) Timing**

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

## 2.10 EXTERNAL MEMORY EXPANSION PORT (PORT A)

### 2.10.1 SRAM Timing

Table 2-8 SRAM Read and Write Accesses<sup>3</sup>

No.	Characteristics	Symbol	Expression <sup>1</sup>	Min	Max	Unit
100	Address valid and AA assertion pulse width	$t_{RC}, t_{WC}$	$(WS + 1) \times T_C - 4.0$ $[1 \leq WS \leq 3]$ $(WS + 2) \times T_C - 4.0$ $[4 \leq WS \leq 7]$ $(WS + 3) \times T_C - 4.0$ $[WS \geq 8]$	16.0	—	ns
101	Address and AA valid to $\overline{WR}$ assertion	$t_{AS}$	$0.25 \times T_C - 2.0$ $[WS = 1]$ $0.75 \times T_C - 2.0$ $[2 \leq WS \leq 3]$ $1.25 \times T_C - 2.0$ $[WS \geq 4]$	0.5	—	ns
102	$\overline{WR}$ assertion pulse width	$t_{WP}$	$1.5 \times T_C - 4.0$ $[WS = 1]$ All frequencies: $WS \times T_C - 4.0$ $[2 \leq WS \leq 3]$ $(WS - 0.5) \times T_C - 4.0$ $[WS \geq 4]$	11.0	—	ns
				16.0	—	ns
				31.0	—	ns

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-8 SRAM Read and Write Accesses<sup>3</sup> (continued)**

No.	Characteristics	Symbol	Expression <sup>1</sup>	Min	Max	Unit
103	$\overline{WR}$ deassertion to address not valid	$t_{WR}$	$0.25 \times T_C - 2.0$ $[1 \leq WS \leq 3]$ $1.25 \times T_C - 2.0$ $[4 \leq WS \leq 7]$ $2.25 \times T_C - 2.0$ $[WS \geq 8]$ All frequencies: $1.25 \times T_C - 4.0$ $[4 \leq WS \leq 7]$ $2.25 \times T_C - 4.0$ $[WS \geq 8]$	0.5	—	ns
104	Address and AA valid to input data valid	$t_{AA}, t_{AC}$	$(WS + 0.75) \times T_C - 7.0$ $[WS \geq 1]$	—	10.5	ns
105	$\overline{RD}$ assertion to input data valid	$t_{OE}$	$(WS + 0.25) \times T_C - 7.0$ $[WS \geq 1]$	—	5.5	ns
106	$\overline{RD}$ deassertion to data not valid (data hold time)	$t_{OHZ}$		0.0	—	ns
107	Address valid to $\overline{WR}$ deassertion <sup>2</sup>	$t_{AW}$	$(WS + 0.75) \times T_C - 4.0$ $[WS \geq 1]$	13.5	—	ns
108	Data valid to $\overline{WR}$ deassertion (data setup time)	$t_{DS} (t_{DW})$	$(WS - 0.25) \times T_C - 3.0$ $[WS \geq 1]$	4.5	—	ns
109	Data hold time from $\overline{WR}$ deassertion	$t_{DH}$	$0.25 \times T_C - 2.0$ $[1 \leq WS \leq 3]$ $1.25 \times T_C - 2.0$ $[4 \leq WS \leq 7]$ $2.25 \times T_C - 2.0$ $[WS \geq 8]$	0.5	—	ns

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-8 SRAM Read and Write Accesses<sup>3</sup> (continued)**

No.	Characteristics	Symbol	Expression <sup>1</sup>	Min	Max	Unit
113	$\overline{RD}$ deassertion time		$0.75 \times T_C - 4.0$ [ $1 \leq WS \leq 3$ ]  $1.75 \times T_C - 4.0$ [ $4 \leq WS \leq 7$ ]  $2.75 \times T_C - 4.0$ [ $WS \geq 8$ ]	3.5	—	ns
114	$\overline{WR}$ deassertion time		$0.5 \times T_C - 4.0$ [ $WS = 1$ ]  $T_C - 2.0$ [ $2 \leq WS \leq 3$ ]  $2.5 \times T_C - 4.0$ [ $4 \leq WS \leq 7$ ]  $3.5 \times T_C - 4.0$ [ $WS \geq 8$ ]	1.0	—	ns
115	Address valid to $\overline{RD}$ assertion		$0.5 \times T_C - 4.0$	1.0	—	ns
116	$\overline{RD}$ assertion pulse width		$(WS + 0.25) \times T_C - 4.0$	8.5	—	ns
117	$\overline{RD}$ deassertion to address not valid		$0.25 \times T_C - 2.0$ [ $1 \leq WS \leq 3$ ]  $1.25 \times T_C - 2.0$ [ $4 \leq WS \leq 7$ ]  $2.25 \times T_C - 2.0$ [ $WS \geq 8$ ]	0.5	—	ns
118	$\overline{TA}$ setup before $\overline{RD}$ or $\overline{WR}$ deassertion <sup>4</sup>		$0.25 \times T_C + 2.0$	4.5	—	ns
119	$\overline{TA}$ hold after $\overline{RD}$ or $\overline{WR}$ deassertion			0	—	ns
Notes:						
1. WS is the number of wait states specified in the BCR. 2. Timings 100, 107 are guaranteed by design, not tested. 3. All timings for 100 MHz are measured from $0.5 \cdot V_{CC}$ to $.05 \cdot V_{CC}$ 4. In the case of $\overline{TA}$ negation: timing 118 is relative to the deassertion edge of $\overline{RD}$ or $WR$ were $\overline{TA}$ to remain active						

### External Memory Expansion Port (Port A)

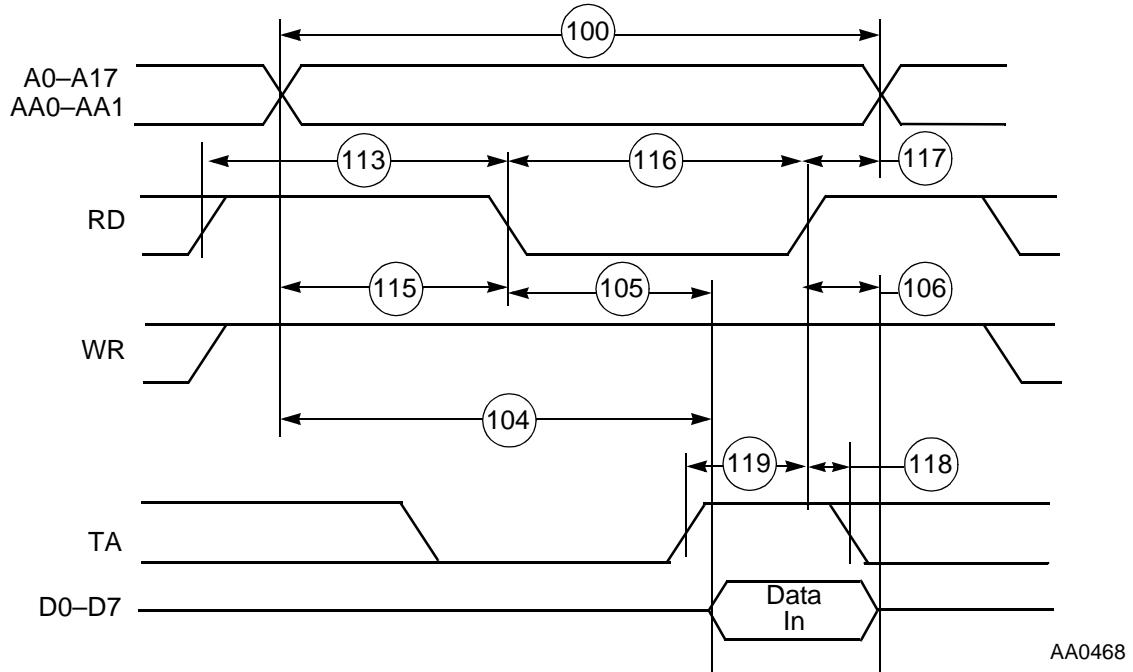


Figure 2-9 SRAM Read Access

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

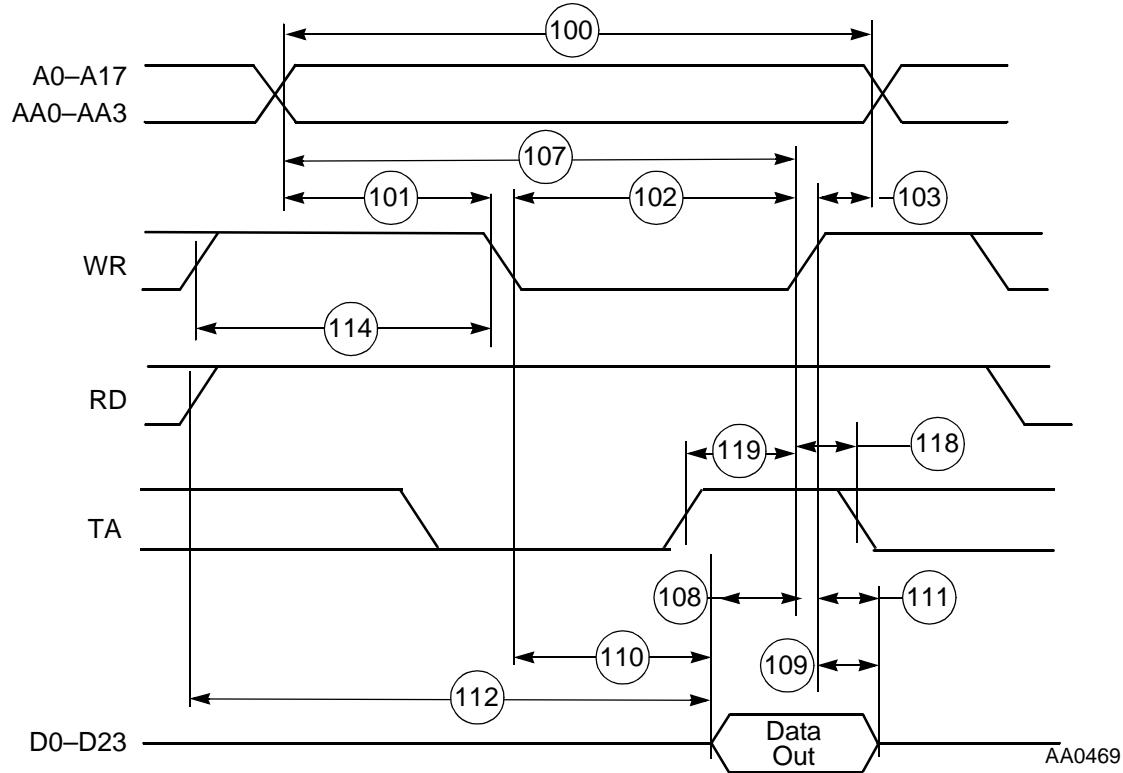
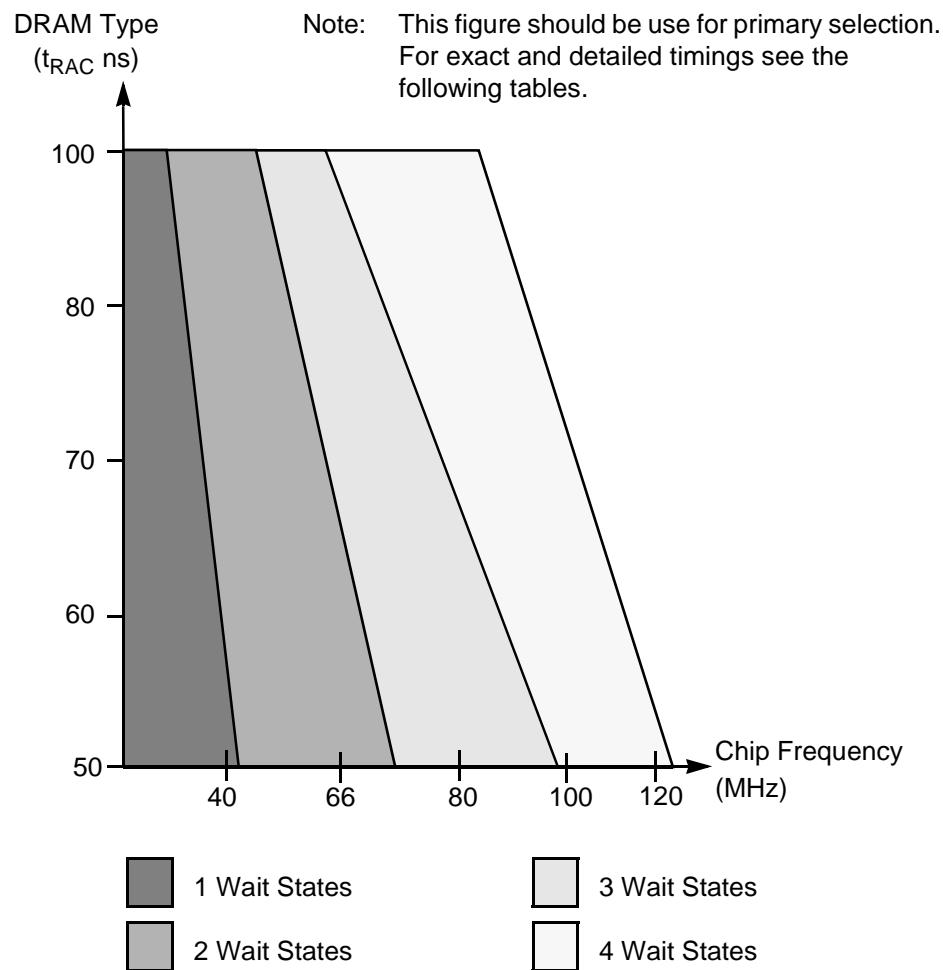


Figure 2-10 SRAM Write Access

## 2.10.2 DRAM Timing

The selection guides provided in Figure 2-11 and Figure 2-14 should be used for primary selection only. Final selection should be based on the timing provided in the following tables. As an example, the selection guide suggests that 4 wait states must be used for 100 MHz operation when using Page Mode DRAM. However, by using the information in the appropriate table, a designer may choose to evaluate whether fewer wait states might be used by determining which timing prevents operation at 100 MHz, running the chip at a slightly lower frequency (e.g., 95 MHz), using faster DRAM (if it becomes available), and control factors such as capacitive and resistive load to improve overall system performance.



**Figure 2-11 DRAM Page Mode Wait States Selection Guide**

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-9 DRAM Page Mode Timings, One Wait State (Low-Power Applications)<sup>1, 2, 3</sup>**

No.	Characteristics	Symbol	Expression	20 MHz <sup>6</sup>		30 MHz <sup>6</sup>		Unit
				Min	Max	Min	Max	
131	Page mode cycle time for two consecutive accesses of the same direction	$t_{PC}$	$2 \times T_C$	100.0	—	66.7	—	ns
	Page mode cycle time for mixed (read and write) accesses		$1.25 \times T_C$	62.5	—	41.7	—	
132	CAS assertion to data valid (read)	$t_{CAC}$	$T_C - 7.5$	—	42.5	—	25.8	ns
133	Column address valid to data valid (read)	$t_{AA}$	$1.5 \times T_C - 7.5$	—	67.5	—	42.5	ns
134	CAS deassertion to data not valid (read hold time)	$t_{OFF}$		0.0	—	0.0	—	ns
135	Last CAS assertion to RAS deassertion	$t_{RSH}$	$0.75 \times T_C - 4.0$	33.5	—	21.0	—	ns
136	Previous CAS deassertion to RAS deassertion	$t_{RHCP}$	$2 \times T_C - 4.0$	96.0	—	62.7	—	ns
137	CAS assertion pulse width	$t_{CAS}$	$0.75 \times T_C - 4.0$	33.5	—	21.0	—	ns
138	Last CAS deassertion to RAS deassertion <sup>4</sup>	$t_{CRP}$	$1.75 \times T_C - 6.0$	81.5	—	52.3	—	ns
	• BRW[1:0] = 00		$3.25 \times T_C - 6.0$	156.5	—	102.2	—	ns
	• BRW[1:0] = 01		$4.25 \times T_C - 6.0$	206.5	—	135.5	—	ns
	• BRW[1:0] = 10		$6.25 \times T_C - 6.0$	306.5	—	202.1	—	ns
139	CAS deassertion pulse width	$t_{CP}$	$0.5 \times T_C - 4.0$	21.0	—	12.7	—	ns
140	Column address valid to CAS assertion	$t_{ASC}$	$0.5 \times T_C - 4.0$	21.0	—	12.7	—	ns
141	CAS assertion to column address not valid	$t_{CAH}$	$0.75 \times T_C - 4.0$	33.5	—	21.0	—	ns
142	Last column address valid to RAS deassertion	$t_{RAL}$	$2 \times T_C - 4.0$	96.0	—	62.7	—	ns

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-9 DRAM Page Mode Timings, One Wait State (Low-Power Applications)<sup>1, 2, 3</sup>**

No.	Characteristics	Symbol	Expression	20 MHz <sup>6</sup>		30 MHz <sup>6</sup>		Unit
				Min	Max	Min	Max	
143	$\overline{WR}$ deassertion to $\overline{CAS}$ assertion	$t_{RCS}$	$0.75 \times T_C - 3.8$	33.7	—	21.2	—	ns
144	$\overline{CAS}$ deassertion to $\overline{WR}$ assertion	$t_{RCH}$	$0.25 \times T_C - 3.7$	8.8	—	4.6	—	ns
145	$\overline{CAS}$ assertion to $\overline{WR}$ deassertion	$t_{WCH}$	$0.5 \times T_C - 4.2$	20.8	—	12.5	—	ns
146	$\overline{WR}$ assertion pulse width	$t_{WP}$	$1.5 \times T_C - 4.5$	70.5	—	45.5	—	ns
147	Last $\overline{WR}$ assertion to $\overline{RAS}$ deassertion	$t_{RWL}$	$1.75 \times T_C - 4.3$	83.2	—	54.0	—	ns
148	$\overline{WR}$ assertion to $\overline{CAS}$ deassertion	$t_{CWL}$	$1.75 \times T_C - 4.3$	83.2	—	54.0	—	ns
149	Data valid to $\overline{CAS}$ assertion (Write)	$t_{DS}$	$0.25 \times T_C - 4.0$	8.5	—	4.3	—	ns
150	$\overline{CAS}$ assertion to data not valid (write)	$t_{DH}$	$0.75 \times T_C - 4.0$	33.5	—	21.0	—	ns
151	$\overline{WR}$ assertion to $\overline{CAS}$ assertion	$t_{WCS}$	$T_C - 4.3$	45.7	—	29.0	—	ns
152	Last $\overline{RD}$ assertion to $\overline{RAS}$ deassertion	$t_{ROH}$	$1.5 \times T_C - 4.0$	71.0	—	46.0	—	ns
153	$\overline{RD}$ assertion to data valid	$t_{GA}$	$T_C - 7.5$	—	42.5	—	25.8	ns
154	$\overline{RD}$ deassertion to data not valid <sup>5</sup>	$t_{GZ}$		0.0	—	0.0	—	ns
155	$\overline{WR}$ assertion to data active		$0.75 \times T_C - 0.3$	37.2	—	24.7	—	ns
156	$\overline{WR}$ deassertion to data high impedance		$0.25 \times T_C$	—	12.5	—	8.3	ns

- Notes:
- The number of wait states for Page mode access is specified in the DCR.
  - The refresh period is specified in the DCR.
  - All the timings are calculated for the worst case. Some of the timings are better for specific cases (e.g.,  $t_{PC}$  equals  $2 \times T_C$  for read-after-read or write-after-write sequences).
  - BRW[1:0] (DRAM control register bits) defines the number of wait states that should be inserted in each DRAM out-of-page access.
  - $\overline{RD}$  deassertion will always occur after  $\overline{CAS}$  deassertion; therefore, the restricted timing is  $t_{OFF}$  and not  $t_{GZ}$ .
  - Reduced DSP clock speed allows use of Page Mode DRAM with one Wait state (See Figure 2-14.).

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-10 DRAM Page Mode Timings, Two Wait States<sup>1, 2, 3, 7</sup>**

No.	Characteristics	Symbol	Expression	66 MHz		80 MHz		Unit
				Min	Max	Min	Max	
131	Page mode cycle time for two consecutive accesses of the same direction	$t_{PC}$	$2 \times T_C$	45.4	—	37.5	—	ns
	Page mode cycle time for mixed (read and write) accesses		$1.25 \times T_C$	41.1	—	34.4	—	
132	CAS assertion to data valid (read)	$t_{CAC}$	$1.5 \times T_C - 7.5$ $1.5 \times T_C - 6.5$	— —	15.2 —	— —	12.3	ns
133	Column address valid to data valid (read)	$t_{AA}$	$2.5 \times T_C - 7.5$ $2.5 \times T_C - 6.5$	— —	30.4 —	— —	24.8	ns
134	CAS deassertion to data not valid (read hold time)	$t_{OFF}$		0.0	—	0.0	—	ns
135	Last CAS assertion to RAS deassertion	$t_{RSH}$	$1.75 \times T_C - 4.0$	22.5	—	17.9	—	ns
136	Previous CAS deassertion to RAS deassertion	$t_{RHCP}$	$3.25 \times T_C - 4.0$	45.2	—	36.6	—	ns
137	CAS assertion pulse width	$t_{CAS}$	$1.5 \times T_C - 4.0$	18.7	—	14.8	—	ns
138	Last CAS deassertion to RAS deassertion <sup>5</sup> • BRW[1:0] = 00 • BRW[1:0] = 01 • BRW[1:0] = 10 • BRW[1:0] = 11	$t_{CRP}$	$2.0 \times T_C - 6.0$	24.4	—	19.0	—	ns
			$3.5 \times T_C - 6.0$	47.2	—	37.8	—	ns
			$4.5 \times T_C - 6.0$	62.4	—	50.3	—	ns
			$6.5 \times T_C - 6.0$	92.8	—	75.3	—	ns
139	CAS deassertion pulse width	$t_{CP}$	$1.25 \times T_C - 4.0$	14.9	—	11.6	—	ns
140	Column address valid to CAS assertion	$t_{ASC}$	$T_C - 4.0$	11.2	—	8.5	—	ns
141	CAS assertion to column address not valid	$t_{CAH}$	$1.75 \times T_C - 4.0$	22.5	—	17.9	—	ns

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-10 DRAM Page Mode Timings, Two Wait States<sup>1, 2, 3, 7</sup> (continued)**

No.	Characteristics	Symbol	Expression	66 MHz		80 MHz		Unit
				Min	Max	Min	Max	
142	Last column address valid to RAS deassertion	t <sub>RAL</sub>	$3 \times T_C - 4.0$	41.5	—	33.5	—	ns
143	WR deassertion to CAS assertion	t <sub>RCS</sub>	$1.25 \times T_C - 3.8$	15.1	—	11.8	—	ns
144	CAS deassertion to WR assertion	t <sub>RCH</sub>	$0.5 \times T_C - 3.7$	3.9	—	2.6	—	ns
145	CAS assertion to WR deassertion	t <sub>WCH</sub>	$1.5 \times T_C - 4.2$	18.5	—	14.6	—	ns
146	WR assertion pulse width	t <sub>WP</sub>	$2.5 \times T_C - 4.5$	33.5	—	26.8	—	ns
147	Last WR assertion to RAS deassertion	t <sub>RWL</sub>	$2.75 \times T_C - 4.3$	33.4	—	26.8	—	ns
148	WR assertion to CAS deassertion	t <sub>CWL</sub>	$2.5 \times T_C - 4.3$	33.6	—	27.0	—	ns
149	Data valid to CAS assertion (write)	t <sub>DS</sub>	$0.25 \times T_C - 3.7$ $0.25 \times T_C - 3.0$	0.1 —	— —	— 0.1	— —	ns ns
150	CAS assertion to data not valid (write)	t <sub>DH</sub>	$1.75 \times T_C - 4.0$	22.5	—	17.9	—	ns
151	WR assertion to CAS assertion	t <sub>WCS</sub>	$T_C - 4.3$	10.9	—	8.2	—	ns
152	Last RD assertion to RAS deassertion	t <sub>ROH</sub>	$2.5 \times T_C - 4.0$	33.9	—	27.3	—	ns
153	RD assertion to data valid	t <sub>GA</sub>	$1.75 \times T_C - 7.5$ $1.75 \times T_C - 6.5$	— —	19.0 —	— —	— 15.4	ns ns
154	RD deassertion to data not valid <sup>6</sup>	t <sub>GZ</sub>		0.0	—	0.0	—	ns
155	WR assertion to data active		$0.75 \times T_C - 0.3$	11.1	—	9.1	—	ns
156	WR deassertion to data high impedance		$0.25 \times T_C$	—	3.8	—	3.1	ns

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-10 DRAM Page Mode Timings, Two Wait States<sup>1, 2, 3, 7</sup> (continued)**

No.	Characteristics	Symbol	Expression	66 MHz		80 MHz		Unit
				Min	Max	Min	Max	
Notes:								
1.	The number of wait states for Page mode access is specified in the DCR.							
2.	The refresh period is specified in the DCR.							
3.	The asynchronous delays specified in the expressions are valid for DSP56364.							
4.	All the timings are calculated for the worst case. Some of the timings are better for specific cases (e.g., $t_{PC}$ equals $3 \times T_C$ for read-after-read or write-after-write sequences).							
5.	BRW[1:0] (DRAM Control Register bits) defines the number of wait states that should be inserted in each DRAM out-of-page access.							
6.	$\overline{RD}$ deassertion will always occur after $\overline{CAS}$ deassertion; therefore, the restricted timing is $t_{OFF}$ and not $t_{GZ}$ .							
7.	There are no DRAMs fast enough to fit to two wait states Page mode @ 100MHz (See Figure 2-11)							

**Table 2-11 DRAM Page Mode Timings, Three Wait States<sup>1, 2, 3</sup>**

No.	Characteristics	Symbol	Expression	Min	Max	Unit
131	Page mode cycle time for two consecutive accesses of the same direction Page mode cycle time for mixed (read and write) accesses	$t_{PC}$	$2 \times T_C$ $1.25 \times T_C$	40.0 35.0	— —	ns
132	$\overline{CAS}$ assertion to data valid (read)	$t_{CAC}$	$2 \times T_C - 7.0$	—	13.0	ns
133	Column address valid to data valid (read)	$t_{AA}$	$3 \times T_C - 7.0$	—	23.0	ns
134	$\overline{CAS}$ deassertion to data not valid (read hold time)	$t_{OFF}$		0.0	—	ns
135	Last $\overline{CAS}$ assertion to $\overline{RAS}$ deassertion	$t_{RSH}$	$2.5 \times T_C - 4.0$	21.0	—	ns
136	Previous $\overline{CAS}$ deassertion to $\overline{RAS}$ deassertion	$t_{RHCP}$	$4.5 \times T_C - 4.0$	41.0	—	ns
137	$\overline{CAS}$ assertion pulse width	$t_{CAS}$	$2 \times T_C - 4.0$	16.0	—	ns
138	Last $\overline{CAS}$ deassertion to $\overline{RAS}$ assertion <sup>5</sup> • BRW[1:0] = 00 • BRW[1:0] = 01 • BRW[1:0] = 10 • BRW[1:0] = 11	$t_{CRP}$	$2.25 \times T_C - 6.0$ $3.75 \times T_C - 6.0$ $4.75 \times T_C - 6.0$ $6.75 \times T_C - 6.0$	— — 41.5 61.5	— — — —	ns
139	$\overline{CAS}$ deassertion pulse width	$t_{CP}$	$1.5 \times T_C - 4.0$	11.0	—	ns
140	Column address valid to $\overline{CAS}$ assertion	$t_{ASC}$	$T_C - 4.0$	6.0	—	ns

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-11 DRAM Page Mode Timings, Three Wait States<sup>1, 2, 3</sup> (continued)**

No.	Characteristics	Symbol	Expression	Min	Max	Unit
141	CAS assertion to column address not valid	$t_{CAH}$	$2.5 \times T_C - 4.0$	21.0	—	ns
142	Last column address valid to RAS deassertion	$t_{RAL}$	$4 \times T_C - 4.0$	36.0	—	ns
143	WR deassertion to CAS assertion	$t_{RCS}$	$1.25 \times T_C - 4.0$	8.5	—	ns
144	CAS deassertion to WR assertion	$t_{RCH}$	$0.75 \times T_C - 4.0$	3.5	—	ns
145	CAS assertion to WR deassertion	$t_{WCH}$	$2.25 \times T_C - 4.2$	18.3	—	ns
146	WR assertion pulse width	$t_{WP}$	$3.5 \times T_C - 4.5$	30.5	—	ns
147	Last WR assertion to RAS deassertion	$t_{RWL}$	$3.75 \times T_C - 4.3$	33.2	—	ns
148	WR assertion to CAS deassertion	$t_{CWL}$	$3.25 \times T_C - 4.3$	28.2	—	ns
149	Data valid to CAS assertion (write)	$t_{DS}$	$0.5 \times T_C - 4.0$	1.0	—	ns
150	CAS assertion to data not valid (write)	$t_{DH}$	$2.5 \times T_C - 4.0$	21.0	—	ns
151	WR assertion to CAS assertion	$t_{WCS}$	$1.25 \times T_C - 4.3$	8.2	—	ns
152	Last RD assertion to RAS deassertion	$t_{ROH}$	$3.5 \times T_C - 4.0$	31.0	—	ns
153	RD assertion to data valid	$t_{GA}$	$2.5 \times T_C - 7.0$	—	18.0	ns
154	RD deassertion to data not valid <sup>6</sup>	$t_{GZ}$		0.0	—	ns
155	WR assertion to data active		$0.75 \times T_C - 0.3$	7.2	—	ns
156	WR deassertion to data high impedance		$0.25 \times T_C$	—	2.5	ns

Notes:

- The number of wait states for Page mode access is specified in the DCR.
- The refresh period is specified in the DCR.
- The asynchronous delays specified in the expressions are valid for DSP56364.
- All the timings are calculated for the worst case. Some of the timings are better for specific cases (e.g.,  $t_{PC}$  equals  $4 \times T_C$  for read-after-read or write-after-write sequences).
- BRW[1:0] (DRAM control register bits) defines the number of wait states that should be inserted in each DRAM out-of page-access.
- RD deassertion will always occur after CAS deassertion; therefore, the restricted timing is  $t_{OFF}$  and not  $t_{GZ}$ .

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-12 DRAM Page Mode Timings, Four Wait States<sup>1, 2, 3</sup>**

No.	Characteristics	Symbol	Expression	Min	Max	Unit
131	Page mode cycle time for two consecutive accesses of the same direction. Page mode cycle time for mixed (read and write) accesses.	$t_{PC}$	$2 \times T_C$ $1.25 \times T_C$	50.0 45.0	— —	ns
132	CAS assertion to data valid (read)	$t_{CAC}$	$2.75 \times T_C - 7.0$	—	20.5	ns
133	Column address valid to data valid (read)	$t_{AA}$	$3.75 \times T_C - 7.0$	—	30.5	ns
134	CAS deassertion to data not valid (read hold time)	$t_{OFF}$		0.0	—	ns
135	Last CAS assertion to RAS deassertion	$t_{RSH}$	$3.5 \times T_C - 4.0$	31.0	—	ns
136	Previous CAS deassertion to RAS deassertion	$t_{RHCP}$	$6 \times T_C - 4.0$	56.0	—	ns
137	CAS assertion pulse width	$t_{CAS}$	$2.5 \times T_C - 4.0$	21.0	—	ns
138	Last CAS deassertion to RAS assertion <sup>5</sup> • BRW[1:0] = 00 • BRW[1:0] = 01 • BRW[1:0] = 10 • BRW[1:0] = 11	$t_{CRP}$	$2.75 \times T_C - 6.0$ $4.25 \times T_C - 6.0$ $5.25 \times T_C - 6.0$ $7.25 \times T_C - 6.0$	— — 46.5 66.5	— — — —	ns
139	CAS deassertion pulse width	$t_{CP}$	$2 \times T_C - 4.0$	16.0	—	ns
140	Column address valid to CAS assertion	$t_{ASC}$	$T_C - 4.0$	6.0	—	ns
141	CAS assertion to column address not valid	$t_{CAH}$	$3.5 \times T_C - 4.0$	31.0	—	ns
142	Last column address valid to RAS deassertion	$t_{RAL}$	$5 \times T_C - 4.0$	46.0	—	ns
143	WR deassertion to CAS assertion	$t_{RCS}$	$1.25 \times T_C - 4.0$	8.5	—	ns
144	CAS deassertion to WR assertion	$t_{RCH}$	$1.25 \times T_C - 4.0$	8.5	—	ns
145	CAS assertion to WR deassertion	$t_{WCH}$	$3.25 \times T_C - 4.2$	28.3	—	ns
146	WR assertion pulse width	$t_{WP}$	$4.5 \times T_C - 4.5$	40.5	—	ns
147	Last WR assertion to RAS deassertion	$t_{RWL}$	$4.75 \times T_C - 4.3$	43.2	—	ns
148	WR assertion to CAS deassertion	$t_{CWL}$	$3.75 \times T_C - 4.3$	33.2	—	ns

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-12 DRAM Page Mode Timings, Four Wait States<sup>1, 2, 3</sup> (continued)**

No.	Characteristics	Symbol	Expression	Min	Max	Unit
149	Data valid to $\overline{\text{CAS}}$ assertion (write)	$t_{DS}$	$0.5 \times T_C - 4.0$	1.0	—	ns
150	$\overline{\text{CAS}}$ assertion to data not valid (write)	$t_{DH}$	$3.5 \times T_C - 4.0$	31.0	—	ns
151	$\overline{\text{WR}}$ assertion to $\overline{\text{CAS}}$ assertion	$t_{WCS}$	$1.25 \times T_C - 4.3$	8.2	—	ns
152	Last $\overline{\text{RD}}$ assertion to $\overline{\text{RAS}}$ deassertion	$t_{ROH}$	$4.5 \times T_C - 4.0$	41.0	—	ns
153	$\overline{\text{RD}}$ assertion to data valid	$t_{GA}$	$3.25 \times T_C - 7.0$	—	25.5	ns
154	$\overline{\text{RD}}$ deassertion to data not valid <sup>6</sup>	$t_{GZ}$		0.0	—	ns
155	$\overline{\text{WR}}$ assertion to data active		$0.75 \times T_C - 0.3$	7.2	—	ns
156	$\overline{\text{WR}}$ deassertion to data high impedance		$0.25 \times T_C$	—	2.5	ns

Notes:

1. The number of wait states for Page mode access is specified in the DCR.
2. The refresh period is specified in the DCR.
3. The asynchronous delays specified in the expressions are valid for DSP56364.
4. All the timings are calculated for the worst case. Some of the timings are better for specific cases (e.g.,  $t_{PC}$  equals  $3 \times T_C$  for read-after-read or write-after-write sequences).
5. BRW[1:0] (DRAM control register bits) defines the number of wait states that should be inserted in each DRAM out-of-page access.
6.  $\overline{\text{RD}}$  deassertion will always occur after  $\overline{\text{CAS}}$  deassertion; therefore, the restricted timing is  $t_{OFF}$  and not  $t_{GZ}$ .

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

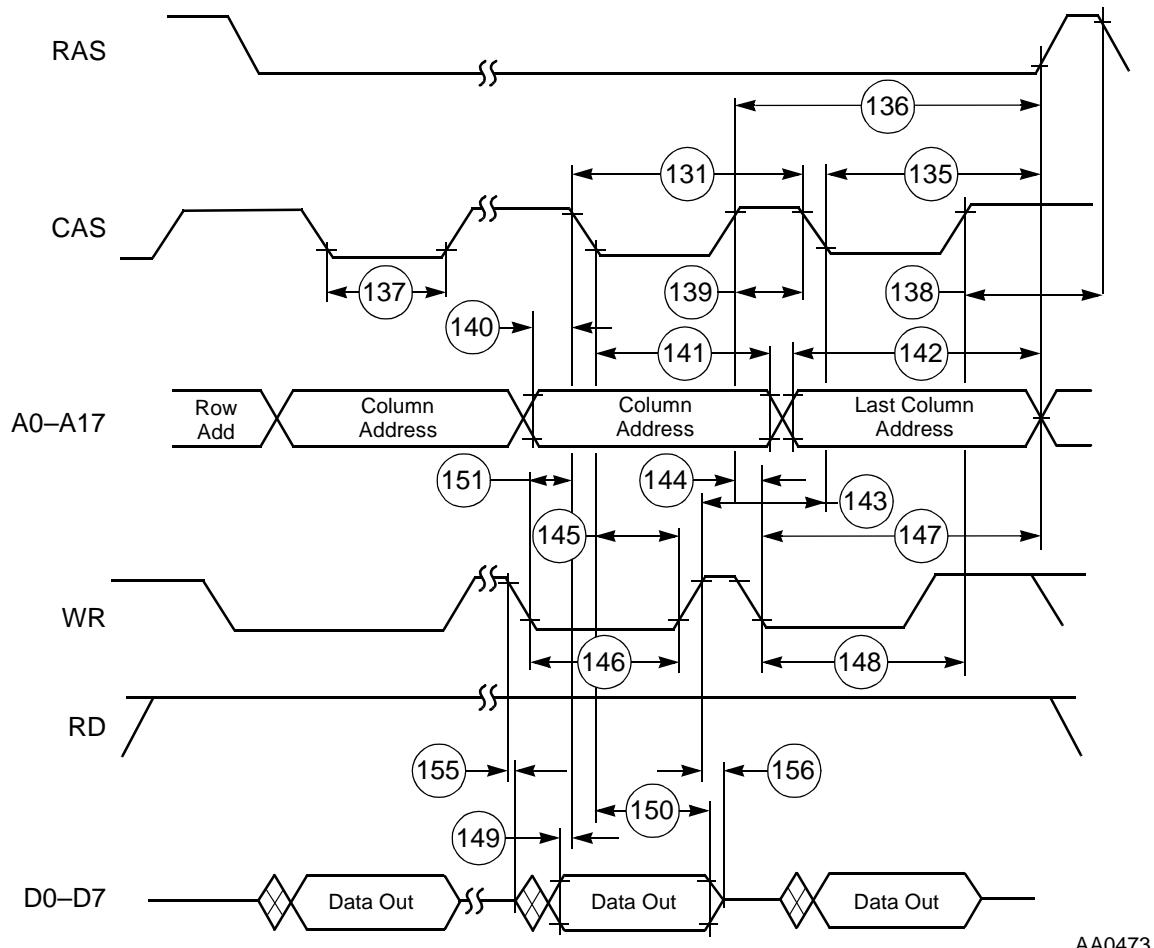


Figure 2-12 DRAM Page Mode Write Accesses

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### External Memory Expansion Port (Port A)

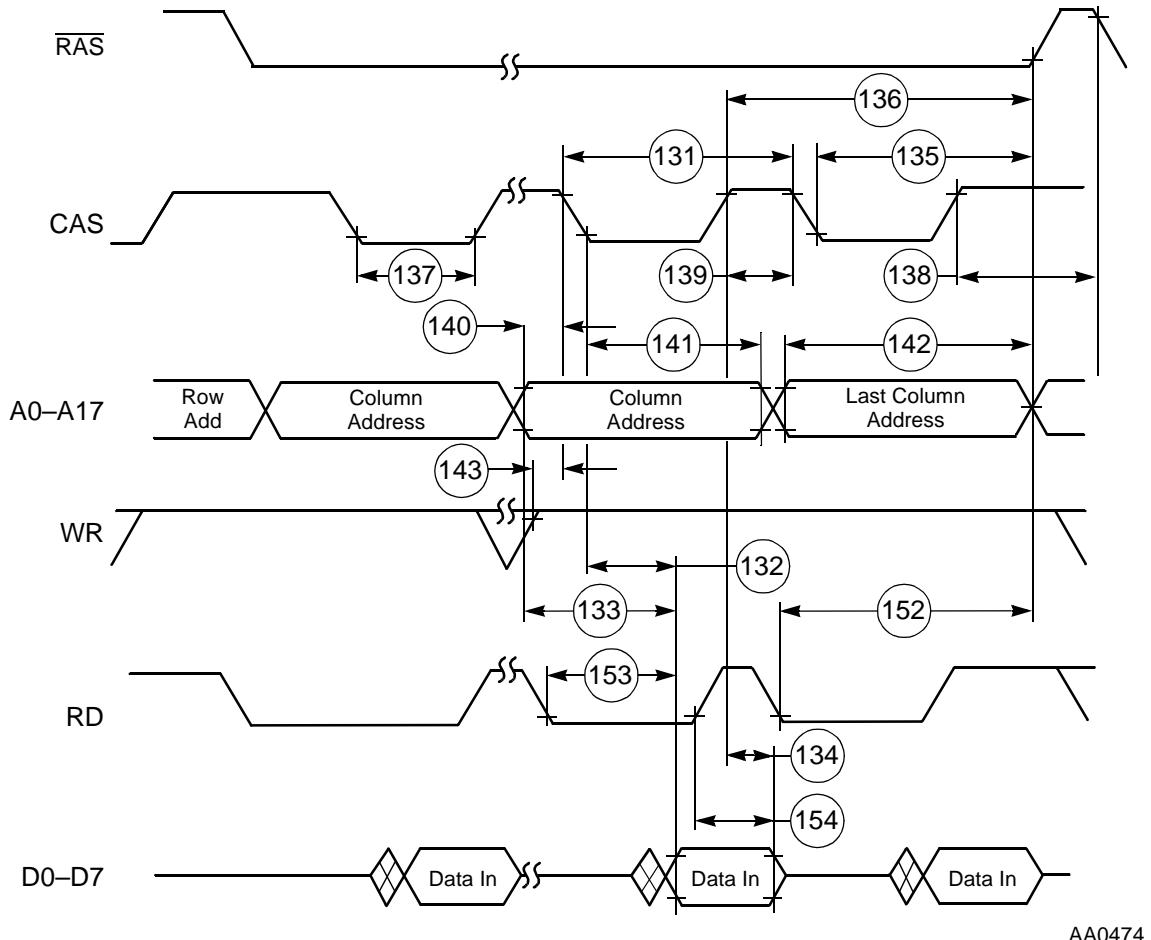
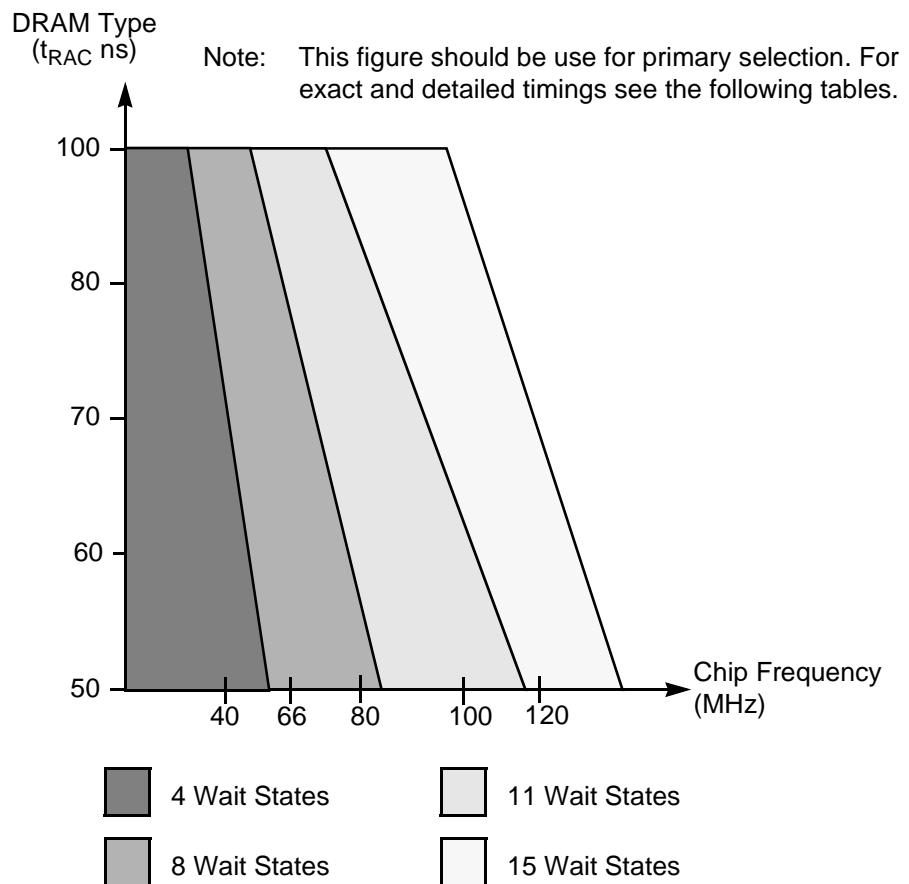


Figure 2-13 DRAM Page Mode Read Accesses

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## Specifications

### External Memory Expansion Port (Port A)



**Figure 2-14 DRAM Out-of-Page Wait States Selection Guide**

**Table 2-13 DRAM Out-of-Page and Refresh Timings, Four Wait States<sup>1, 2</sup>**

No.	Characteristics <sup>3</sup>	Symbol	Expression	20 MHz <sup>4</sup>		30 MHz <sup>4</sup>		Unit
				Min	Max	Min	Max	
157	Random read or write cycle time	t <sub>RC</sub>	5 × T <sub>C</sub>	250.0	—	166.7	—	ns
158	RAS assertion to data valid (read)	t <sub>RAC</sub>	2.75 × T <sub>C</sub> – 7.5	—	130.0	—	84.2	ns
159	CAS assertion to data valid (read)	t <sub>CAC</sub>	1.25 × T <sub>C</sub> – 7.5	—	55.0	—	34.2	ns
160	Column address valid to data valid (read)	t <sub>AA</sub>	1.5 × T <sub>C</sub> – 7.5	—	67.5	—	42.5	ns

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-13 DRAM Out-of-Page and Refresh Timings, Four Wait States<sup>1, 2</sup> (continued)**

No.	Characteristics <sup>3</sup>	Symbol	Expression	20 MHz <sup>4</sup>		30 MHz <sup>4</sup>		Unit
				Min	Max	Min	Max	
161	CAS deassertion to data not valid (read hold time)	t <sub>OFF</sub>		0.0	—	0.0	—	ns
162	RAS deassertion to RAS assertion	t <sub>RP</sub>	$1.75 \times T_C - 4.0$	83.5	—	54.3	—	ns
163	RAS assertion pulse width	t <sub>RAS</sub>	$3.25 \times T_C - 4.0$	158.5	—	104.3	—	ns
164	CAS assertion to RAS deassertion	t <sub>RSH</sub>	$1.75 \times T_C - 4.0$	83.5	—	54.3	—	ns
165	RAS assertion to CAS deassertion	t <sub>CSH</sub>	$2.75 \times T_C - 4.0$	133.5	—	87.7	—	ns
166	CAS assertion pulse width	t <sub>CAS</sub>	$1.25 \times T_C - 4.0$	58.5	—	37.7	—	ns
167	RAS assertion to CAS assertion	t <sub>RCD</sub>	$1.5 \times T_C \pm 2$	73.0	77.0	48.0	52.0	ns
168	RAS assertion to column address valid	t <sub>RAD</sub>	$1.25 \times T_C \pm 2$	60.5	64.5	39.7	43.7	ns
169	CAS deassertion to RAS assertion	t <sub>CRP</sub>	$2.25 \times T_C - 4.0$	108.5	—	71.0	—	ns
170	CAS deassertion pulse width	t <sub>CP</sub>	$1.75 \times T_C - 4.0$	83.5	—	54.3	—	ns
171	Row address valid to RAS assertion	t <sub>ASR</sub>	$1.75 \times T_C - 4.0$	83.5	—	54.3	—	ns
172	RAS assertion to row address not valid	t <sub>RAH</sub>	$1.25 \times T_C - 4.0$	58.5	—	37.7	—	ns
173	Column address valid to CAS assertion	t <sub>ASC</sub>	$0.25 \times T_C - 4.0$	8.5	—	4.3	—	ns
174	CAS assertion to column address not valid	t <sub>CAH</sub>	$1.75 \times T_C - 4.0$	83.5	—	54.3	—	ns
175	RAS assertion to column address not valid	t <sub>AR</sub>	$3.25 \times T_C - 4.0$	158.5	—	104.3	—	ns

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## Specifications

### External Memory Expansion Port (Port A)

**Table 2-13 DRAM Out-of-Page and Refresh Timings, Four Wait States<sup>1, 2</sup> (continued)**

No.	Characteristics <sup>3</sup>	Symbol	Expression	20 MHz <sup>4</sup>		30 MHz <sup>4</sup>		Unit
				Min	Max	Min	Max	
176	Column address valid to RAS deassertion	t <sub>RAL</sub>	$2 \times T_C - 4.0$	96.0	—	62.7	—	ns
177	WR deassertion to CAS assertion	t <sub>RCS</sub>	$1.5 \times T_C - 3.8$	71.2	—	46.2	—	ns
178	CAS deassertion to WR assertion	t <sub>RCH</sub>	$0.75 \times T_C - 3.7$	33.8	—	21.3	—	ns
179	RAS deassertion to WR assertion	t <sub>RRH</sub>	$0.25 \times T_C - 3.7$	8.8	—	4.6	—	ns
180	CAS assertion to WR deassertion	t <sub>WCH</sub>	$1.5 \times T_C - 4.2$	70.8	—	45.8	—	ns
181	RAS assertion to WR deassertion	t <sub>WCR</sub>	$3 \times T_C - 4.2$	145.8	—	95.8	—	ns
182	WR assertion pulse width	t <sub>WP</sub>	$4.5 \times T_C - 4.5$	220.5	—	145.5	—	ns
183	WR assertion to RAS deassertion	t <sub>RWL</sub>	$4.75 \times T_C - 4.3$	233.2	—	154.0	—	ns
184	WR assertion to CAS deassertion	t <sub>CWL</sub>	$4.25 \times T_C - 4.3$	208.2	—	137.4	—	ns
185	Data valid to CAS assertion (write)	t <sub>DS</sub>	$2.25 \times T_C - 4.0$	108.5	—	71.0	—	ns
186	CAS assertion to data not valid (write)	t <sub>DH</sub>	$1.75 \times T_C - 4.0$	83.5	—	54.3	—	ns
187	RAS assertion to data not valid (write)	t <sub>DHR</sub>	$3.25 \times T_C - 4.0$	158.5	—	104.3	—	ns
188	WR assertion to CAS assertion	t <sub>WCS</sub>	$3 \times T_C - 4.3$	145.7	—	95.7	—	ns
189	CAS assertion to RAS assertion (refresh)	t <sub>CSR</sub>	$0.5 \times T_C - 4.0$	21.0	—	12.7	—	ns
190	RAS deassertion to CAS assertion (refresh)	t <sub>RPC</sub>	$1.25 \times T_C - 4.0$	58.5	—	37.7	—	ns
191	RD assertion to RAS deassertion	t <sub>ROH</sub>	$4.5 \times T_C - 4.0$	221.0	—	146.0	—	ns

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-13 DRAM Out-of-Page and Refresh Timings, Four Wait States<sup>1, 2</sup> (continued)**

No.	Characteristics <sup>3</sup>	Symbol	Expression	20 MHz <sup>4</sup>		30 MHz <sup>4</sup>		Unit
				Min	Max	Min	Max	
192	$\overline{RD}$ assertion to data valid	$t_{GA}$	$4 \times T_C - 7.5$	—	192.5	—	125.8	ns
193	$\overline{RD}$ deassertion to data not valid <sup>3</sup>	$t_{GZ}$		0.0	—	0.0	—	ns
194	$\overline{WR}$ assertion to data active		$0.75 \times T_C - 0.3$	37.2	—	24.7	—	ns
195	$\overline{WR}$ deassertion to data high impedance		$0.25 \times T_C$	—	12.5	—	8.3	ns

Notes:

1. The number of wait states for out of page access is specified in the DCR.
2. The refresh period is specified in the DCR.
3.  $\overline{RD}$  deassertion will always occur after  $\overline{CAS}$  deassertion; therefore, the restricted timing is  $t_{OFF}$  and not  $t_{GZ}$ .
4. Reduced DSP clock speed allows use of DRAM out-of-page access with four Wait states (See Figure 2-17).

**Table 2-14 DRAM Out-of-Page and Refresh Timings, Eight Wait States<sup>1, 2</sup>**

No.	Characteristics <sup>4</sup>	Symbol	Expression <sup>3</sup>	66 MHz		80 MHz		Unit
				Min	Max	Min	Max	
157	Random read or write cycle time	$t_{RC}$	$9 \times T_C$	136.4	—	112.5	—	ns
158	$\overline{RAS}$ assertion to data valid (read)	$t_{RAC}$	$4.75 \times T_C - 7.5$	—	64.5	—	—	ns
			$4.75 \times T_C - 6.5$	—	—	—	52.9	ns
159	$\overline{CAS}$ assertion to data valid (read)	$t_{CAC}$	$2.25 \times T_C - 7.5$	—	26.6	—	—	ns
			$2.25 \times T_C - 6.5$	—	—	—	21.6	ns
160	Column address valid to data valid (read)	$t_{AA}$	$3 \times T_C - 7.5$	—	40.0	—	—	ns
			$3 \times T_C - 6.5$	—	—	—	31.0	ns
161	$\overline{CAS}$ deassertion to data not valid (read hold time)	$t_{OFF}$		0.0	—	0.0	—	ns

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## Specifications

### External Memory Expansion Port (Port A)

**Table 2-14 DRAM Out-of-Page and Refresh Timings, Eight Wait States<sup>1,2</sup> (continued)**

No.	Characteristics <sup>4</sup>	Symbol	Expression <sup>3</sup>	66 MHz		80 MHz		Unit
				Min	Max	Min	Max	
162	RAS deassertion to RAS assertion	t <sub>RP</sub>	$3.25 \times T_C - 4.0$	45.2	—	36.6	—	ns
163	RAS assertion pulse width	t <sub>RAS</sub>	$5.75 \times T_C - 4.0$	83.1	—	67.9	—	ns
164	CAS assertion to RAS deassertion	t <sub>RSH</sub>	$3.25 \times T_C - 4.0$	45.2	—	36.6	—	ns
165	RAS assertion to CAS deassertion	t <sub>CSH</sub>	$4.75 \times T_C - 4.0$	68.0	—	55.5	—	ns
166	CAS assertion pulse width	t <sub>CAS</sub>	$2.25 \times T_C - 4.0$	30.1	—	24.1	—	ns
167	RAS assertion to CAS assertion	t <sub>RCD</sub>	$2.5 \times T_C \pm 2$	35.9	39.9	29.3	33.3	ns
168	RAS assertion to column address valid	t <sub>RAD</sub>	$1.75 \times T_C \pm 2$	24.5	28.5	19.9	23.9	ns
169	CAS deassertion to RAS assertion	t <sub>CRP</sub>	$4.25 \times T_C - 4.0$	59.8	—	49.1	—	ns
170	CAS deassertion pulse width	t <sub>CP</sub>	$2.75 \times T_C - 4.0$	37.7	—	30.4	—	ns
171	Row address valid to RAS assertion	t <sub>ASR</sub>	$3.25 \times T_C - 4.0$	45.2	—	36.6	—	ns
172	RAS assertion to row address not valid	t <sub>RAH</sub>	$1.75 \times T_C - 4.0$	22.5	—	17.9	—	ns
173	Column address valid to CAS assertion	t <sub>ASC</sub>	$0.75 \times T_C - 4.0$	7.4	—	5.4	—	ns
174	CAS assertion to column address not valid	t <sub>CAH</sub>	$3.25 \times T_C - 4.0$	45.2	—	36.6	—	ns
175	RAS assertion to column address not valid	t <sub>AR</sub>	$5.75 \times T_C - 4.0$	83.1	—	67.9	—	ns
176	Column address valid to RAS deassertion	t <sub>RAL</sub>	$4 \times T_C - 4.0$	56.6	—	46.0	—	ns
177	WR deassertion to CAS assertion	t <sub>RCS</sub>	$2 \times T_C - 3.8$	26.5	—	21.2	—	ns

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-14 DRAM Out-of-Page and Refresh Timings, Eight Wait States<sup>1,2</sup> (continued)**

No.	Characteristics <sup>4</sup>	Symbol	Expression <sup>3</sup>	66 MHz		80 MHz		Unit
				Min	Max	Min	Max	
178	CAS deassertion to WR <sup>5</sup> assertion	t <sub>RCH</sub>	$1.25 \times T_C - 3.7$	15.2	—	11.9	—	ns
179	RAS deassertion to WR <sup>5</sup> assertion	t <sub>RRH</sub>	$0.25 \times T_C - 3.7$	0.1	—	—	—	ns
			$0.25 \times T_C - 3.0$	—	—	0.1	—	ns
180	CAS assertion to WR deassertion	t <sub>WCH</sub>	$3 \times T_C - 4.2$	41.3	—	33.3	—	ns
181	RAS assertion to WR deassertion	t <sub>WCR</sub>	$5.5 \times T_C - 4.2$	79.1	—	64.6	—	ns
182	WR assertion pulse width	t <sub>WP</sub>	$8.5 \times T_C - 4.5$	124.3	—	101.8	—	ns
183	WR assertion to RAS deassertion	t <sub>RWL</sub>	$8.75 \times T_C - 4.3$	128.3	—	105.1	—	ns
184	WR assertion to CAS deassertion	t <sub>CWL</sub>	$7.75 \times T_C - 4.3$	113.1	—	92.6	—	ns
185	Data valid to CAS assertion (write)	t <sub>DS</sub>	$4.75 \times T_C - 4.0$	68.0	—	55.4	—	ns
186	CAS assertion to data not valid (write)	t <sub>DH</sub>	$3.25 \times T_C - 4.0$	45.2	—	36.6	—	ns
187	RAS assertion to data not valid (write)	t <sub>DHR</sub>	$5.75 \times T_C - 4.0$	83.1	—	67.9	—	ns
188	WR assertion to CAS assertion	t <sub>WCS</sub>	$5.5 \times T_C - 4.3$	79.0	—	64.5	—	ns
189	CAS assertion to RAS assertion (refresh)	t <sub>CSR</sub>	$1.5 \times T_C - 4.0$	18.7	—	14.8	—	ns
190	RAS deassertion to CAS assertion (refresh)	t <sub>RPC</sub>	$1.75 \times T_C - 4.0$	22.5	—	17.9	—	ns
191	RD assertion to RAS deassertion	t <sub>ROH</sub>	$8.5 \times T_C - 4.0$	124.8	—	102.3	—	ns
192	RD assertion to data valid	t <sub>GA</sub>	$7.5 \times T_C - 7.5$	—	106.1	—	—	ns
			$7.5 \times T_C - 6.5$	—	—	—	87.3	ns

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-14 DRAM Out-of-Page and Refresh Timings, Eight Wait States<sup>1,2</sup> (continued)**

No.	Characteristics <sup>4</sup>	Symbol	Expression <sup>3</sup>	66 MHz		80 MHz		Unit
				Min	Max	Min	Max	
193	$\overline{\text{RD}}$ deassertion to data not valid <sup>4</sup>	$t_{GZ}$	0.0	0.0	—	0.0	—	ns
194	$\overline{\text{WR}}$ assertion to data active		$0.75 \times T_C - 0.3$	11.1	—	9.1	—	ns
195	$\overline{\text{WR}}$ deassertion to data high impedance		$0.25 \times T_C$	—	3.8	—	3.1	ns
Notes:								
1. The number of wait states for out-of-page access is specified in the DCR. 2. The refresh period is specified in the DCR. 3. The asynchronous delays specified in the expressions are valid for DSP56364. 4. $\overline{\text{RD}}$ deassertion will always occur after $\overline{\text{CAS}}$ deassertion; therefore, the restricted timing is $t_{OFF}$ and not $t_{GZ}$ . 5. Either $t_{RCH}$ or $t_{RRH}$ must be satisfied for read cycles.								

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## Specifications

### External Memory Expansion Port (Port A)

**Table 2-15 DRAM Out-of-Page and Refresh Timings, Eleven Wait States<sup>1, 2</sup>**

No.	Characteristics <sup>4</sup>	Symbol	Expression <sup>3</sup>	Min	Max	Unit
157	Random read or write cycle time	$t_{RC}$	$12 \times T_C$	120.0	—	ns
158	RAS assertion to data valid (read)	$t_{RAC}$	$6.25 \times T_C - 7.0$	—	55.5	ns
159	CAS assertion to data valid (read)	$t_{CAC}$	$3.75 \times T_C - 7.0$	—	30.5	ns
160	Column address valid to data valid (read)	$t_{AA}$	$4.5 \times T_C - 7.0$	—	38.0	ns
161	CAS deassertion to data not valid (read hold time)	$t_{OFF}$		0.0	—	ns
162	RAS deassertion to RAS assertion	$t_{RP}$	$4.25 \times T_C - 4.0$	38.5	—	ns
163	RAS assertion pulse width	$t_{RAS}$	$7.75 \times T_C - 4.0$	73.5	—	ns
164	CAS assertion to RAS deassertion	$t_{RSH}$	$5.25 \times T_C - 4.0$	48.5	—	ns
165	RAS assertion to CAS deassertion	$t_{CSH}$	$6.25 \times T_C - 4.0$	58.5	—	ns
166	CAS assertion pulse width	$t_{CAS}$	$3.75 \times T_C - 4.0$	33.5	—	ns
167	RAS assertion to CAS assertion	$t_{RCD}$	$2.5 \times T_C \pm 4.0$	21.0	29.0	ns
168	RAS assertion to column address valid	$t_{RAD}$	$1.75 \times T_C \pm 4.0$	13.5	21.5	ns
169	CAS deassertion to RAS assertion	$t_{CRP}$	$5.75 \times T_C - 4.0$	53.5	—	ns
170	CAS deassertion pulse width	$t_{CP}$	$4.25 \times T_C - 4.0$	38.5	—	ns
171	Row address valid to RAS assertion	$t_{ASR}$	$4.25 \times T_C - 4.0$	38.5	—	ns
172	RAS assertion to row address not valid	$t_{RAH}$	$1.75 \times T_C - 4.0$	13.5	—	ns
173	Column address valid to CAS assertion	$t_{ASC}$	$0.75 \times T_C - 4.0$	3.5	—	ns
174	CAS assertion to column address not valid	$t_{CAH}$	$5.25 \times T_C - 4.0$	48.5	—	ns
175	RAS assertion to column address not valid	$t_{AR}$	$7.75 \times T_C - 4.0$	73.5	—	ns
176	Column address valid to RAS deassertion	$t_{RAL}$	$6 \times T_C - 4.0$	56.0	—	ns
177	WR deassertion to CAS assertion	$t_{RCS}$	$3.0 \times T_C - 4.0$	26.0	—	ns
178	CAS deassertion to WR <sup>5</sup> assertion	$t_{RCH}$	$1.75 \times T_C - 4.0$	13.5	—	ns
179	RAS deassertion to WR <sup>5</sup> assertion	$t_{RRH}$	$0.25 \times T_C - 2.0$	0.5	—	ns

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-15 DRAM Out-of-Page and Refresh Timings, Eleven Wait States<sup>1, 2</sup> (continued)**

No.	Characteristics <sup>4</sup>	Symbol	Expression <sup>3</sup>	Min	Max	Unit
180	CAS assertion to WR deassertion	$t_{WCH}$	$5 \times T_C - 4.2$	45.8	—	ns
181	RAS assertion to WR deassertion	$t_{WCR}$	$7.5 \times T_C - 4.2$	70.8	—	ns
182	WR assertion pulse width	$t_{WP}$	$11.5 \times T_C - 4.5$	110.5	—	ns
183	WR assertion to RAS deassertion	$t_{RWL}$	$11.75 \times T_C - 4.3$	113.2	—	ns
184	WR assertion to CAS deassertion	$t_{CWL}$	$10.25 \times T_C - 4.3$	103.2	—	ns
185	Data valid to CAS assertion (write)	$t_{DS}$	$5.75 \times T_C - 4.0$	53.5	—	ns
186	CAS assertion to data not valid (write)	$t_{DH}$	$5.25 \times T_C - 4.0$	48.5	—	ns
187	RAS assertion to data not valid (write)	$t_{DHR}$	$7.75 \times T_C - 4.0$	73.5	—	ns
188	WR assertion to CAS assertion	$t_{WCS}$	$6.5 \times T_C - 4.3$	60.7	—	ns
189	CAS assertion to RAS assertion (refresh)	$t_{CSR}$	$1.5 \times T_C - 4.0$	11.0	—	ns
190	RAS deassertion to CAS assertion (refresh)	$t_{RPC}$	$2.75 \times T_C - 4.0$	23.5	—	ns
191	RD assertion to RAS deassertion	$t_{ROH}$	$11.5 \times T_C - 4.0$	111.0	—	ns
192	RD assertion to data valid	$t_{GA}$	$10 \times T_C - 7.0$	—	93.0	ns
193	RD deassertion to data not valid <sup>4</sup>	$t_{GZ}$		0.0	—	ns
194	WR assertion to data active		$0.75 \times T_C - 0.3$	7.2	—	ns
195	WR deassertion to data high impedance		$0.25 \times T_C$	—	2.5	ns

Notes:

- The number of wait states for out-of-page access is specified in the DCR.
- The refresh period is specified in the DCR.
- The asynchronous delays specified in the expressions are valid for DSP56364.
- RD deassertion will always occur after CAS deassertion; therefore, the restricted timing is  $t_{OFF}$  and not  $t_{GZ}$ .
- Either  $t_{RCH}$  or  $t_{RRH}$  must be satisfied for read cycles.

# Freescale Semiconductor, Inc.

## Specifications

### External Memory Expansion Port (Port A)

**Table 2-16 DRAM Out-of-Page and Refresh Timings, Fifteen Wait States<sup>1, 2</sup>**

No.	Characteristics <sup>3</sup>	Symbol	Expression	Min	Max	Unit
157	Random read or write cycle time	$t_{RC}$	$16 \times T_C$	160.0	—	ns
158	$\overline{RAS}$ assertion to data valid (read)	$t_{RAC}$	$8.25 \times T_C - 5.7$	—	76.8	ns
159	$\overline{CAS}$ assertion to data valid (read)	$t_{CAC}$	$4.75 \times T_C - 5.7$	—	41.8	ns
160	Column address valid to data valid (read)	$t_{AA}$	$5.5 \times T_C - 5.7$	—	49.3	ns
161	$\overline{CAS}$ deassertion to data not valid (read hold time)	$t_{OFF}$	0.0	0.0	—	ns
162	$\overline{RAS}$ deassertion to $\overline{RAS}$ assertion	$t_{RP}$	$6.25 \times T_C - 4.0$	58.5	—	ns
163	$\overline{RAS}$ assertion pulse width	$t_{RAS}$	$9.75 \times T_C - 4.0$	93.5	—	ns
164	$\overline{CAS}$ assertion to $\overline{RAS}$ deassertion	$t_{RSH}$	$6.25 \times T_C - 4.0$	58.5	—	ns
165	$\overline{RAS}$ assertion to $\overline{CAS}$ deassertion	$t_{CSH}$	$8.25 \times T_C - 4.0$	78.5	—	ns
166	$\overline{CAS}$ assertion pulse width	$t_{CAS}$	$4.75 \times T_C - 4.0$	43.5	—	ns
167	$\overline{RAS}$ assertion to $\overline{CAS}$ assertion	$t_{RCD}$	$3.5 \times T_C \pm 2$	33.0	37.0	ns
168	$\overline{RAS}$ assertion to column address valid	$t_{RAD}$	$2.75 \times T_C \pm 2$	25.5	29.5	ns
169	$\overline{CAS}$ deassertion to $\overline{RAS}$ assertion	$t_{CRP}$	$7.75 \times T_C - 4.0$	73.5	—	ns
170	$\overline{CAS}$ deassertion pulse width	$t_{CP}$	$6.25 \times T_C - 4.0$	58.5	—	ns
171	Row address valid to $\overline{RAS}$ assertion	$t_{ASR}$	$6.25 \times T_C - 4.0$	58.5	—	ns
172	$\overline{RAS}$ assertion to row address not valid	$t_{RAH}$	$2.75 \times T_C - 4.0$	23.5	—	ns
173	Column address valid to $\overline{CAS}$ assertion	$t_{ASC}$	$0.75 \times T_C - 4.0$	3.5	—	ns
174	$\overline{CAS}$ assertion to column address not valid	$t_{CAH}$	$6.25 \times T_C - 4.0$	58.5	—	ns
175	$\overline{RAS}$ assertion to column address not valid	$t_{AR}$	$9.75 \times T_C - 4.0$	93.5	—	ns
176	Column address valid to $\overline{RAS}$ deassertion	$t_{RAL}$	$7 \times T_C - 4.0$	66.0	—	ns
177	$\overline{WR}$ deassertion to $\overline{CAS}$ assertion	$t_{RCS}$	$5 \times T_C - 3.8$	46.2	—	ns
178	$\overline{CAS}$ deassertion to $\overline{WR}^5$ assertion	$t_{RCH}$	$1.75 \times T_C - 3.7$	13.8	—	ns
179	$\overline{RAS}$ deassertion to $\overline{WR}^5$ assertion	$t_{RRH}$	$0.25 \times T_C - 2.0$	0.5	—	ns

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## Specifications

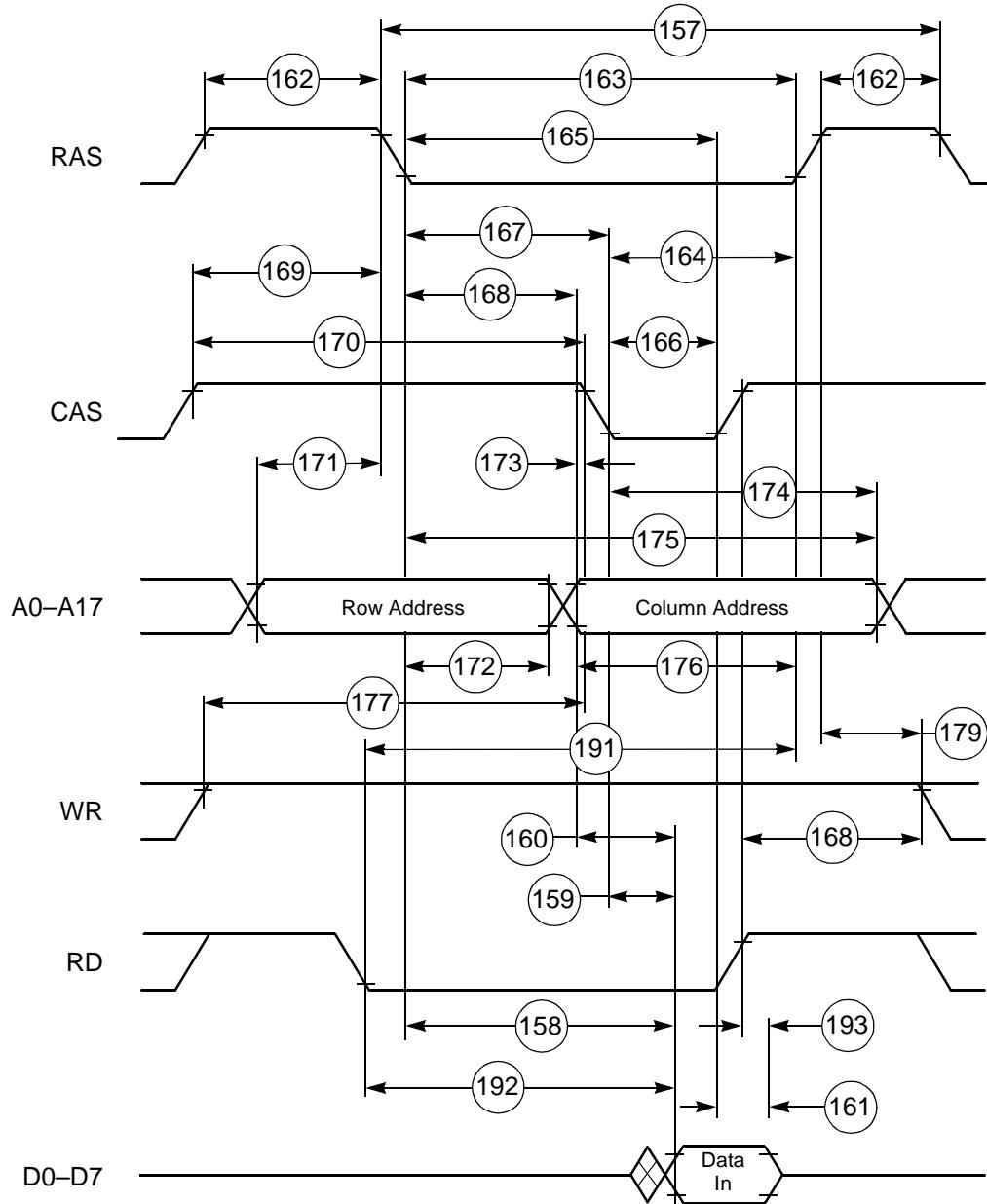
### External Memory Expansion Port (Port A)

**Table 2-16 DRAM Out-of-Page and Refresh Timings, Fifteen Wait States<sup>1, 2</sup> (continued)**

No.	Characteristics <sup>3</sup>	Symbol	Expression	Min	Max	Unit
180	CAS assertion to $\overline{\text{WR}}$ deassertion	$t_{WCH}$	$6 \times T_C - 4.2$	55.8	—	ns
181	$\overline{\text{RAS}}$ assertion to $\overline{\text{WR}}$ deassertion	$t_{WCR}$	$9.5 \times T_C - 4.2$	90.8	—	ns
182	$\overline{\text{WR}}$ assertion pulse width	$t_{WP}$	$15.5 \times T_C - 4.5$	150.5	—	ns
183	$\overline{\text{WR}}$ assertion to $\overline{\text{RAS}}$ deassertion	$t_{RWL}$	$15.75 \times T_C - 4.3$	153.2	—	ns
184	$\overline{\text{WR}}$ assertion to $\overline{\text{CAS}}$ deassertion	$t_{CWL}$	$14.25 \times T_C - 4.3$	138.2	—	ns
185	Data valid to $\overline{\text{CAS}}$ assertion (write)	$t_{DS}$	$8.75 \times T_C - 4.0$	83.5	—	ns
186	CAS assertion to data not valid (write)	$t_{DH}$	$6.25 \times T_C - 4.0$	58.5	—	ns
187	$\overline{\text{RAS}}$ assertion to data not valid (write)	$t_{DHR}$	$9.75 \times T_C - 4.0$	93.5	—	ns
188	$\overline{\text{WR}}$ assertion to $\overline{\text{CAS}}$ assertion	$t_{WCS}$	$9.5 \times T_C - 4.3$	90.7	—	ns
189	CAS assertion to $\overline{\text{RAS}}$ assertion (refresh)	$t_{CSR}$	$1.5 \times T_C - 4.0$	11.0	—	ns
190	$\overline{\text{RAS}}$ deassertion to $\overline{\text{CAS}}$ assertion (refresh)	$t_{RPC}$	$4.75 \times T_C - 4.0$	43.5	—	ns
191	$\overline{\text{RD}}$ assertion to $\overline{\text{RAS}}$ deassertion	$t_{ROH}$	$15.5 \times T_C - 4.0$	151.0	—	ns
192	$\overline{\text{RD}}$ assertion to data valid	$t_{GA}$	$14 \times T_C - 5.7$	—	134.3	ns
193	$\overline{\text{RD}}$ deassertion to data not valid <sup>3</sup>	$t_{GZ}$		0.0	—	ns
194	$\overline{\text{WR}}$ assertion to data active		$0.75 \times T_C - 0.3$	7.2	—	ns
195	$\overline{\text{WR}}$ deassertion to data high impedance		$0.25 \times T_C$	—	2.5	ns

- Notes:
1. The number of wait states for out-of-page access is specified in the DCR.
  2. The refresh period is specified in the DCR.
  3.  $\overline{\text{RD}}$  deassertion will always occur after  $\overline{\text{CAS}}$  deassertion; therefore, the restricted timing is  $t_{OFF}$  and not  $t_{GZ}$ .
  4. Either  $t_{RCH}$  or  $t_{RRH}$  must be satisfied for read cycles.

## **External Memory Expansion Port (Port A)**



**Figure 2-15 DRAM Out-of-Page Read Access**

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## Specifications

### External Memory Expansion Port (Port A)

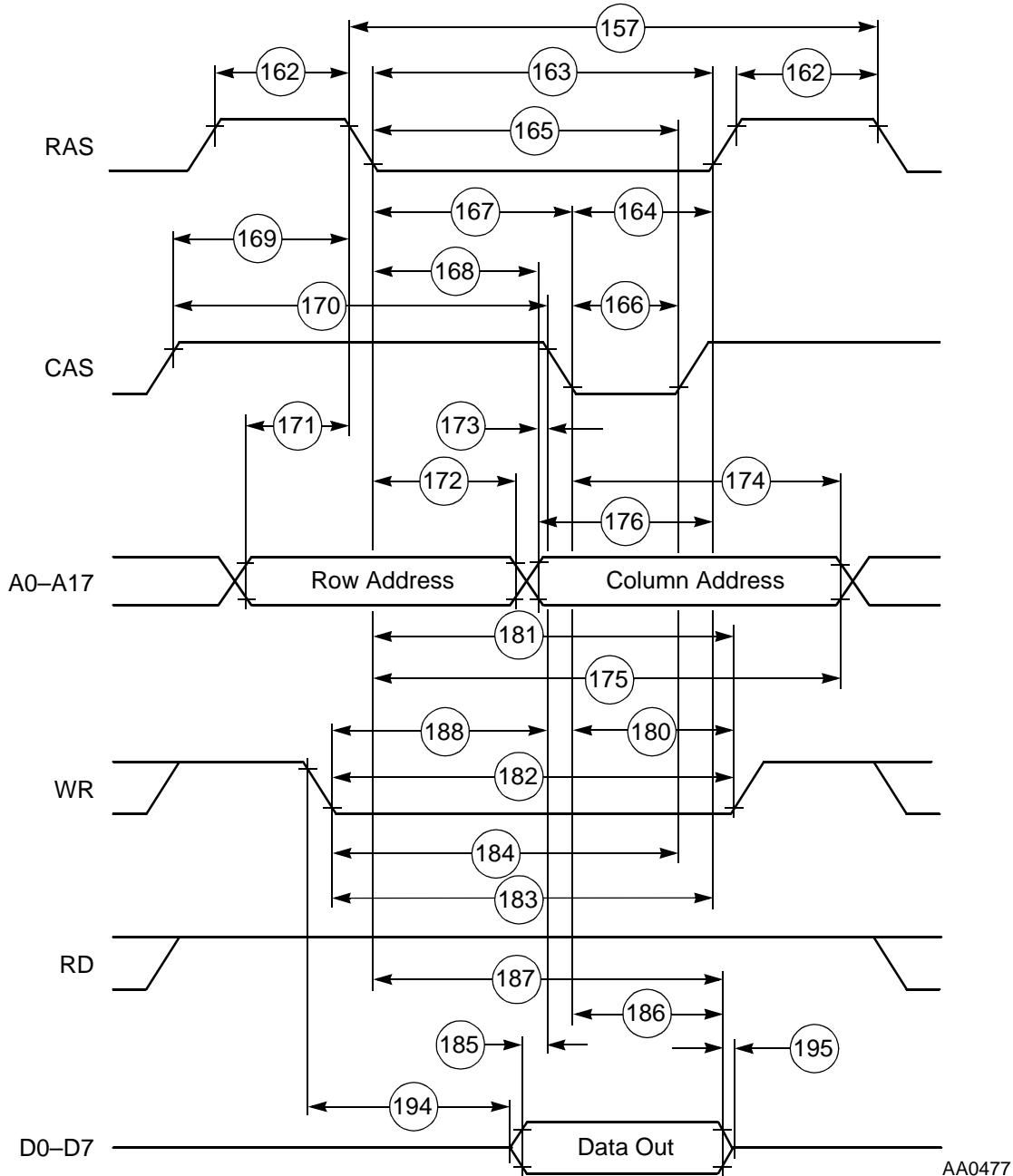
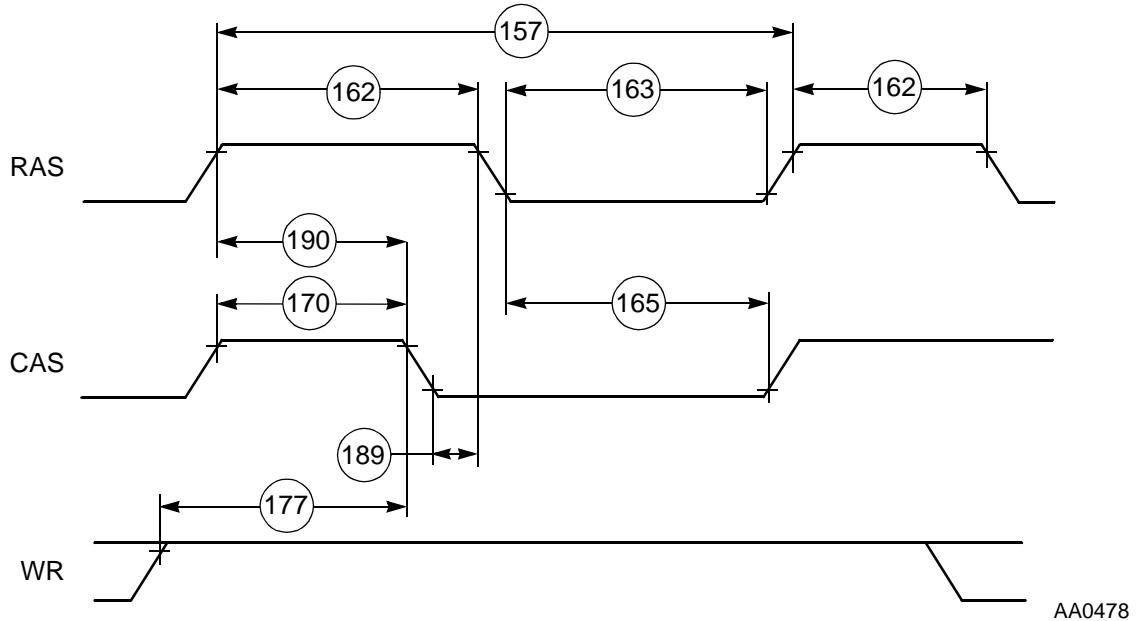


Figure 2-16 DRAM Out-of-Page Write Access

**External Memory Expansion Port (Port A)****Figure 2-17 DRAM Refresh Access**

# Freescale Semiconductor, Inc.

## Specifications

### Serial Host Interface SPI Protocol Timing

## 2.11 SERIAL HOST INTERFACE SPI PROTOCOL TIMING

Table 2-17 Serial Host Interface SPI Protocol Timing

No.	Characteristics	Mode	Filter Mode	Expression	Min	Max	Unit
140	Tolerable spike width on clock or data in	—	Bypassed	—	—	0	ns
			Narrow	—	—	50	ns
			Wide	—	—	100	ns
141	Minimum serial clock cycle = $t_{SPICC(min)}$	Master	Bypassed	$6 \times T_C + 46$	106	—	ns
			Narrow	$6 \times T_C + 152$	212	—	ns
			Wide	$6 \times T_C + 223$	283	—	ns
142	Serial clock high period	Master	Bypassed	$0.5 \times t_{SPICC} - 10$	43	—	ns
			Narrow	$0.5 \times t_{SPICC} - 10$	96	—	ns
			Wide	$0.5 \times t_{SPICC} - 10$	131	—	ns
		Slave	Bypassed	$2.5 \times T_C + 12$	37	—	ns
			Narrow	$2.5 \times T_C + 102$	127	—	ns
			Wide	$2.5 \times T_C + 189$	214	—	ns
143	Serial clock low period	Master	Bypassed	$0.5 \times t_{SPICC} - 10$	43	—	ns
			Narrow	$0.5 \times t_{SPICC} - 10$	96	—	ns
			Wide	$0.5 \times t_{SPICC} - 10$	131	—	ns
		Slave	Bypassed	$2.5 \times T_C + 12$	37	—	ns
			Narrow	$2.5 \times T_C + 102$	127	—	ns
			Wide	$2.5 \times T_C + 189$	214	—	ns
144	Serial clock rise/fall time	Master	—	—	—	10	ns
		Slave	—	—	—	2000	ns

# Freescale Semiconductor, Inc.

## Specifications

### Serial Host Interface SPI Protocol Timing

**Table 2-17 Serial Host Interface SPI Protocol Timing (continued)**

No.	Characteristics	Mode	Filter Mode	Expression	Min	Max	Unit
146	$\overline{SS}$ assertion to first SCK edge CPHA = 0	Slave	Bypassed	$3.5 \times T_C + 15$	50	—	ns
			Narrow	0	0	—	ns
			Wide	0	0	—	ns
	CPHA = 1	Slave	Bypassed	10	10	—	ns
			Narrow	0	0	—	ns
			Wide	0	0	—	ns
147	Last SCK edge to $\overline{SS}$ not asserted	Slave	Bypassed	12	12	—	ns
			Narrow	102	102	—	ns
			Wide	189	189	—	ns
148	Data input valid to SCK edge (data input set-up time)	Master/ Slave	Bypassed	0	0	—	ns
			Narrow	$\text{MAX}\{(20-T_C), 0\}$	10	—	ns
			Wide	$\text{MAX}\{(40-T_C), 0\}$	30	—	ns
149	SCK last sampling edge to data input not valid	Master/ Slave	Bypassed	$2.5 \times T_C + 10$	35	—	ns
			Narrow	$2.5 \times T_C + 30$	55	—	ns
			Wide	$2.5 \times T_C + 50$	75	—	ns
150	$\overline{SS}$ assertion to data out active	Slave	—	2	2	—	ns
151	$\overline{SS}$ deassertion to data high impedance	Slave	—	9	—	9	ns
152	SCK edge to data out valid (data out delay time)	Master/ Slave	Bypassed	$2 \times T_C + 33$	—	53	ns
			Narrow	$2 \times T_C + 123$	—	143	ns
			Wide	$2 \times T_C + 210$	—	230	ns

# Freescale Semiconductor, Inc.

## Specifications

### Serial Host Interface SPI Protocol Timing

**Table 2-17 Serial Host Interface SPI Protocol Timing (continued)**

No.	Characteristics	Mode	Filter Mode	Expression	Min	Max	Unit
153	SCK edge to data out not valid (data out hold time)	Master/ Slave	Bypassed	$T_C+5$	15	—	ns
			Narrow	$T_C+55$	65	—	ns
			Wide	$T_C+106$	116	—	ns
154	SS assertion to data out valid (CPHA = 0)	Slave	—	$T_C+33$	—	43	ns
157	First SCK sampling edge to HREQ output deassertion	Slave	Bypassed	$2.5 \times T_C + 30$	—	55	ns
			Narrow	$2.5 \times T_C + 120$	—	145	ns
			Wide	$2.5 \times T_C + 217$	—	242	ns
158	Last SCK sampling edge to HREQ output not deasserted (CPHA = 1)	Slave	Bypassed	$2.5 \times T_C + 30$	55	—	ns
			Narrow	$2.5 \times T_C + 80$	105	—	ns
			Wide	$2.5 \times T_C + 136$	161	—	ns
159	SS deassertion to HREQ output not deasserted (CPHA = 0)	Slave	—	$2.5 \times T_C + 30$	55	—	ns
160	SS deassertion pulse width (CPHA = 0)	Slave	—	$T_C+6$	16	—	ns
161	HREQ in assertion to first SCK edge	Master	Bypassed	$0.5 \times t_{SPICC} + 2.5 \times T_C + 43$	121	—	ns
			Narrow	$0.5 \times t_{SPICC} + 2.5 \times T_C + 43$	174	—	ns
			Wide	$0.5 \times t_{SPICC} + 2.5 \times T_C + 43$	209	—	ns
162	HREQ in deassertion to last SCK sampling edge (HREQ in set-up time) (CPHA = 1)	Master	—	0	0	—	ns
163	First SCK edge to HREQ in not asserted (HREQ in hold time)	Master	—	0	0	—	ns

Note: Periodically sampled, not 100% tested

### Serial Host Interface SPI Protocol Timing

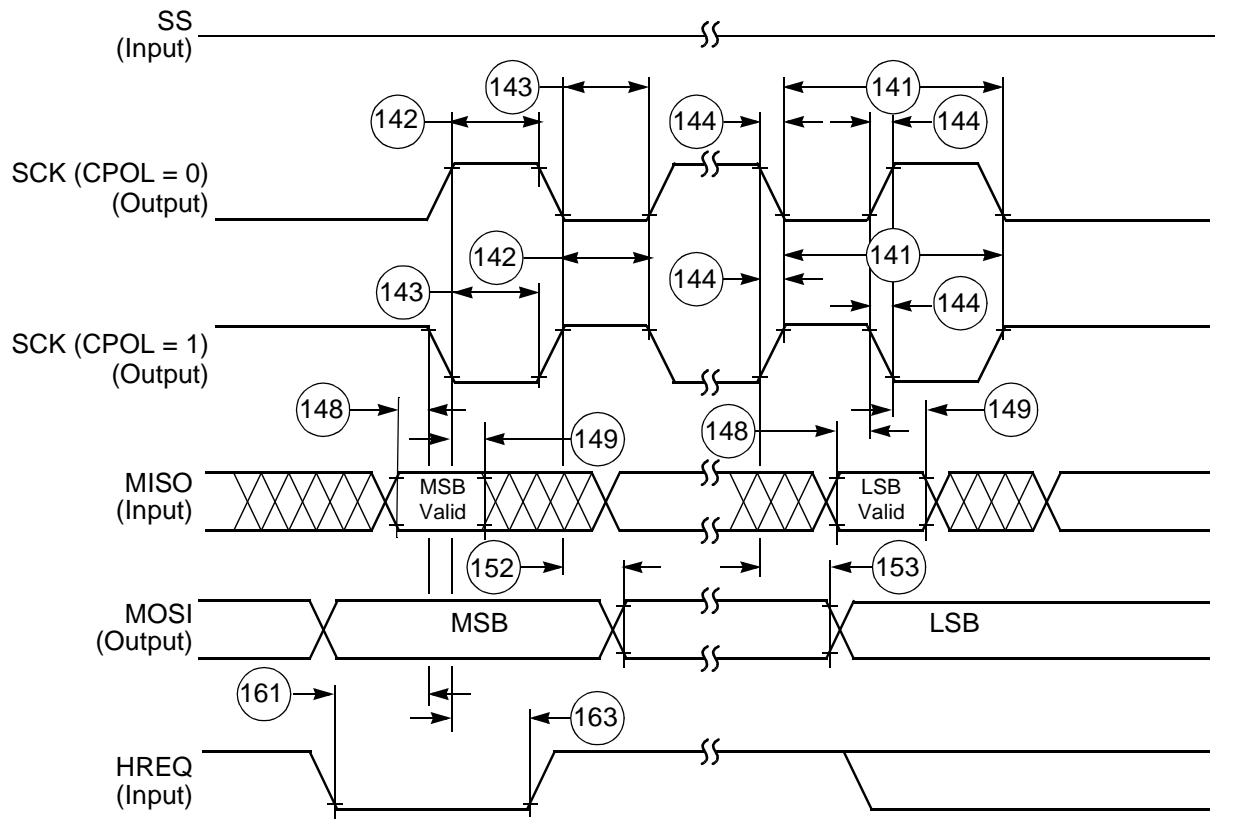


Figure 2-18 SPI Master Timing (CPHA = 0)

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## Specifications

### Serial Host Interface SPI Protocol Timing

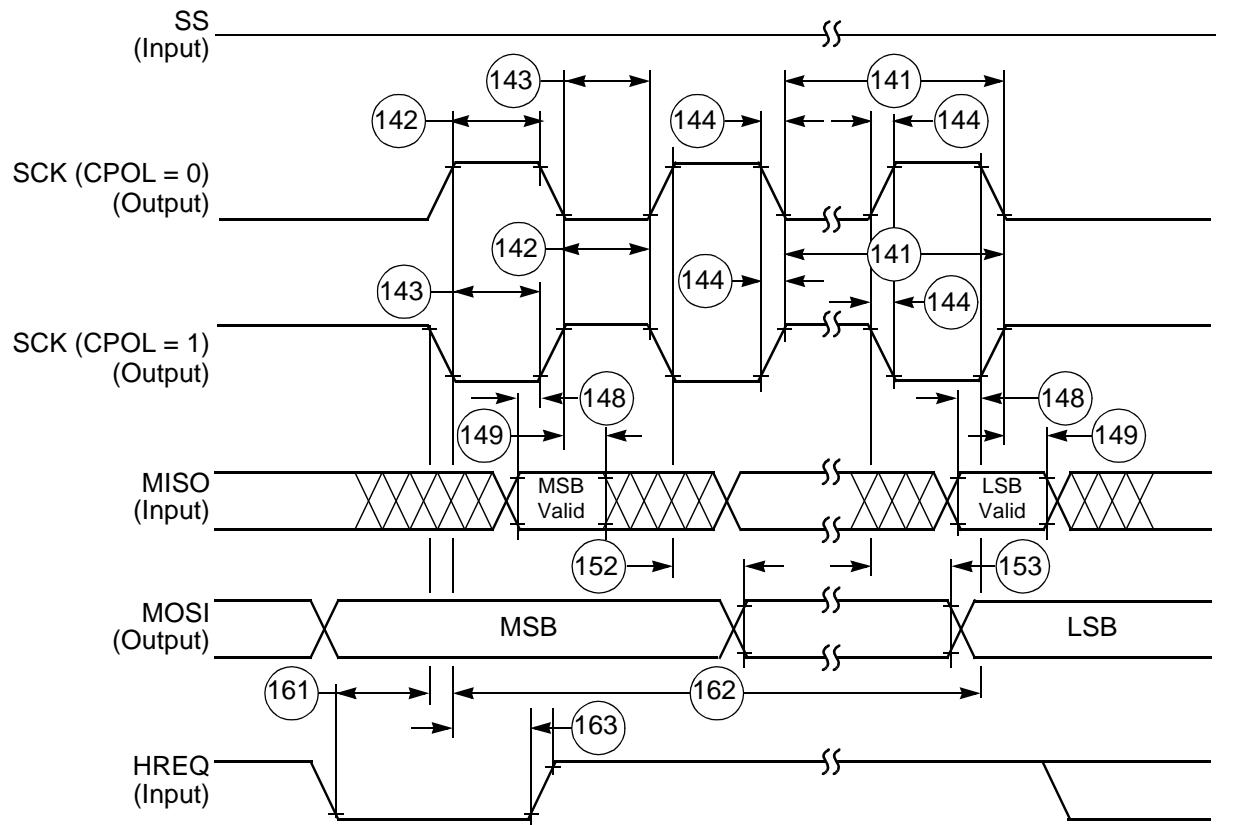
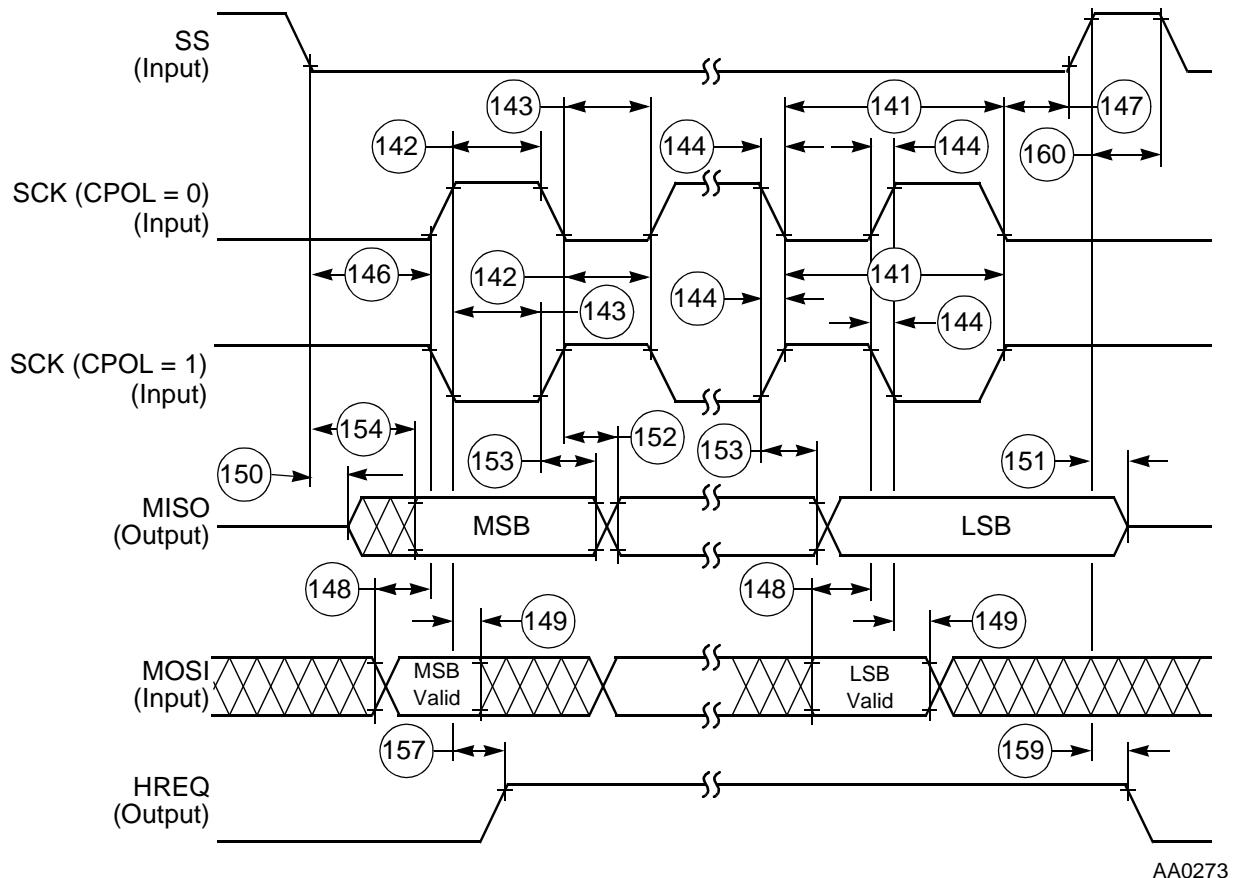


Figure 2-19 SPI Master Timing (CPHA = 1)

### Serial Host Interface SPI Protocol Timing



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Figure 2-20 SPI Slave Timing (CPHA = 0)

### Serial Host Interface (SHI) I<sup>2</sup>C Protocol Timing

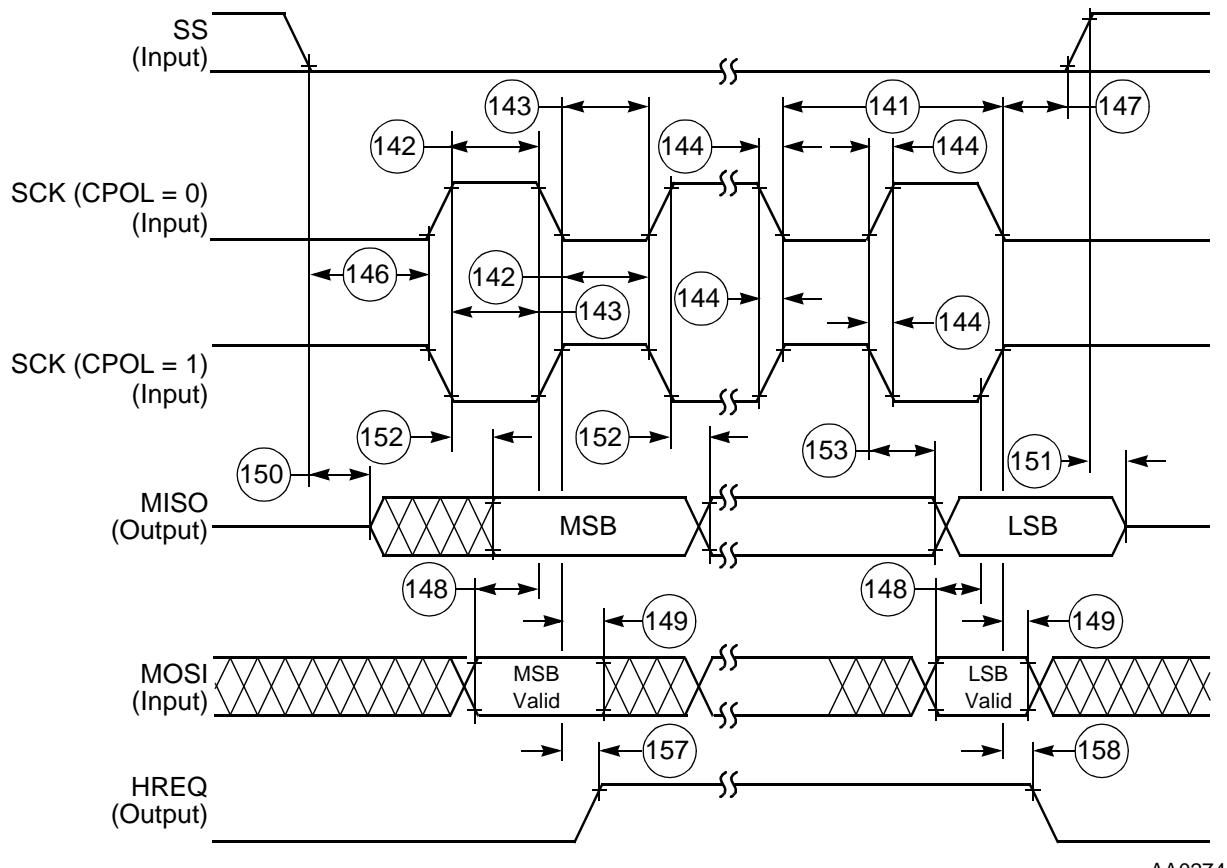


Figure 2-21 SPI Slave Timing (CPHA = 1)

## 2.12 SERIAL HOST INTERFACE (SHI) I<sup>2</sup>C PROTOCOL TIMING

# Freescale Semiconductor, Inc.

## Specifications

### Serial Host Interface (SHI) I<sup>2</sup>C Protocol Timing

**Table 2-18 SHI I<sup>2</sup>C Protocol Timing**

Standard I <sup>2</sup> C*							
No.	Characteristics	Symbol/ Expression	Standard-Mode		Fast-Mode		Unit
			Min	Max	Min	Max	
	Tolerable spike width on SCL or SDA	—	—	—	—	—	ns
	Filters bypassed	—	—	0	—	0	ns
	Narrow filters enabled	—	—	50	—	50	ns
	Wide filters enabled	—	—	100	—	100	ns
171	SCL clock frequency	F <sub>SCL</sub>	—	100	—	400	kHz
172	Bus free time	T <sub>BUF</sub>	4.7	—	1.3	—	μs
173	Start condition set-up time	T <sub>SU;STA</sub>	4.7	—	0.6	—	μs
174	Start condition hold time	T <sub>HD;STA</sub>	4.0	—	0.6	—	μs
175	SCL low period	T <sub>LOW</sub>	4.7	—	1.3	—	μs
176	SCL high period	T <sub>HIGH</sub>	4.0	—	1.3	—	μs
177	SCL and SDA rise time	T <sub>R</sub>	—	1000	20 + 0.1 × C <sub>b</sub>	300	ns
178	SCL and SDA fall time	T <sub>F</sub>	—	300	20 + 0.1 × C <sub>b</sub>	300	ns
179	Data set-up time	T <sub>SU;DAT</sub>	250	—	100	—	ns
180	Data hold time	T <sub>HD;DAT</sub>	0.0	—	0.0	0.9	μs
181	Stop condition set-up time	T <sub>SU;STO</sub>	4.0	—	0.6	—	μs
182	Capacitive load for each line	C <sub>b</sub>	—	400	—	400	pF
183	DSP clock frequency	F <sub>DSP</sub>					
	Filters bypassed		10.6	—	28.5	—	MHz
	Narrow filters enabled		11.8	—	39.7	—	MHz
	Wide filters enabled		13.1	—	61.0	—	MHz
184	HREQ in deassertion to last SCL edge (HREQ in set-up time)	t <sub>SU;RQI</sub>	0.0	—	0.0	—	ns

# Freescale Semiconductor, Inc.

## Specifications

### Serial Host Interface (SHI) I<sup>2</sup>C Protocol Timing

**Table 2-18 SHI I<sup>2</sup>C Protocol Timing (continued)**

No.	Characteristics	Symbol/ Expression	Standard I <sup>2</sup> C*				Unit	
			Standard-Mode		Fast-Mode			
			Min	Max	Min	Max		
186	First SCL sampling edge to HREQ output deassertion <sup>2</sup>	$T_{NG;RQO}$					ns	
	Filters bypassed	$2 \times T_C + 30$	—	50	—	50		
	Narrow filters enabled	$2 \times T_C + 120$	—	140	—	140		
	Wide filters enabled	$2 \times T_C + 208$	—	228	—	228		
187	Last SCL edge to HREQ output not deasserted <sup>2</sup>	$T_{AS;RQO}$					ns	
	Filters bypassed	$2 \times T_C + 30$	50	—	50	—		
	Narrow filters enabled	$2 \times T_C + 80$	100	—	100	—		
	Wide filters enabled	$2 \times T_C + 135$	155	—	155	—		
188	HREQ in assertion to first SCL edge	$T_{AS;RQI}$ $0.5 \times T_{I^2CCP} - 0.5 \times T_C - 21$					ns	
	Filters bypassed		4327	—	927	—		
	Narrow filters enabled		4282	—	882	—		
	Wide filters enabled		4238	—	838	—		
$R_P \text{ (min)} = 1.5 \text{ k}^{3/4}$								

### 2.12.1 Programming the Serial Clock

The programmed serial clock cycle,  $T_{I^2CCP}$ , is specified by the value of the HDM[5:0] and HRS bits of the HCKR (SHI clock control register).

The expression for  $T_{I^2CCP}$  is

$$T_{I^2CCP} = [T_C \times 2 \times (HDM[7:0] + 1) \times (7 \times (1 - HRS) + 1)]$$

where

- HRS is the prescaler rate select bit. When HRS is cleared, the fixed divide-by-eight prescaler is operational. When HRS is set, the prescaler is bypassed.
- HDM[7:0] are the divider modulus select bits.
- A divide ratio from 1 to 64 (HDM[5:0] = 0 to \$3F) may be selected.

### Serial Host Interface (SHI) I<sup>2</sup>C Protocol Timing

In I<sup>2</sup>C mode, the user may select a value for the programmed serial clock cycle from

$$6 \times T_C \quad (\text{if HDM[5:0] = \$02 and HRS = 1})$$

to

$$4096 \times T_C \quad (\text{if HDM[7:0] = \$FF and HRS = 0})$$

The programmed serial clock cycle ( $T_{I^2CCP}$ ), SCL rise time ( $T_R$ ), and the filters selected should be chosen in order to achieve the desired SCL frequency, as shown in Table 2-19.

**Table 2-19 SCL Serial Clock Cycle generated as Master**

Filters bypassed	$T_{I^2CCP} + 2.5 \times T_C + 45\text{ns} + T_R$
Narrow filters enabled	$T_{I^2CCP} + 2.5 \times T_C + 135\text{ns} + T_R$
Wide filters enabled	$T_{I^2CCP} + 2.5 \times T_C + 223\text{ns} + T_R$

EXAMPLE:

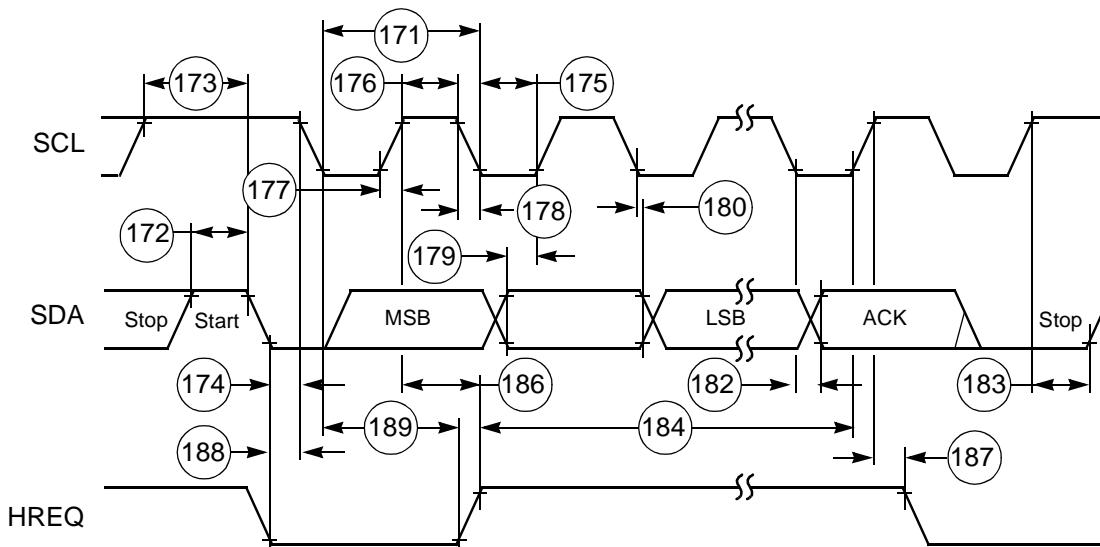
For DSP clock frequency of 100 MHz (i.e.  $T_C = 10\text{ns}$ ), operating in a standard-mode I<sup>2</sup>C environment ( $F_{SCL} = 100\text{ KHz}$  (i.e.  $T_{SCL} = 10\mu\text{s}$ ),  $T_R = 1000\text{ns}$ ), with filters bypassed

$$T_{I^2CCP} = 10\mu\text{s} - 2.5 \times 10\text{ns} - 45\text{ns} - 1000\text{ns} = 8930\text{ns}$$

Choosing HRS = 0 gives

$$\text{HDM[7:0]} = 8930\text{ns} / (2 \times 10\text{ns} \times 8) - 1 = 55.8$$

Thus the HDM[7:0] value should be programmed to \$38 (=56).



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**Figure 2-22 I<sup>2</sup>C Timing**

# Freescale Semiconductor, Inc.

## Specifications

### Enhanced Serial Audio Interface Timing

## 2.13 ENHANCED SERIAL AUDIO INTERFACE TIMING

**Table 2-20 Enhanced Serial Audio Interface Timing**

No.	Characteristics <sup>1, 2, 3</sup>	Symbol	Expression	Min	Max	Cond-i tion <sup>4</sup>	Unit
430	Clock cycle <sup>5</sup>	t <sub>SSICC</sub>	$4 \times T_C$ $3 \times T_C$ TXC:max[3*tc; t454]	40.0	—	i ck	ns
431	Clock high period • For internal clock  • For external clock	—	$2 \times T_C - 10.0$  $1.5 \times T_C$	10.0	—		ns
432	Clock low period • For internal clock  • For external clock	—	$2 \times T_C - 10.0$  $1.5 \times T_C$	10.0	—		ns
433	RXC rising edge to FSR out (bl) high	—	—	—	37.0 22.0	x ck i ck a	ns
434	RXC rising edge to FSR out (bl) low	—	—	—	37.0 22.0	x ck i ck a	ns
435	RXC rising edge to FSR out (wr) high <sup>6</sup>	—	—	—	39.0 24.0	x ck i ck a	ns
436	RXC rising edge to FSR out (wr) low <sup>6</sup>	—	—	—	39.0 24.0	x ck i ck a	ns
437	RXC rising edge to FSR out (wl) high	—	—	—	36.0 21.0	x ck i ck a	ns
438	RXC rising edge to FSR out (wl) low	—	—	—	37.0 22.0	x ck i ck a	ns
439	Data in setup time before RXC (SCK in synchronous mode) falling edge	—	—	0.0 19.0	—	x ck i ck	ns
440	Data in hold time after RXC falling edge	—	—	5.0 3.0	—	x ck i ck	ns
441	FSR input (bl, wr) high before RXC falling edge <sup>6</sup>	—	—	23.0 1.0	—	x ck i ck a	ns

# Freescale Semiconductor, Inc.

## Specifications

### Enhanced Serial Audio Interface Timing

**Table 2-20 Enhanced Serial Audio Interface Timing (continued)**

No.	Characteristics <sup>1, 2, 3</sup>	Symbol	Expression	Min	Max	Cond-i tion <sup>4</sup>	Unit
442	FSR input (wl) high before RXC falling edge	—	—	1.0 23.0	— —	x ck i ck a	ns
443	FSR input hold time after RXC falling edge	—	—	3.0 0.0	— —	x ck i ck a	ns
444	Flags input setup before RXC falling edge	—	—	0.0 19.0	— —	x ck i ck s	ns
445	Flags input hold time after RXC falling edge	—	—	6.0 0.0	— —	x ck i ck s	ns
446	TXC rising edge to FST out (bl) high	—	—	— —	29.0 15.0	x ck i ck	ns
447	TXC rising edge to FST out (bl) low	—	—	— —	31.0 17.0	x ck i ck	ns
448	TXC rising edge to FST out (wr) high <sup>6</sup>	—	—	— —	31.0 17.0	x ck i ck	ns
449	TXC rising edge to FST out (wr) low <sup>6</sup>	—	—	— —	33.0 19.0	x ck i ck	ns
450	TXC rising edge to FST out (wl) high	—	—	— —	30.0 16.0	x ck i ck	ns
451	TXC rising edge to FST out (wl) low	—	—	— —	31.0 17.0	x ck i ck	ns
452	TXC rising edge to data out enable from high impedance	—	—	— —	31.0 17.0	x ck i ck	ns
453	TXC rising edge to transmitter #0 drive enable assertion	—	—	— —	34.0 20.0	x ck i ck	ns
454	TXC rising edge to data out valid	—	$23 + 0.5 \times T_C$ 21.0	— —	28.0 21.0	x ck i ck	ns
455	TXC rising edge to data out high impedance <sup>7</sup>	—	—	— —	31.0 16.0	x ck i ck	ns
456	TXC rising edge to transmitter #0 drive enable deassertion <sup>7</sup>	—	—	— —	34.0 20.0	x ck i ck	ns
457	FST input (bl, wr) setup time before TXC falling edge <sup>6</sup>	—	—	2.0 21.0	— —	x ck i ck	ns

# Freescale Semiconductor, Inc.

## Specifications

### Enhanced Serial Audio Interface Timing

**Table 2-20 Enhanced Serial Audio Interface Timing (continued)**

No.	Characteristics <sup>1, 2, 3</sup>	Symbol	Expression	Min	Max	Cond-i tion <sup>4</sup>	Unit
458	FST input (wl) to data out enable from high impedance	—	—	—	27.0	—	ns
459	FST input (wl) to transmitter #0 drive enable assertion	—	—	—	31.0	—	ns
460	FST input (wl) setup time before TXC falling edge	—	—	2.0 21.0	—	x ck i ck	ns
461	FST input hold time after TXC falling edge	—	—	4.0 0.0	—	x ck i ck	ns
462	Flag output valid after TXC rising edge	—	—	— —	32.0 18.0	x ck i ck	ns
463	HCKR/HCKT clock cycle	—	—	40.0	—		ns
464	HCKT input rising edge to TXC output	—	—	—	27.5		ns
465	HCKR input rising edge to RXC output	—	—	—	27.5		ns

Notes:

1.  $V_{CC} = 3.16 \text{ V} \pm 0.16 \text{ V}$ ;  $T_J = 0^\circ\text{C}$  to  $+105^\circ\text{C}$ ,  $C_L = 50 \text{ pF}$

2. i ck = internal clock

x ck = external clock

i ck a = internal clock, asynchronous mode

(asynchronous implies that TXC and RXC are two different clocks)

i ck s = internal clock, synchronous mode

(synchronous implies that TXC and RXC are the same clock)

3. bl = bit length

wl = word length

wr = word length relative

4. TXC(SCKT pin) = transmit clock

RXC(SCKR pin) = receive clock

FST(FST pin) = transmit frame sync

FSR(FSR pin) = receive frame sync

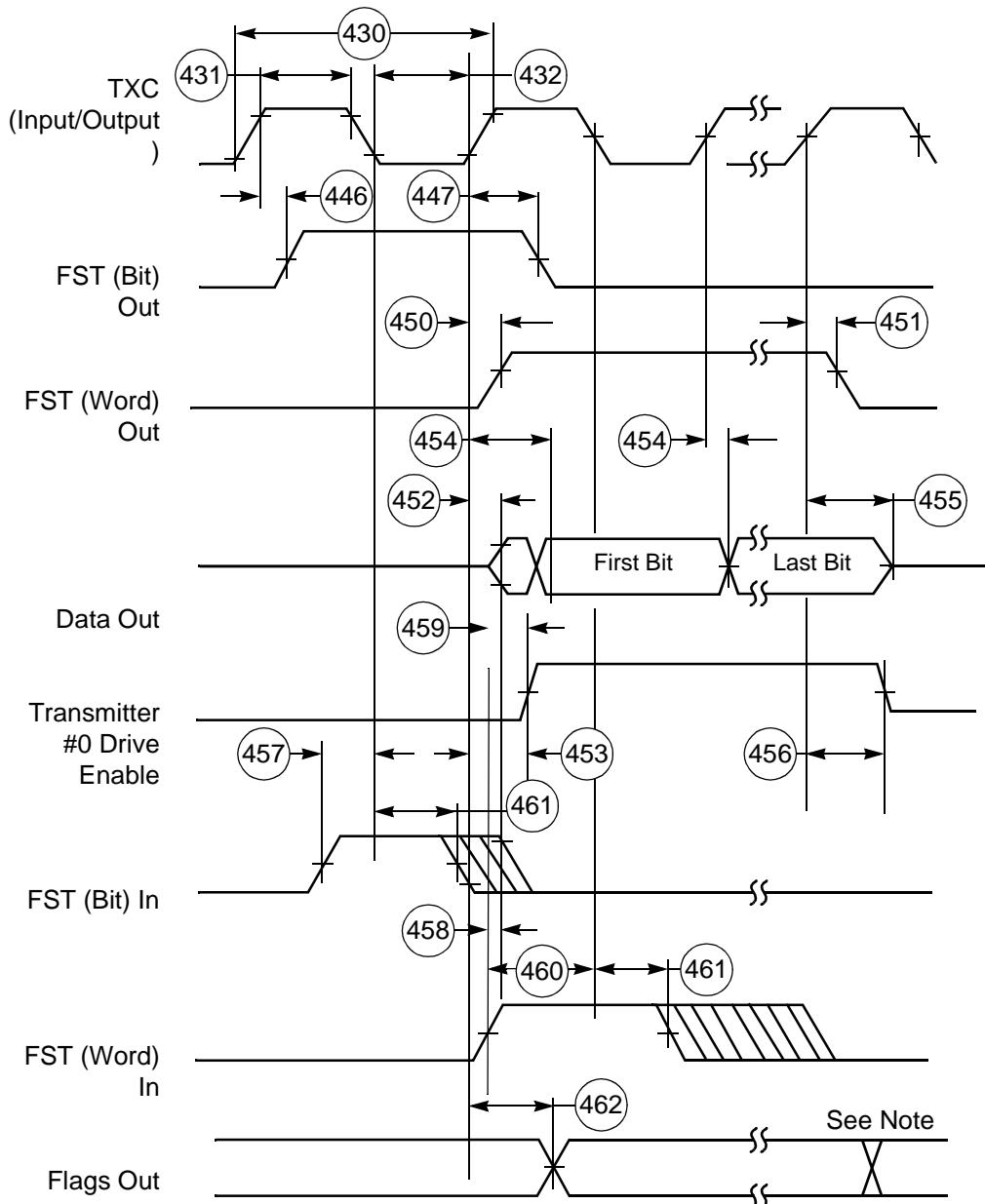
HCKT(HCKT pin) = transmit high speed clock

HCKR(HCKR pin) = receive high speed clock

5. For the internal clock, the external clock cycle is defined by Icyc and the ESAI control register.

6. The word-relative frame sync signal waveform relative to the clock operates in the same manner as the bit-length frame sync signal waveform, but spreads from one serial clock before first bit clock (same as bit length frame sync signal), until the one before last bit clock of the first word in frame.

7. Periodically sampled and not 100% tested



Note: In network mode, output flag transitions can occur at the start of each time slot within the frame. In normal mode, the output flag state is asserted for the entire frame period.

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Figure 2-23 ESAI Transmitter Timing

# Freescale Semiconductor, Inc.

## Specifications

### Enhanced Serial Audio Interface Timing

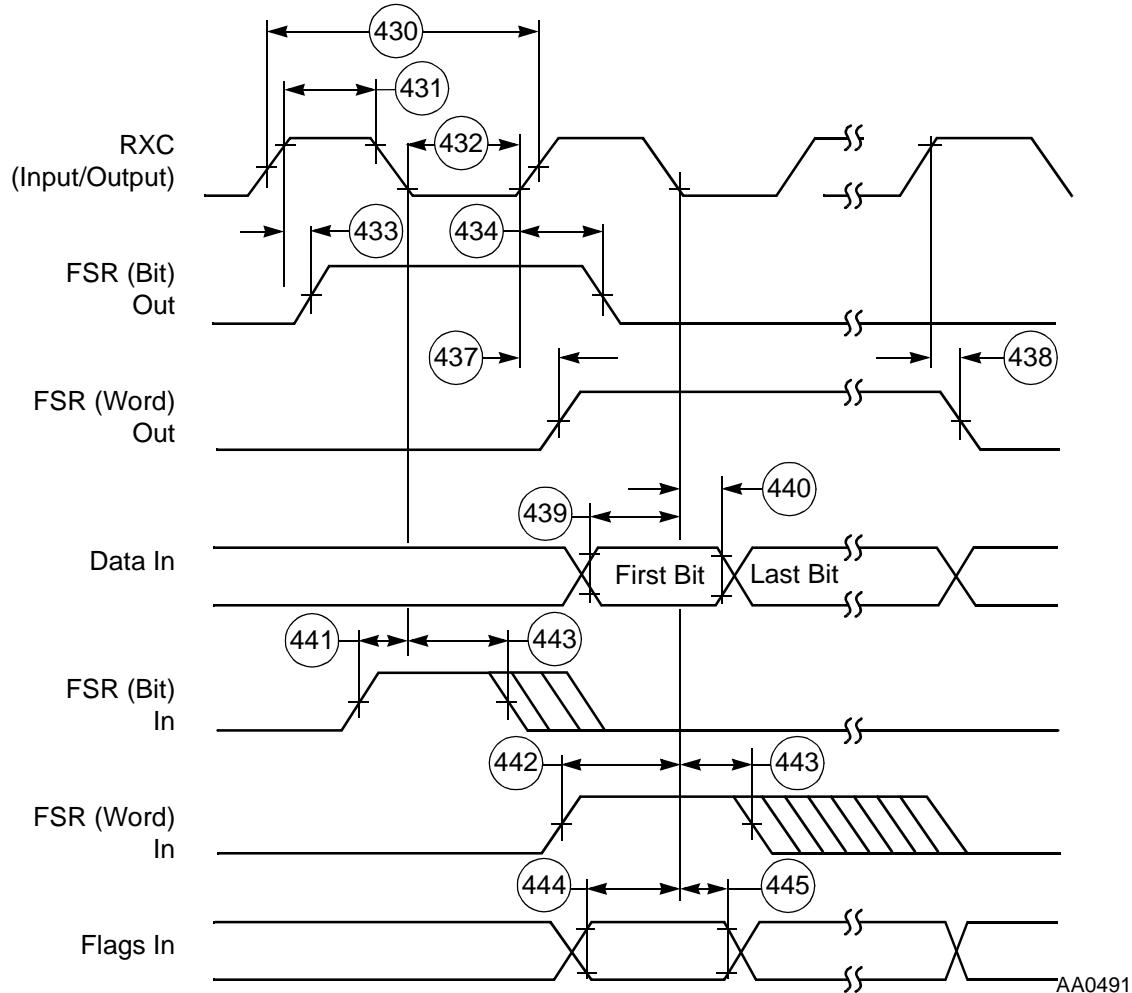


Figure 2-24 ESAI Receiver Timing

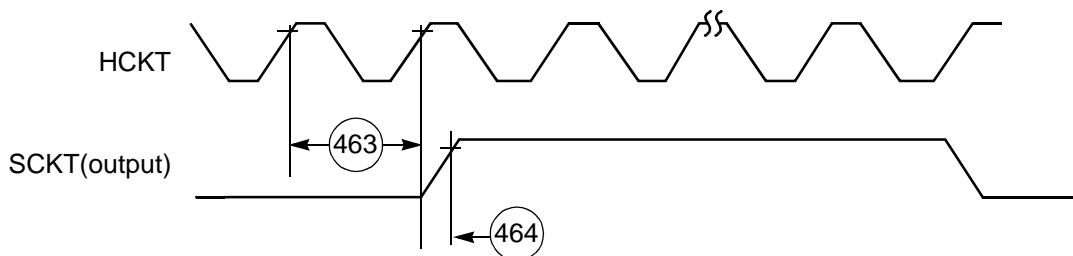
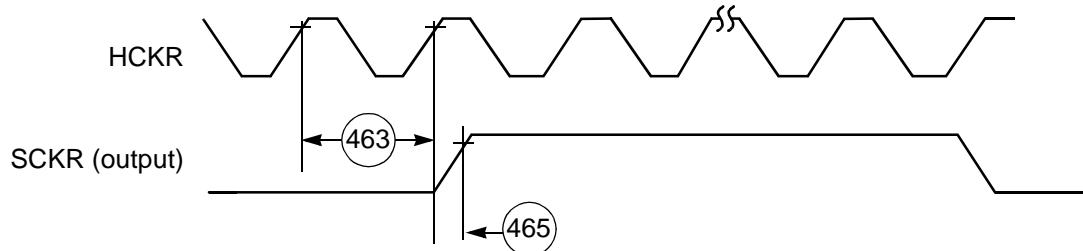


Figure 2-25 ESAI HCKT Timing



**Figure 2-26 ESAI HCKR Timing**

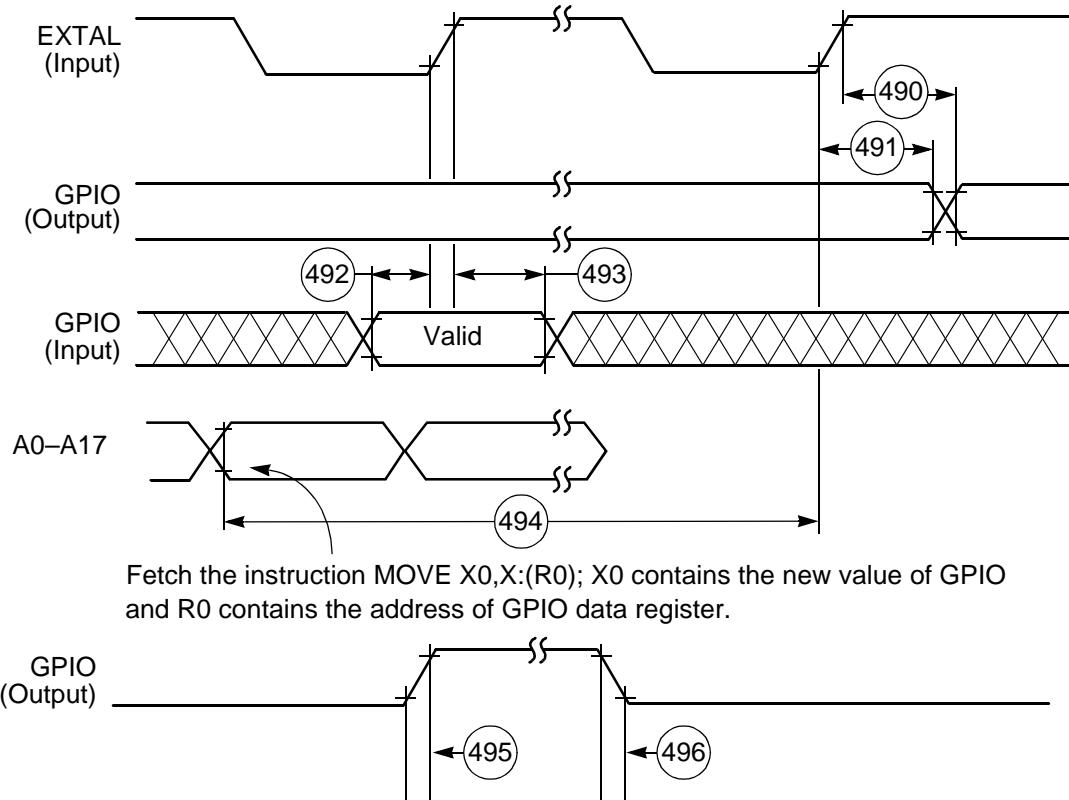
## 2.14 GPIO TIMING

**Table 2-21 GPIO Timing**

No.	Characteristics <sup>1</sup>	Expression	Min	Max	Unit
490 <sup>2</sup>	EXTAL edge to GPIO out valid (GPIO out delay time)		—	32.8	ns
491	EXTAL edge to GPIO out not valid (GPIO out hold time)		4.8	—	ns
492	GPIO In valid to EXTAL edge (GPIO in set-up time)		10.2	—	ns
493	EXTAL edge to GPIO in not valid (GPIO in hold time)		1.8	—	ns
494 <sup>2</sup>	Fetch to EXTAL edge before GPIO change	$6.75 \times T_C - 1.8$	65.7	—	ns
495	GPIO out rise time	—	—	13	ns
496	GPIO out fall time	—	—	13	ns

Notes:

- 1.  $V_{CC} = 3.3 \text{ V} \pm 0.16 \text{ V}$ ;  $T_J = 0^\circ\text{C}$  to  $+105^\circ\text{C}$ ,  $C_L = 50 \text{ pF}$
- 2. Valid only when PLL enabled with multiplication factor equal to one.

**Freescale Semiconductor, Inc.****Specifications****GPIO Timing****Figure 2-27** **GPIO Timing**

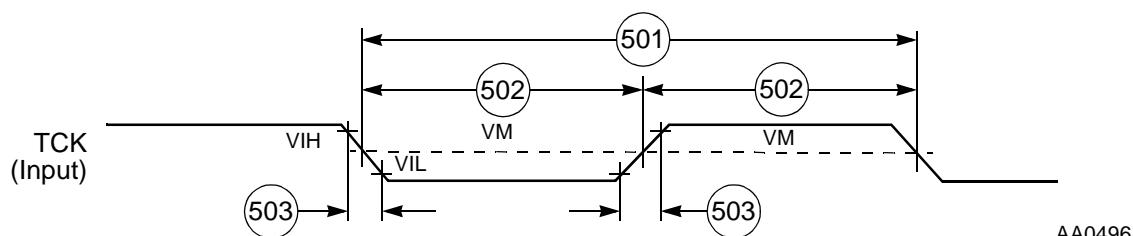
## 2.15 JTAG TIMING

**Table 2-22 JTAG Timing**

No.	Characteristics	All frequencies		Unit
		Min	Max	
500	TCK frequency of operation ( $1/(T_C \times 3)$ ; maximum 22 MHz)	0.0	22.0	MHz
501	TCK cycle time in Crystal mode	45.0	—	ns
502	TCK clock pulse width measured at 1.5 V	20.0	—	ns
503	TCK rise and fall times	0.0	3.0	ns
504	Boundary scan input data setup time	5.0	—	ns
505	Boundary scan input data hold time	24.0	—	ns
506	TCK low to output data valid	0.0	40.0	ns
507	TCK low to output high impedance	0.0	40.0	ns
508	TMS, TDI data setup time	5.0	—	ns
509	TMS, TDI data hold time	25.0	—	ns
510	TCK low to TDO data valid	0.0	44.0	ns
511	TCK low to TDO high impedance	0.0	44.0	ns

Notes:

- $V_{CC} = 3.3 \text{ V} \pm 0.16 \text{ V}$ ;  $T_J = 0^\circ\text{C}$  to  $+105^\circ\text{C}$ ,  $C_L = 50 \text{ pF}$
- All timings apply to OnCE module data transfers because it uses the JTAG port as an interface.

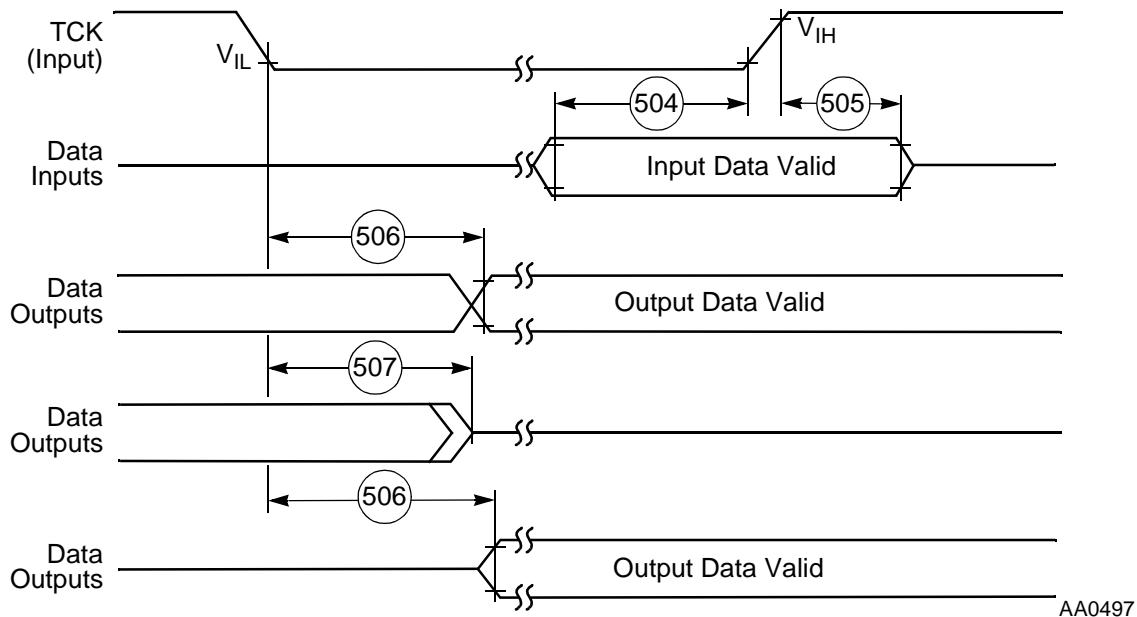


**Figure 2-28 Test Clock Input Timing Diagram**

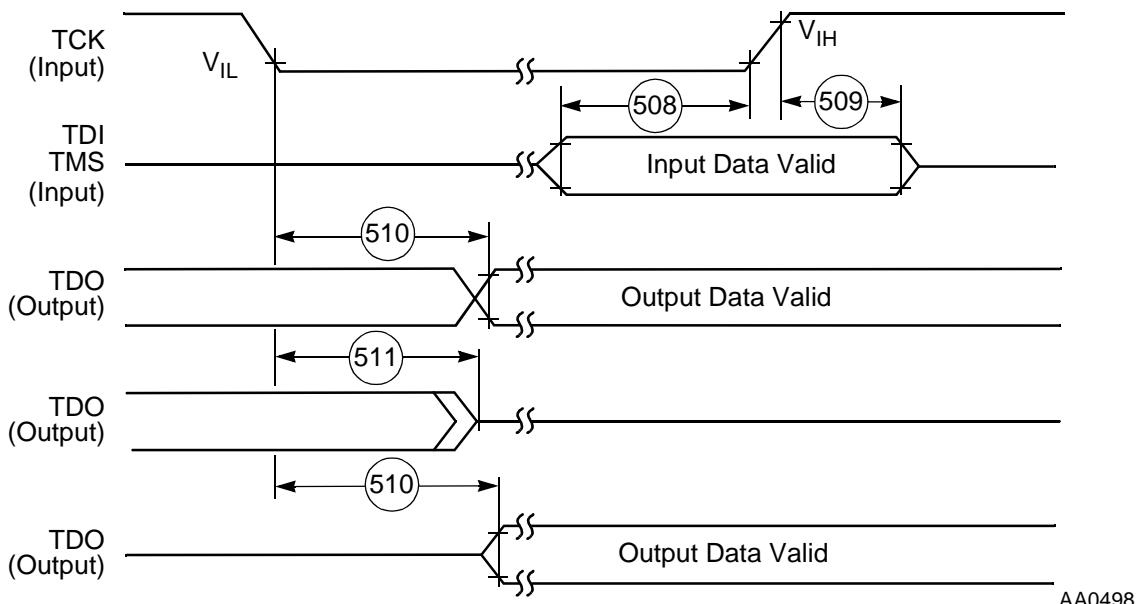
## Freescale Semiconductor, Inc.

### Specifications

#### JTAG Timing



**Figure 2-29 Boundary Scan (JTAG) Timing Diagram**



**Figure 2-30 Test Access Port Timing Diagram**

## **Freescale Semiconductor, Inc.**

# **SECTION 3**

# **PACKAGING**

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### **3.1 PIN-OUT AND PACKAGE INFORMATION**

This section provides information about the available package for this product, including diagrams of the package pinouts and tables describing how the signals described in Section 1, *Signal/Connection Descriptions* are allocated for the package. The DSP56364 is available in a 100-pin TQFP package. Table 3-1 and Table 3-2 show the pin/name assignments for the packages.

#### **3.1.1 TQFP Package Description**

Top view of the 100-pin TQFP package is shown in Figure 3-1 with its pin-outs. The 100-pin TQFP package mechanical drawing is shown in Figure 3-2.

**Freescale Semiconductor, Inc.**

## Packaging

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## **Pin-out and Package Information**

**Figure 3-1 DSP56364 100-Pin Thin Quad Flat Pack (TQFP), Top View**

**Freescale Semiconductor, Inc.****Packaging****Pin-out and Package Information****Table 3-1 DSP56364 100-Pin TQFP Signal Identification by Pin Number**

<b>Pin No.</b>	<b>Signal Name</b>						
1	MODD/IRQD	26	SCK/SCL	51	A3	76	D1
2	MODB/IRQB	27	HREQ	52	A4	77	D2
3	MODA/IRQA	28	PINIT/NMI	53	A5	78	D3
4	FST	29	RESET	54	A6	79	VCCD
5	FSR	30	No Connect	55	VCCA	80	GNDD
6	SCKT	31	VCCP	56	GNDA	81	D4
7	SCKR	32	PCAP	57	A7	82	D5
8	VCCS	33	GNDP	58	A8	83	D6
9	GNDS	34	EXTAL	59	A9	84	D7
10	HCKT	35	VCCHQ	60	A10	85	No Connect
11	VCCLQ	36	GNDQ	61	VCCHQ	86	No Connect
12	GNDQ	37	VCCLQ	62	A11	87	VCCLQ
13	HCKR	38	TA	63	VCCA	88	GNDQ
14	SDO0	39	CAS	64	GNDA	89	VCCHQ
15	VCCHQ	40	WR	65	GNDQ	90	No Connect
16	SDO1	41	RD	66	VCCLQ	91	GPIO0
17	SDO2/SDI3	42	VCCC	67	A12	92	VCCS
18	SDO3/SDI2	43	GNDC	68	A13	93	GNDS
19	SDO4/SDI1	44	AA1/RAS1	69	A14	94	GPIO1
20	SDO5/SDI0	45	AA0/RAS0	70	A15	95	GPIO2
21	VCCS	46	A0	71	VCCA	96	GPIO3
22	GNDS	47	A1	72	GNDA	97	TDO
23	SS/HA2	48	VCCQ	73	A16	98	TDI
24	MOSI/HA0	49	GNDQ	74	A17	99	TCK
25	MISO/SDA	50	A2	75	D0	100	TMS

Notes: Signal names are based on configured functionality. Most pins supply a single signal. Some pins provide a signal with dual functionality, such as the MODx/IRQx pins that select an operating mode after RESET is deasserted, but act as interrupt lines during operation.

# Freescale Semiconductor, Inc.

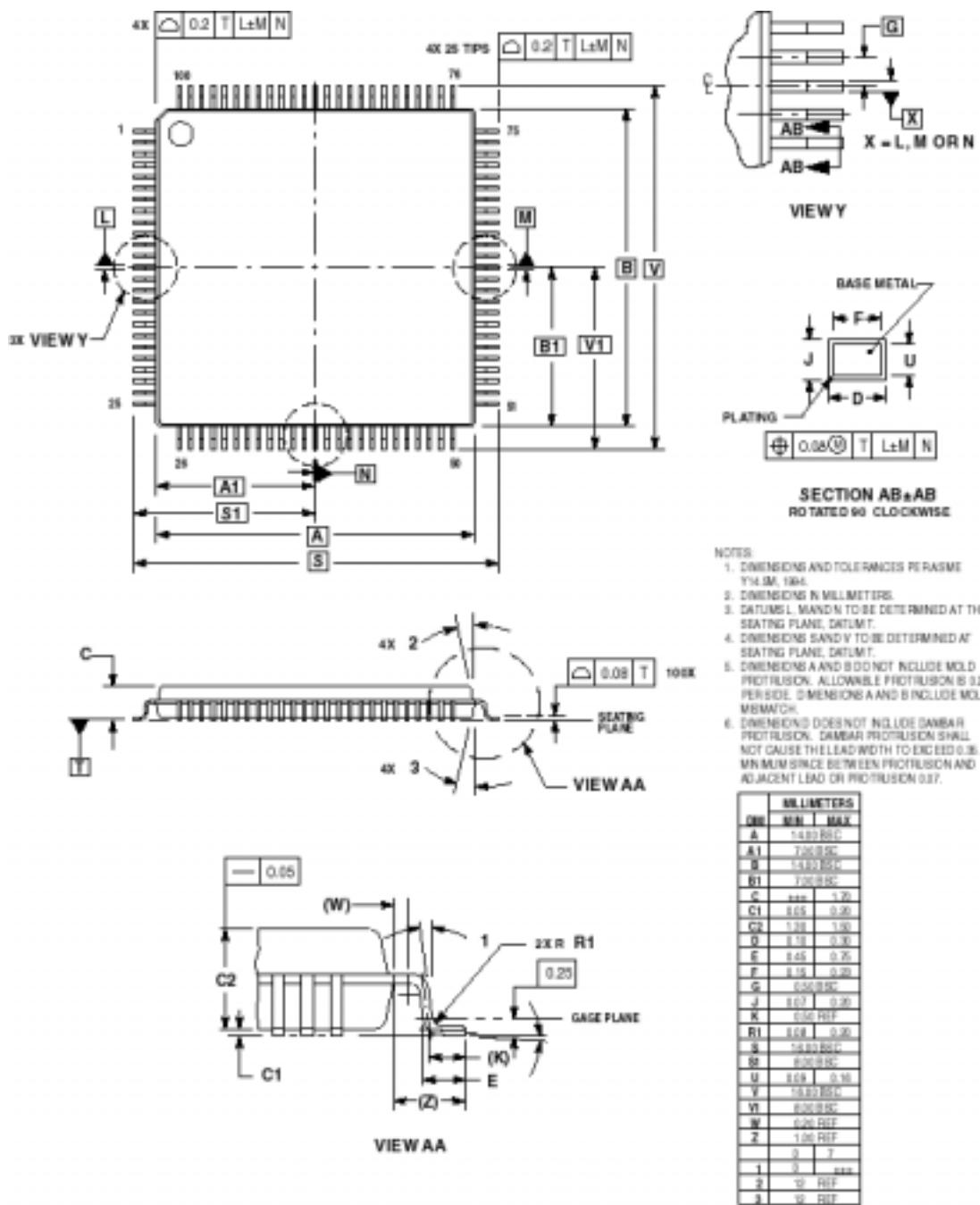
## Packaging

### Pin-out and Package Information

**Table 3-2 DSP56364 100-Pin TQFP Signal Identification by Name**

Signal Name	Pin No.						
A0	46	D4	81	HCKR	13	SDO4/SDI1	19
A1	47	D5	82	HCKT	10	TA	38
A10	60	D6	83	HREQ	27	TCK	99
A11	62	D7	84	MISO/SDA	25	TDI	98
A12	67	EXTAL	34	MODA/IRQA	3	TD0	97
A13	68	FSR	5	MODB/IRQB	2	TMS	100
A14	69	FST	4	MODD/IRQD	1	VCCA	48
A15	70	GNDA	49	MOSI/HA0	24	VCCA	55
A16	73	GNDA	56	No Connect	30	VCCA	63
A17	74	GNDA	64	No Connect	85	VCCA	71
A2	50	GNDA	72	No Connect	86	VCCC	42
A3	51	GNDC	43	No Connect	90	VCCD	79
A4	52	GNDD	80	PCAP	32	VCCHQ	15
A5	53	GNDP	33	PINIT/NMI	28	VCCHQ	35
A6	54	GNDQ	12	RD	41	VCCHQ	61
A7	57	GNDQ	36	RESET	29	VCCHQ	89
A8	58	GNDQ	65	SCK/SCL	26	VCCLQ	11
A9	59	GNDQ	88	SCKR	7	VCCLQ	37
AA0	45	GNDS	9	SCKT	6	VCCLQ	66
AA1	44	GNDS	22	SDO0	14	VCCLQ	87
CAS	39	GNDS	93	SDO1	16	VCCP	31
D0	75	GPIO0	91	SDO5/SDI0	20	VCCS	8
D1	76	GPIO1	94	SS/HA2	23	VCCS	21
D2	77	GPIO2	95	SDO2/SDI3	17	VCCS	92
D3	78	GPIO3	96	SDO3/SDI2	18	WR	40

### 3.1.2 TQFP Package Mechanical Drawing



CASE 983±02  
ISSUE E

DATE 01/30/96

Figure 3-2 DSP56364 100-pin TQFP Package

# **Freescale Semiconductor, Inc.**

## **Packaging**

### **Ordering Drawings**

#### **3.2 ORDERING DRAWINGS**

The detailed package drawing is available on the Motorola web page at:

<http://mot.sps.com/cgi-bin/cases>

Use package 983 for the search.

**SECTION 4****DESIGN CONSIDERATIONS****4.1 THERMAL DESIGN CONSIDERATIONS**

An estimation of the chip junction temperature,  $T_J$ , in °C can be obtained from the following equation:

$$T_J = T_A + (P_D \times R_{\theta JA})$$

Where:  $T_A$  = ambient temperature °C

$R_{qJA}$  = package junction-to-ambient thermal resistance °C/W

$P_D$  = power dissipation in package W

Historically, thermal resistance has been expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance.

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

Where:  $R_{\theta JA}$  = package junction-to-ambient thermal resistance °C/W

$R_{\theta JC}$  = package junction-to-case thermal resistance °C/W

$R_{\theta CA}$  = package case-to-ambient thermal resistance °C/W

$R_{\theta JC}$  is device-related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance,  $R_{\theta CA}$ . For example, the user can change the air flow around the device, add a heat sink, change the mounting arrangement on the printed circuit board (PCB), or otherwise change the thermal dissipation capability of the area surrounding the device on a PCB. This model is most useful for ceramic packages with heat sinks; some 90% of the heat flow is dissipated through the case to the heat sink and out to the ambient environment. For ceramic packages, in situations where the heat flow is split between a path to the case and an alternate path through the PCB, analysis of the device thermal performance may need the additional modeling capability of a system level thermal simulation tool.

The thermal performance of plastic packages is more dependent on the temperature of the PCB to which the package is mounted. Again, if the estimations obtained from  $R_{\theta JA}$  do not satisfactorily answer whether the thermal performance is adequate, a system level model may be appropriate.

A complicating factor is the existence of three common ways for determining the junction-to-case thermal resistance in plastic packages.

- To minimize temperature variation across the surface, the thermal resistance is measured from the junction to the outside surface of the package (case) closest to the chip mounting area when that surface has a proper heat sink.
- To define a value approximately equal to a junction-to-board thermal resistance, the thermal resistance is measured from the junction to where the leads are attached to the case.
- If the temperature of the package case ( $T_T$ ) is determined by a thermocouple, the thermal resistance is computed using the value obtained by the equation  $(T_J - T_T)/P_D$ .

# Freescale Semiconductor, Inc.

## Design Considerations

Electrical Design Considerations

As noted above, the junction-to-case thermal resistances quoted in this data sheet are determined using the first definition. From a practical standpoint, that value is also suitable for determining the junction temperature from a case thermocouple reading in forced convection environments. In natural convection, using the junction-to-case thermal resistance to estimate junction temperature from a thermocouple reading on the case of the package will estimate a junction temperature slightly hotter than actual temperature. Hence, the new thermal metric, thermal characterization parameter or  $\Psi_{JT}$ , has been defined to be  $(T_J - T_T)/P_D$ . This value gives a better estimate of the junction temperature in natural convection when using the surface temperature of the package. Remember that surface temperature readings of packages are subject to significant errors caused by inadequate attachment of the sensor to the surface and to errors caused by heat loss to the sensor. The recommended technique is to attach a 40-gauge thermocouple wire and bead to the top center of the package with thermally conductive epoxy.

## 4.2 ELECTRICAL DESIGN CONSIDERATIONS

### CAUTION

This device contains circuitry protecting against damage due to high static voltage or electrical fields. However, normal precautions should be taken to avoid exceeding maximum voltage ratings. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). The suggested value for a pullup or pulldown resistor is 10 k ohm.

Use the following list of recommendations to assure correct DSP operation:

- Provide a low-impedance path from the board power supply to each  $V_{CC}$  pin on the DSP and from the board ground to each GND pin.
- Use at least six 0.01–0.1  $\mu$ F bypass capacitors positioned as close as possible to the four sides of the package to connect the  $V_{CC}$  power source to GND.
- Ensure that capacitor leads and associated printed circuit traces that connect to the chip  $V_{CC}$  and GND pins are less than 1.2 cm (0.5 inch) per capacitor lead.
- Use at least a four-layer PCB with two inner layers for  $V_{CC}$  and GND.
- Because the DSP output signals have fast rise and fall times, PCB trace lengths should be minimal. This recommendation particularly applies to the address and data buses as well as the  $\overline{IRQA}$ ,  $\overline{IRQB}$ ,  $\overline{IRQD}$ , and  $\overline{TA}$  pins. Maximum PCB trace lengths on the order of 15 cm (6 inches) are recommended.
- Consider all device loads as well as parasitic capacitance due to PCB traces when calculating capacitance. This is especially critical in systems with higher capacitive loads that could create higher transient currents in the  $V_{CC}$  and GND circuits.

---

Power Consumption Considerations

- All inputs must be terminated (i.e., not allowed to float) using CMOS levels, except for the three pins with internal pull-up resistors (TMS, TDI, TCK).
- Take special care to minimize noise levels on the  $V_{CCP}$  and  $GND_P$  pins.
- If multiple DSP56364 devices are on the same board, check for cross-talk or excessive spikes on the supplies due to synchronous operation of the devices.
- RESET must be asserted when the chip is powered up. A stable EXTAL signal must be supplied before deassertion of RESET.
- At power-up, ensure that the voltage difference between the 5 V tolerant pins and the chip  $V_{CC}$  never exceeds 3.95 V.

## 4.3 POWER CONSUMPTION CONSIDERATIONS

Power dissipation is a key issue in portable DSP applications. Some of the factors which affect current consumption are described in this section. Most of the current consumed by CMOS devices is alternating current (ac), which is charging and discharging the capacitances of the pins and internal nodes.

Current consumption is described by the following formula:

$$I = C \times V \times f$$

where             $C$  = node/pin capacitance  
                   $V$  = voltage swing  
                   $f$  = frequency of node/pin toggle

### Example 1 Current Consumption

---

For a Port A address pin loaded with 50 pF capacitance, operating at 3.3 V, and with a 100 MHz clock, toggling at its maximum possible rate (50 MHz), the current consumption is

$$I = 50 \times 10^{-12} \times 3.3 \times 50 \times 10^6 = 8.25\text{mA}$$

---

The maximum internal current ( $I_{CCI}^{max}$ ) value reflects the typical possible switching of the internal buses on best-case operation conditions, which is not necessarily a real application case. The typical internal current ( $I_{CCI}^{typ}$ ) value reflects the average switching of the internal buses on typical operating conditions.

For applications that require very low current consumption, do the following:

- Set the EBD bit when not accessing external memory.
- Minimize external memory accesses and use internal memory accesses.
- Minimize the number of pins that are switching.
- Minimize the capacitive load on the pins.
- Connect the unused inputs to pull-up or pull-down resistors.
- Disable unused peripherals.

## Freescale Semiconductor, Inc.

### Design Considerations

#### PLL Performance Issues

One way to evaluate power consumption is to use a current per MIPS measurement methodology to minimize specific board effects (i.e., to compensate for measured board current not caused by the DSP). A benchmark power consumption test algorithm is listed in Appendix A. Use the test algorithm, specific test current measurements, and the following equation to derive the current per MIPS value.

$$I/\text{MIPS} = I/\text{MHz} = (I_{\text{typF2}} - I_{\text{typF1}})/(F2 - F1)$$

where :  $I_{\text{typF2}}$  = current at F2

$I_{\text{typF1}}$  = current at F1

F2 = high frequency (any specified operating frequency)

F1 = low frequency (any specified operating frequency lower than F2)

**Note:** F1 should be significantly less than F2. For example, F2 could be 66 MHz and F1 could be 33 MHz. The degree of difference between F1 and F2 determines the amount of precision with which the current rating can be determined for an application.

## 4.4 PLL PERFORMANCE ISSUES

The following explanations should be considered as general observations on expected PLL behavior. There is no testing that verifies these exact numbers. These observations were measured on a limited number of parts and were not verified over the entire temperature and voltage ranges.

### 4.4.1 Input (EXTAL) Jitter Requirements

The allowed jitter on the frequency of EXTAL is 0.5%. If the rate of change of the frequency of EXTAL is slow (i.e., it does not jump between the minimum and maximum values in one cycle) or the frequency of the jitter is fast (i.e., it does not stay at an extreme value for a long time), then the allowed jitter can be 2%. The phase and frequency jitter performance results are only valid if the input jitter is less than the prescribed values.

**Freescale Semiconductor, Inc.****SECTION 5****ORDERING INFORMATION**

Consult a Motorola Semiconductor sales office or authorized distributor to determine product availability and to place an order.

**Table 5-1 Ordering Information**

Part	Supply Voltage	Package Type	Pin Count	Frequency (MHz)	Order Number
DSP56364	3.3 V	Thin quad flat pack (TQFP)	100	100	XCB56364FU100
		Quad flat pack (QFP)	112	100	XCB56364PV100

Notes:

1. The DSP56364 can include factory-programmed ROM. The listed 'B' ROM code is a generic unused ROM available to any customer. Variations will be supported for Dolby digital (AC-3), DTS, MPEG2, and other features. These products are only available to authorized licensees of those technologies. Please consult the web site at [www.dspsaudio.motorola.com](http://www.dspsaudio.motorola.com) for current availability.
2. Future products in the DSP56364 family may include other ROM-based options. For additional information on future part development, or to request customer-specific ROM-based support, call your local Motorola Semiconductor sales office or authorized distributor.

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**Freescale Semiconductor, Inc.****APPENDIX A****IBIS MODEL**

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```
IBIS Model
[IBIS Ver]          3.2
[File name]         56364_e.ibs
[File Rev]          e
[Date]              Feb 13, 2002
[Component]         56364
[Manufacturer]      MOTOROLA SEMI CONDUCTOR Ltd.
[Package]
| variable          typ        min        max
R_pkg               45.0m     22.0m     75.0m
L_pkg               2.5nH     1.1nH     4.3nH
C_pkg               1.3pF     1.2pF     1.4pF
[Pin]    signal_name           model_name   R_pin       L_pin
C_pin
1      irqd_                ipad5v_io
2      irqb_                ipad5v_io
3      irqa_                ipad5v_io
4      fst                  ipad5v_io
5      fsr                  ipad5v_io
6      sckt                 ipad5v_io
7      sckr                 ipad5v_io
8      vccs                 power
9      gnds                gnd
10     hckt                ipad5v_io
11     vcclq                power
12     gndq                gnd
13     hckr                ipad5v_io
14     sdo0                 ipad5v_io
15     vcchq                power
16     sdol                 ipad5v_io
17     sdo2/sdi3            ipad5v_io
18     sdo3/sdi2            ipad5v_io
19     sdo4/sdi1            ipad5v_io
20     sdo5/sdi0            ipad5v_io
21     vccs                 power
22     gnds                gnd
23     ss_/ha2              ipad5v_io
24     mosi/ha0              ipad5v_io
25     miso/sda              ipad5i_io
26     sck/scl              ipad5i_io
27     hreq_                ipad5i_io
28     pinit/nmi_
29     reset_                ipad5v_io
31     vccp                 power
32     pcap                 power
33     gndp                 gnd
34     extal                ipadex_i
35     vcchq                power
```

**Freescale Semiconductor, Inc.****IBIS Model**

```
36      gndq          gnd
37      vcclq          power
38      ta_            ipadn_io
39      cas_           ipadm_3st
40      wr_            ipadn_io
41      rd_            ipadn_io
42      vccc            power
43      gndc            gnd
44      aa1/ras1_       ipado_3st
45      aa0/ras0_       ipado_3st
46      a0              ipada_3st
47      a1              ipada_3st
48      vccq            power
49      gndq            gnd
50      a2              ipada_3st
51      a3              ipada_3st
52      a4              ipada_3st
53      a5              ipada_3st
54      a6              ipada_3st
55      vcca            power
56      gnda            gnd
57      a7              ipada_3st
58      a8              ipada_3st
59      a9              ipada_3st
60      a10             ipada_3st
61      vcchq            power
62      a11             ipada_3st
63      vcca            power
64      gnda            gnd
65      gndq            gnd
66      vcclq            power
67      a12             power
68      a13             ipada_3st
69      a14             ipada_3st
70      a15             ipada_3st
71      vcca            power
72      gnda            gnd
73      a16             ipada_3st
74      a17             ipada_3st
75      d0              ipadd_io
76      d1              ipadd_io
77      d2              ipadd_io
78      d3              ipadd_io
79      vccd            power
80      gndd            gnd
81      d4              ipadd_io
82      d5              ipadd_io
83      d6              ipadd_io
84      d7              ipadd_io
87      vcclq            power
88      gndq            gnd
89      vcchq            power
91      gpio0           ipad5v_io
```

```

92          vccs           power
93          gnds          gnd
94          gpio1         ipad5v_io
95          gpio2         ipad5v_io
96          gpio3         ipad5v_io
97          tdo           ipad5f_io
98          tdi           ipad5f_io
99          tck           ipad5f_io
100         tms           ipad5f_io

[Model]          ipad5f_io |   "
Model_type      I/O
Vinl = 0.8
Vinh = 2
| variable      typ     min     max
C_comp          1.96p   1.87p   2.06p
| variable      typ     min     max
[Temperature Range] 40.0   0.0    120.0
| variable      typ     min     max
[Voltage Range]   3.30V   3.00V   3.60V
|
[Pulldown]
| pulldown in the table = pulldown subtract gnd_clamp
| Voltage       I(typ)   I(min)   I(max)
|
-3.30V        -142.303u -76.239u -215.182u
-3.20V        -149.700u -80.226u -226.432u
-3.10V        -157.861u -84.616u -238.866u
-3.00V        -166.908u -89.472u -252.678u
-2.90V        -176.992u -94.869u -268.107u
-2.80V        -188.295u -100.900u -285.446u
-2.70V        -201.049u -107.679u -305.068u
-2.60V        -215.545u -115.349u -327.446u
-2.50V        -232.155u -124.094u -353.191u
-2.40V        -251.367u -134.145u -383.107u
-2.30V        -273.825u -145.808u -418.273u
-2.20V        -300.403u -159.488u -460.167u
-2.10V        -332.314u -175.737u -510.874u
-2.00V        -371.286u -195.318u -573.418u
-1.90V        -419.868u -219.325u -652.360u
-1.80V        -481.968u -249.369u -754.892u
-1.70V        -563.882u -287.925u -893.013u
-1.60V        -676.382u -338.973u -1.088m
-1.50V        -839.410u -409.300u -1.383m
-1.40V        -1.094m  -511.367u -1.873m
-1.30V        -1.537m  -670.350u -2.819m
-1.20V        -2.451m  -943.845u -5.162m
-1.10V        -4.857m  -1.486m -12.214m
-1.00V        -10.606m -2.746m -20.764m
-0.90V        -14.267m -5.259m -21.749m
-0.80V        -13.851m -7.108m -20.142m
-0.70V        -12.481m -7.168m -18.211m
-0.60V        -10.883m -6.348m -15.981m

```

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-0.50V	-9.156m	-5.339m	-13.503m
-0.40V	-7.378m	-4.288m	-10.922m
-0.30V	-5.572m	-3.224m	-8.282m
-0.20V	-3.741m	-2.154m	-5.584m
-0.10V	-1.885m	-1.080m	-2.825m
0.00V	1.898p	1.419p	1.871p
0.10V	1.857m	1.057m	2.800m
0.20V	3.630m	2.064m	5.482m
0.30V	5.323m	3.023m	8.052m
0.40V	6.936m	3.935m	10.508m
0.50V	8.467m	4.798m	12.849m
0.60V	9.915m	5.611m	15.073m
0.70V	11.275m	6.371m	17.176m
0.80V	12.546m	7.078m	19.155m
0.90V	13.723m	7.726m	21.011m
1.00V	36.925m	20.745m	56.704m
1.10V	39.391m	22.074m	60.708m
1.20V	41.612m	23.244m	64.383m
1.30V	43.585m	24.247m	67.726m
1.40V	45.305m	25.079m	70.735m
1.50V	46.773m	25.741m	73.414m
1.60V	47.997m	26.251m	75.766m
1.70V	48.985m	26.633m	77.783m
1.80V	49.733m	26.905m	79.441m
1.90V	50.257m	27.092m	80.724m
2.00V	50.612m	27.223m	81.651m
2.10V	50.858m	27.321m	82.294m
2.20V	51.040m	27.399m	82.744m
2.30V	51.182m	27.465m	83.074m
2.40V	51.302m	27.522m	83.332m
2.50V	51.405m	27.572m	83.543m
2.60V	51.497m	27.618m	83.724m
2.70V	51.581m	27.657m	83.884m
2.80V	51.658m	27.674m	84.030m
2.90V	51.727m	27.587m	84.165m
3.00V	51.757m	27.577m	84.290m
3.10V	51.229m	28.700m	84.409m
3.20V	49.190m	30.042m	84.515m
3.30V	49.441m	31.171m	84.491m
3.40V	51.034m	32.199m	81.077m
3.50V	54.363m	33.153m	79.736m
3.60V	57.165m	34.039m	80.276m
3.70V	58.834m	34.872m	82.430m
3.80V	60.328m	35.686m	85.482m
3.90V	61.725m	36.495m	91.743m
4.00V	63.035m	37.291m	94.219m
4.10V	64.319m	38.051m	96.276m
4.20V	65.598m	38.755m	98.249m
4.30V	66.836m	39.394m	100.059m
4.40V	67.999m	39.962m	101.849m
4.50V	69.069m	40.453m	103.628m
4.60V	70.046m	40.840m	105.345m
4.70V	70.938m	41.065m	106.956m

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4.80V      71.751m   40.952m   108.448m
4.90V      72.476m   40.067m   109.826m
5.00V      73.089m   39.395m   111.106m
5.10V      73.531m   39.313m   112.297m
5.20V      73.651m   39.358m   113.400m
5.30V      72.901m   39.410m   114.401m
5.40V      71.005m   39.460m   115.267m
5.50V      70.389m   39.508m   115.917m
5.60V      70.321m   39.552m   116.139m
5.70V      70.361m   39.595m   114.582m
5.80V      70.422m   39.634m   111.344m
5.90V      70.489m   39.672m   110.612m
6.00V      70.557m   39.708m   110.449m
6.10V      70.624m   39.743m   110.455m
6.20V      70.690m   39.777m   110.515m
6.30V      70.753m   39.812m   110.595m
6.40V      70.817m   39.848m   110.686m
6.50V      70.881m   39.886m   110.783m
6.60V      70.949m   39.929m   110.885m

|
[Pullup]
| pullup in the table = pullup subtract power_clamp
| Voltage      I(typ)    I(min)    I(max)
|
-3.30V      75.797u   7.914u    161.477u
-3.20V      90.464u   17.699u   181.779u
-3.10V      105.160u   27.445u   202.314u
-3.00V      119.836u   37.119u   223.007u
-2.90V      134.451u   46.694u   243.785u
-2.80V      148.966u   56.144u   264.581u
-2.70V      163.342u   65.447u   285.332u
-2.60V      177.543u   74.582u   305.982u
-2.50V      191.536u   83.527u   326.474u
-2.40V      205.285u   92.262u   346.757u
-2.30V      218.754u   100.766u  366.776u
-2.20V      231.907u   109.016u  386.478u
-2.10V      244.706u   116.988u  405.807u
-2.00V      257.106u   124.659u  424.699u
-1.90V      269.061u   131.998u  443.089u
-1.80V      280.519u   138.978u  460.899u
-1.70V      291.423u   145.565u  478.046u
-1.60V      301.710u   151.723u  494.457u
-1.50V      311.348u   157.417u  521.406u
-1.40V      729.899u   162.626u   1.612m
-1.30V      10.510m   445.517u   14.832m
-1.20V      9.629m    6.444m    13.576m
-1.10V      8.670m    5.833m    12.231m
-1.00V      7.693m    5.190m    10.854m
-0.90V      6.732m    4.551m    9.483m
-0.80V      5.825m    3.942m    8.169m
-0.70V      5.004m    3.382m    6.971m
-0.60V      4.261m    2.869m    5.921m
-0.50V      3.549m    2.381m    4.953m

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-0.40V	2.841m	1.902m	3.978m
-0.30V	2.135m	1.426m	2.987m
-0.20V	1.437m	951.489u	2.003m
-0.10V	722.340u	478.341u	1.005m
-0.00V	22.329p	3.311p	24.081p
0.10V	-708.556u	-465.927u	-990.647u
0.20V	-1.377m	-903.637u	-1.943m
0.30V	-2.007m	-1.319m	-2.832m
0.40V	-2.614m	-1.710m	-3.702m
0.50V	-3.192m	-2.079m	-4.537m
0.60V	-3.738m	-2.423m	-5.336m
0.70V	-4.253m	-2.742m	-6.096m
0.80V	-4.736m	-3.037m	-6.817m
0.90V	-5.185m	-3.305m	-7.499m
1.00V	-5.600m	-3.547m	-8.139m
1.10V	-5.980m	-3.762m	-8.737m
1.20V	-6.324m	-3.948m	-9.292m
1.30V	-6.631m	-17.709m	-9.802m
1.40V	-29.730m	-18.279m	-10.265m
1.50V	-30.749m	-18.747m	-45.983m
1.60V	-31.630m	-19.131m	-47.620m
1.70V	-32.393m	-19.454m	-49.086m
1.80V	-33.055m	-19.730m	-50.392m
1.90V	-33.632m	-19.973m	-51.551m
2.00V	-34.135m	-20.188m	-52.571m
2.10V	-34.575m	-20.381m	-53.463m
2.20V	-34.960m	-20.556m	-54.240m
2.30V	-35.302m	-20.715m	-54.917m
2.40V	-35.608m	-20.861m	-55.510m
2.50V	-35.884m	-20.997m	-56.035m
2.60V	-36.137m	-21.123m	-56.505m
2.70V	-36.370m	-21.241m	-56.932m
2.80V	-36.586m	-21.352m	-57.322m
2.90V	-36.788m	-21.457m	-57.683m
3.00V	-36.978m	-21.556m	-58.019m
3.10V	-37.157m	-21.650m	-58.334m
3.20V	-37.327m	-21.741m	-58.631m
3.30V	-37.489m	-21.827m	-58.913m
3.40V	-37.643m	-21.909m	-59.181m
3.50V	-37.791m	-21.989m	-59.436m
3.60V	-37.933m	-22.067m	-59.681m
3.70V	-38.070m	-22.143m	-59.916m
3.80V	-38.202m	-22.216m	-60.142m
3.90V	-38.332m	-22.284m	-60.361m
4.00V	-38.460m	-22.352m	-60.573m
4.10V	-38.590m	-22.420m	-60.780m
4.20V	-38.714m	-22.490m	-60.986m
4.30V	-38.828m	-22.561m	-61.194m
4.40V	-38.949m	-22.635m	-61.406m
4.50V	-39.076m	-22.713m	-61.623m
4.60V	-39.211m	-22.798m	-61.819m
4.70V	-39.357m	-22.892m	-62.024m
4.80V	-39.516m	-22.997m	-62.254m

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4.90V	-39.693m	-23.116m	-62.506m
5.00V	-39.893m	-23.253m	-62.785m
5.10V	-40.121m	-23.411m	-63.098m
5.20V	-40.384m	-23.595m	-63.453m
5.30V	-40.689m	-23.801m	-63.860m
5.40V	-41.043m	-24.032m	-64.330m
5.50V	-41.444m	-24.288m	-64.874m
5.60V	-41.886m	-24.570m	-65.505m
5.70V	-42.370m	-24.880m	-66.214m
5.80V	-42.899m	-25.217m	-66.983m
5.90V	-43.473m	-25.585m	-67.815m
6.00V	-44.095m	-25.983m	-68.711m
6.10V	-44.769m	-26.415m	-69.678m
6.20V	-45.498m	-26.884m	-70.721m
6.30V	-46.287m	-27.390m	-71.848m
6.40V	-47.140m	-27.929m	-73.065m
6.50V	-48.049m	-28.487m	-74.374m
6.60V	-48.990m	-29.080m	-75.748m
[GND_clamp]			
Voltage	I(typ)	I(min)	I(max)
-3.30V	-1.875	-1.074	-2.155
-3.20V	-1.793	-1.029	-2.059
-3.10V	-1.711	-983.765m	-1.963
-2.90V	-1.548	-893.931m	-1.771
-2.80V	-1.466	-849.071m	-1.675
-2.70V	-1.385	-804.256m	-1.579
-2.60V	-1.303	-759.489m	-1.483
-2.50V	-1.221	-714.777m	-1.388
-2.40V	-1.140	-670.127m	-1.292
-2.30V	-1.059	-625.548m	-1.197
-2.20V	-977.735m	-581.048m	-1.102
-2.10V	-896.773m	-536.642m	-1.007
-1.90V	-735.446m	-448.177m	-817.634m
-1.80V	-655.171m	-404.164m	-723.409m
-1.70V	-575.242m	-360.342m	-629.587m
-1.60V	-495.760m	-316.758m	-536.295m
-1.50V	-416.878m	-273.482m	-443.730m
-1.40V	-338.839m	-230.618m	-352.222m
-1.30V	-262.067m	-188.327m	-262.384m
-1.20V	-187.395m	-146.891m	-175.533m
-1.10V	-116.756m	-106.839m	-95.231m
-0.90V	-16.024m	-37.029m	-6.612m
-0.80V	-2.254m	-14.319m	-2.370m
-0.70V	-476.015u	-2.883m	-845.181u
-0.60V	-85.877u	-295.354u	-147.930u
-0.50V	-8.033u	-33.637u	-9.999u
-0.40V	-432.304n	-3.576u	-310.975n
-0.30V	-20.874n	-340.944n	-8.593n
-0.20V	-964.564p	-30.895n	-258.649p
-0.10V	-72.583p	-2.560n	-43.910p

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0.00V	-33.685p	-210.508p	-34.610p
0.10V	-27.665p	-30.628p	-29.748p
0.20V	-22.754p	13.546p	-25.110p
0.30V	-18.303p	48.356p	-20.906p
0.40V	-14.129p	81.869p	-16.971p
0.50V	-9.979p	114.849p	-13.050p
0.60V	-5.833p	147.499p	-9.130p
0.70V	-1.689p	179.924p	-5.210p
0.80V	2.454p	212.188p	-1.291p
0.90V	6.596p	244.335p	2.628p
1.10V	14.877p	308.388p	10.466p
1.20V	19.017p	340.335p	14.384p
1.30V	23.157p	372.250p	18.302p
1.40V	27.297p	404.143p	22.221p
1.50V	31.436p	436.027p	26.139p
1.60V	35.576p	467.910p	30.057p
1.70V	39.715p	499.805p	33.974p
1.80V	43.855p	531.722p	37.892p
1.90V	47.995p	563.675p	41.810p
2.10V	56.277p	627.761p	49.646p
2.20V	60.418p	659.933p	53.564p
2.30V	64.561p	692.106p	57.482p
2.40V	68.706p	723.142p	61.400p
2.50V	72.847p	751.973p	65.319p
2.60V	76.869p	780.264p	69.237p
2.70V	80.074p	808.442p	73.156p
2.80V	82.499p	835.513p	77.065p
2.90V	84.837p	860.391p	80.794p
3.10V	89.018p	1.265n	86.195p
3.20V	89.573p	1.305n	88.344p
3.30V	103.108p	1.593n	90.478p
<hr/>			
[POWER_clamp]			
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Voltage	I(typ)	I(min)	I(max)
3.30V	-33.685p	-340.944n	-20.906p
3.40V	-72.583p	-3.576u	-25.110p
3.50V	-964.564p	-33.637u	-29.748p
3.60V	-20.874n	-295.354u	-34.610p
3.70V	-432.304n	-2.883m	-43.910p
3.80V	-8.033u	-14.319m	-258.649p
3.90V	-85.877u	-37.029m	-8.593n
4.10V	-2.254m	-106.839m	-9.999u
4.20V	-16.024m	-146.891m	-147.930u
4.30V	-55.636m	-188.327m	-845.181u
4.40V	-116.756m	-230.618m	-2.370m
4.50V	-187.395m	-273.482m	-6.612m
4.60V	-262.067m	-316.758m	-33.199m
4.70V	-338.839m	-360.342m	-95.231m
4.80V	-416.878m	-404.164m	-175.533m
4.90V	-495.760m	-448.177m	-262.384m
5.10V	-655.171m	-536.642m	-443.730m

**Freescale Semiconductor, Inc.****IBIS Model**

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5.20V      -735.446m -581.048m -536.295m
5.30V      -815.997m -625.548m -629.587m
5.40V      -896.773m -670.127m -723.409m
5.50V      -977.735m -714.777m -817.634m
5.60V      -1.059   -759.489m -912.174m
5.70V      -1.140   -804.256m   -1.007
5.80V      -1.221   -849.071m   -1.102
5.90V      -1.303   -893.931m   -1.197
6.10V      -1.466   -983.765m   -1.388
6.20V      -1.548   -1.029     -1.483
6.30V      -1.630   -1.074     -1.579
6.40V      -1.711   -1.119     -1.675
6.50V      -1.793   -1.164     -1.771
6.60V      -1.875   -1.209     -1.867

|
[Ramp]
|Voltage      I(typ)      I(min)      I(max)
|
dV/dt_f    2.04/136.004p 1.86/237.542p 2.23/85.504p
|
dV/dt_r    2.05/194.744p 1.86/343.805p 2.23/118.850p
R_load=10000ohms
|R_load was connected to ground for Ramp_up test and power for Ramp_dn
test
|
|End model
[Model]          ipad5i_io           |   "
Model_type     I/O
Vinl = 0.8
Vinh = 2
| variable      typ        min        max
C_comp         4.44p     3.89p     4.56p
| variable      typ        min        max
[Temperature Range] 40.0     0.0       120.0
| variable      typ        min        max
[Voltage Range]   3.30V     3.00V     3.60V
|
[Pulldown]
| pulldown in the table = pulldown subtract gnd_clamp
|Voltage      I(typ)      I(min)      I(max)
|
-3.30V      -142.303u  -76.239u  -215.182u
-3.20V      -149.700u  -80.226u  -226.432u
-3.10V      -157.861u  -84.616u  -238.866u
-3.00V      -166.908u  -89.472u  -252.678u
-2.90V      -176.992u  -94.869u  -268.107u
-2.80V      -188.295u  -100.900u  -285.446u
-2.70V      -201.049u  -107.679u  -305.068u
-2.60V      -215.545u  -115.349u  -327.446u
-2.50V      -232.155u  -124.094u  -353.191u
-2.40V      -251.367u  -134.145u  -383.107u
-2.30V      -273.825u  -145.808u  -418.273u
-2.20V      -300.403u  -159.488u  -460.167u

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**Freescale Semiconductor, Inc.****IBIS Model**

-2.10V	-332.314u	-175.737u	-510.874u
-2.00V	-371.286u	-195.318u	-573.418u
-1.90V	-419.868u	-219.325u	-652.360u
-1.80V	-481.968u	-249.369u	-754.892u
-1.70V	-563.882u	-287.925u	-893.013u
-1.60V	-676.382u	-338.973u	-1.088m
-1.50V	-839.410u	-409.300u	-1.383m
-1.40V	-1.094m	-511.367u	-1.873m
-1.30V	-1.537m	-670.350u	-2.819m
-1.20V	-2.451m	-943.845u	-5.162m
-1.10V	-4.857m	-1.486m	-12.214m
-1.00V	-10.606m	-2.746m	-20.764m
-0.90V	-14.267m	-5.259m	-21.749m
-0.80V	-13.851m	-7.108m	-20.142m
-0.70V	-12.481m	-7.168m	-18.211m
-0.60V	-10.883m	-6.348m	-15.981m
-0.50V	-9.156m	-5.339m	-13.503m
-0.40V	-7.378m	-4.288m	-10.922m
-0.30V	-5.572m	-3.224m	-8.282m
-0.20V	-3.741m	-2.154m	-5.584m
-0.10V	-1.885m	-1.080m	-2.825m
0.00V	1.898p	1.419p	1.871p
0.10V	1.857m	1.057m	2.800m
0.20V	3.630m	2.064m	5.482m
0.30V	5.323m	3.023m	8.052m
0.40V	6.936m	3.935m	10.508m
0.50V	8.467m	4.798m	12.849m
0.60V	9.915m	5.611m	15.073m
0.70V	11.275m	6.371m	17.176m
0.80V	12.546m	7.078m	19.155m
0.90V	13.723m	7.726m	21.011m
1.00V	36.925m	20.745m	56.704m
1.10V	39.391m	22.074m	60.708m
1.20V	41.612m	23.244m	64.383m
1.30V	43.585m	24.247m	67.726m
1.40V	45.305m	25.079m	70.735m
1.50V	46.773m	25.741m	73.414m
1.60V	47.997m	26.251m	75.766m
1.70V	48.985m	26.633m	77.783m
1.80V	49.733m	26.905m	79.441m
1.90V	50.257m	27.092m	80.724m
2.00V	50.612m	27.223m	81.651m
2.10V	50.858m	27.321m	82.294m
2.20V	51.040m	27.399m	82.744m
2.30V	51.182m	27.465m	83.074m
2.40V	51.302m	27.522m	83.332m
2.50V	51.405m	27.572m	83.543m
2.60V	51.497m	27.618m	83.724m
2.70V	51.581m	27.658m	83.884m
2.80V	51.658m	27.683m	84.030m
2.90V	51.729m	27.643m	84.165m
3.00V	51.781m	27.704m	84.290m
3.10V	51.640m	28.793m	84.409m

**Freescale Semiconductor, Inc.****IBIS Model**


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Voltage	I(typ)	I(min)	I(max)
3.20V	50.282m	30.065m	84.519m
3.30V	50.273m	31.174m	84.574m
3.40V	51.871m	32.200m	83.365m
3.50V	55.121m	33.153m	80.948m
3.60V	57.228m	34.039m	81.423m
3.70V	58.838m	34.872m	83.424m
3.80V	60.328m	35.687m	87.158m
3.90V	61.725m	36.498m	91.951m
4.00V	63.035m	37.296m	94.228m
4.10V	64.321m	38.059m	96.276m
4.20V	65.602m	38.767m	98.249m
4.30V	66.844m	39.409m	100.060m
4.40V	68.012m	39.982m	101.853m
4.50V	69.088m	40.478m	103.638m
4.60V	70.072m	40.871m	105.361m
4.70V	70.973m	41.102m	106.982m
4.80V	71.794m	40.996m	108.484m
4.90V	72.529m	40.118m	109.875m
5.00V	73.152m	39.453m	111.168m
5.10V	73.605m	39.379m	112.374m
5.20V	73.737m	39.432m	113.492m
5.30V	72.999m	39.492m	114.510m
5.40V	71.115m	39.551m	115.392m
5.50V	70.512m	39.608m	116.061m
5.60V	70.457m	39.661m	116.301m
5.70V	70.511m	39.713m	114.763m
5.80V	70.586m	39.762m	111.545m
5.90V	70.667m	39.809m	110.833m
6.00V	70.749m	39.855m	110.689m
6.10V	70.831m	39.899m	110.716m
6.20V	70.911m	39.944m	110.796m
6.30V	70.989m	39.988m	110.897m
6.40V	71.068m	40.034m	111.009m
6.50V	71.148m	40.083m	111.127m
6.60V	71.230m	40.136m	111.250m
[Pullup]			
pullup in the table = pullup subtract power_clamp			
Voltage	I(typ)	I(min)	I(max)
-3.30V	357.190u	184.381u	591.381u
-3.20V	356.622u	184.121u	590.188u
-3.10V	356.193u	183.920u	589.287u
-3.00V	355.875u	183.765u	588.617u
-2.90V	355.641u	183.645u	588.129u
-2.80V	355.468u	183.550u	587.779u
-2.70V	355.340u	183.472u	587.528u
-2.60V	355.242u	183.405u	587.349u
-2.50V	355.163u	183.345u	587.218u
-2.40V	355.097u	183.288u	587.118u
-2.30V	355.036u	183.233u	587.036u
-2.20V	354.978u	183.177u	586.964u
-2.10V	354.920u	183.119u	586.896u

**Freescale Semiconductor, Inc.****IBIS Model**

-2.00V	354.860u	183.060u	586.829u
-1.90V	354.799u	182.997u	586.762u
-1.80V	354.734u	182.931u	586.692u
-1.70V	354.666u	182.862u	586.621u
-1.60V	354.595u	182.788u	586.574u
-1.50V	354.559u	182.711u	597.934u
-1.40V	764.198u	182.650u	1.674m
-1.30V	10.536m	460.815u	14.880m
-1.20V	9.648m	6.455m	13.612m
-1.10V	8.683m	5.841m	12.257m
-1.00V	7.701m	5.195m	10.870m
-0.90V	6.737m	4.554m	9.492m
-0.80V	5.827m	3.944m	8.173m
-0.70V	5.004m	3.383m	6.972m
-0.60V	4.262m	2.870m	5.921m
-0.50V	3.549m	2.382m	4.953m
-0.40V	2.841m	1.902m	3.978m
-0.30V	2.134m	1.426m	2.985m
-0.20V	1.434m	951.249u	2.002m
-0.10V	721.882u	477.946u	1.005m
-0.00V	23.094p	36.805p	24.891p
0.10V	-708.040u	-465.659u	-990.277u
0.20V	-1.374m	-903.549u	-1.941m
0.30V	-2.007m	-1.319m	-2.832m
0.40V	-2.614m	-1.710m	-3.702m
0.50V	-3.192m	-2.079m	-4.537m
0.60V	-3.738m	-2.423m	-5.336m
0.70V	-4.253m	-2.742m	-6.096m
0.80V	-4.736m	-3.037m	-6.817m
0.90V	-5.185m	-3.305m	-7.499m
1.00V	-5.600m	-3.547m	-8.139m
1.10V	-5.980m	-3.762m	-8.737m
1.20V	-6.324m	-3.948m	-9.292m
1.30V	-6.631m	-17.709m	-9.802m
1.40V	-29.730m	-18.279m	-10.265m
1.50V	-30.749m	-18.747m	-45.983m
1.60V	-31.630m	-19.131m	-47.620m
1.70V	-32.393m	-19.454m	-49.086m
1.80V	-33.055m	-19.730m	-50.392m
1.90V	-33.632m	-19.973m	-51.551m
2.00V	-34.135m	-20.188m	-52.571m
2.10V	-34.575m	-20.381m	-53.463m
2.20V	-34.960m	-20.556m	-54.240m
2.30V	-35.302m	-20.715m	-54.917m
2.40V	-35.608m	-20.861m	-55.510m
2.50V	-35.884m	-20.997m	-56.035m
2.60V	-36.137m	-21.123m	-56.505m
2.70V	-36.370m	-21.241m	-56.932m
2.80V	-36.586m	-21.352m	-57.322m
2.90V	-36.788m	-21.457m	-57.683m
3.00V	-36.978m	-21.556m	-58.019m
3.10V	-37.157m	-21.650m	-58.334m
3.20V	-37.327m	-21.741m	-58.631m

**Freescale Semiconductor, Inc.****IBIS Model**

3.30V	-37.489m	-21.827m	-58.913m
3.40V	-37.643m	-21.909m	-59.181m
3.50V	-37.791m	-21.989m	-59.436m
3.60V	-37.933m	-22.067m	-59.681m
3.70V	-38.070m	-22.143m	-59.916m
3.80V	-38.202m	-22.216m	-60.142m
3.90V	-38.332m	-22.284m	-60.361m
4.00V	-38.460m	-22.352m	-60.573m
4.10V	-38.590m	-22.420m	-60.780m
4.20V	-38.714m	-22.490m	-60.986m
4.30V	-38.828m	-22.561m	-61.194m
4.40V	-38.949m	-22.635m	-61.406m
4.50V	-39.076m	-22.713m	-61.623m
4.60V	-39.211m	-22.798m	-61.819m
4.70V	-39.357m	-22.892m	-62.024m
4.80V	-39.516m	-22.997m	-62.254m
4.90V	-39.693m	-23.116m	-62.506m
5.00V	-39.893m	-23.253m	-62.785m
5.10V	-40.121m	-23.411m	-63.098m
5.20V	-40.384m	-23.595m	-63.453m
5.30V	-40.689m	-23.801m	-63.860m
5.40V	-41.043m	-24.032m	-64.330m
5.50V	-41.444m	-24.288m	-64.874m
5.60V	-41.886m	-24.570m	-65.505m
5.70V	-42.370m	-24.880m	-66.214m
5.80V	-42.899m	-25.217m	-66.983m
5.90V	-43.473m	-25.585m	-67.815m
6.00V	-44.095m	-25.983m	-68.711m
6.10V	-44.769m	-26.415m	-69.678m
6.20V	-45.498m	-26.884m	-70.721m
6.30V	-46.287m	-27.390m	-71.848m
6.40V	-47.140m	-27.929m	-73.065m
6.50V	-48.049m	-28.487m	-74.374m
6.60V	-48.990m	-29.080m	-75.748m
[GND_clamp]			
Voltage	I(typ)	I(min)	I(max)
-3.30V	-1.875	-1.074	-2.155
-3.20V	-1.793	-1.029	-2.059
-3.10V	-1.711	-983.769m	-1.963
-2.90V	-1.548	-893.934m	-1.771
-2.80V	-1.466	-849.075m	-1.675
-2.70V	-1.385	-804.259m	-1.579
-2.60V	-1.303	-759.493m	-1.483
-2.50V	-1.221	-714.781m	-1.388
-2.40V	-1.140	-670.131m	-1.292
-2.30V	-1.059	-625.551m	-1.197
-2.20V	-977.740m	-581.052m	-1.102
-2.10V	-896.779m	-536.646m	-1.007
-1.90V	-735.452m	-448.180m	-817.639m
-1.80V	-655.177m	-404.167m	-723.415m

# Freescale Semiconductor, Inc.

## IBIS Model

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Voltage	I(typ)	I(min)	I(max)
-1.70V	-575.247m	-360.345m	-629.593m
-1.60V	-495.766m	-316.761m	-536.300m
-1.50V	-416.883m	-273.485m	-443.735m
-1.40V	-338.844m	-230.621m	-352.227m
-1.30V	-262.072m	-188.330m	-262.388m
-1.20V	-187.399m	-146.893m	-175.537m
-1.10V	-116.760m	-106.842m	-95.235m
-0.90V	-16.027m	-37.031m	-6.614m
-0.80V	-2.255m	-14.321m	-2.370m
-0.70V	-476.049u	-2.884m	-845.183u
-0.60V	-85.878u	-295.501u	-147.930u
-0.50V	-8.033u	-33.646u	-9.999u
-0.40V	-432.308n	-3.576u	-310.979n
-0.30V	-20.878n	-340.971n	-8.597n
-0.20V	-968.068p	-30.900n	-262.449p
-0.10V	-75.987p	-2.564n	-47.610p
0.00V	-36.990p	-214.009p	-38.210p
0.10V	-30.869p	-34.018p	-33.249p
0.20V	-25.858p	10.263p	-28.510p
0.30V	-21.307p	45.181p	-24.206p
0.40V	-17.033p	78.801p	-20.171p
0.50V	-12.783p	111.888p	-16.150p
0.60V	-8.537p	144.645p	-12.130p
0.70V	-4.293p	177.177p	-8.110p
0.80V	-49.635f	209.548p	-4.091p
0.90V	4.192p	241.802p	-71.907f
1.10V	12.674p	306.070p	7.965p
1.20V	16.914p	338.124p	11.984p
1.30V	21.154p	370.146p	16.002p
1.40V	25.393p	402.147p	20.020p
1.50V	29.633p	434.138p	24.038p
1.60V	-31.788p	466.129p	28.056p
1.70V	38.112p	498.131p	-33.622p
1.80V	42.352p	530.156p	36.092p
1.90V	46.592p	562.217p	40.110p
2.10V	55.074p	626.519p	48.146p
2.20V	59.316p	658.799p	52.164p
2.30V	63.559p	691.080p	56.182p
2.40V	67.803p	722.224p	60.200p
2.50V	72.044p	751.129p	64.219p
2.60V	76.162p	779.443p	68.237p
2.70V	79.409p	807.731p	72.256p
2.80V	81.838p	835.534p	76.265p
2.90V	84.178p	864.770p	80.080p
3.10V	88.733p	1.234n	85.501p
3.20V	90.025p	1.247n	87.652p
3.30V	96.129p	1.274n	89.793p
[POWER_clamp]			
Voltage			
I(typ) I(min) I(max)			
3.30V -36.990p -340.971n -24.206p			

**Freescale Semiconductor, Inc.****IBIS Model**

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3.40V      -75.987p   -3.576u   -28.510p
3.50V      -968.068p   -33.646u   -33.249p
3.60V      -20.878n   -295.501u   -38.210p
3.70V      -432.308n   -2.884m   -47.610p
3.80V      -8.033u    -14.321m   -262.449p
3.90V      -85.878u   -37.031m   -8.597n
4.10V      -2.255m    -106.842m   -9.999u
4.20V      -16.027m   -146.893m   -147.930u
4.30V      -55.640m   -188.330m   -845.183u
4.40V      -116.760m   -230.621m   -2.370m
4.50V      -187.399m   -273.485m   -6.614m
4.60V      -262.072m   -316.761m   -33.203m
4.70V      -338.844m   -360.345m   -95.235m
4.80V      -416.883m   -404.167m   -175.537m
4.90V      -495.766m   -448.180m   -262.388m
5.10V      -655.177m   -536.646m   -443.735m
5.20V      -735.452m   -581.052m   -536.300m
5.30V      -816.003m   -625.551m   -629.593m
5.40V      -896.779m   -670.131m   -723.415m
5.50V      -977.740m   -714.781m   -817.639m
5.60V      -1.059     -759.493m   -912.179m
5.70V      -1.140     -804.259m   -1.007
5.80V      -1.221     -849.075m   -1.102
5.90V      -1.303     -893.934m   -1.197
6.10V      -1.466     -983.769m   -1.388
6.20V      -1.548     -1.029     -1.483
6.30V      -1.630     -1.074     -1.579
6.40V      -1.711     -1.119     -1.675
6.50V      -1.793     -1.164     -1.771
6.60V      -1.875     -1.209     -1.867

|
[Ramp]
|Voltage      I(typ)      I(min)      I(max)
|
dV/dt_f      2.01/129.093p 1.83/223.594p 2.20/79.668p
|
dV/dt_r      2.02/200.492p 1.83/352.515p 2.20/122.321p
R_load=10000ohms
| R_load was connected to ground for Ramp_up test and power for Ramp_dn
test
|
|End model
[Model]          ipad5v_io
Model_type      I/O
Vinl = 0.8
Vinh = 2
| variable      typ        min        max
C_comp          1.96p     1.87p     2.06p
| variable      typ        min        max
[Temperature Range] 40.0      0.0       120.0
| variable      typ        min        max
[Voltage Range]  3.30V     3.00V     3.60V
|

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# Freescale Semiconductor, Inc.

## IBIS Model

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[Pulldown]			
Voltage	I(typ)	I(min)	I(max)
-3.30V	-142.303u	-76.239u	-215.182u
-3.20V	-149.700u	-80.226u	-226.432u
-3.10V	-157.861u	-84.616u	-238.866u
-3.00V	-166.908u	-89.472u	-252.678u
-2.90V	-176.992u	-94.869u	-268.107u
-2.80V	-188.295u	-100.900u	-285.446u
-2.70V	-201.049u	-107.679u	-305.068u
-2.60V	-215.545u	-115.349u	-327.446u
-2.50V	-232.155u	-124.094u	-353.191u
-2.40V	-251.367u	-134.145u	-383.107u
-2.30V	-273.825u	-145.808u	-418.273u
-2.20V	-300.403u	-159.488u	-460.167u
-2.10V	-332.314u	-175.737u	-510.874u
-2.00V	-371.286u	-195.318u	-573.418u
-1.90V	-419.868u	-219.325u	-652.360u
-1.80V	-481.968u	-249.369u	-754.892u
-1.70V	-563.882u	-287.925u	-893.013u
-1.60V	-676.382u	-338.973u	-1.088m
-1.50V	-839.410u	-409.300u	-1.383m
-1.40V	-1.094m	-511.367u	-1.873m
-1.30V	-1.537m	-670.350u	-2.819m
-1.20V	-2.451m	-943.845u	-5.162m
-1.10V	-4.857m	-1.486m	-12.214m
-1.00V	-10.606m	-2.746m	-20.764m
-0.90V	-14.267m	-5.259m	-21.749m
-0.80V	-13.851m	-7.108m	-20.142m
-0.70V	-12.481m	-7.168m	-18.211m
-0.60V	-10.883m	-6.348m	-15.981m
-0.50V	-9.156m	-5.339m	-13.503m
-0.40V	-7.378m	-4.288m	-10.922m
-0.30V	-5.572m	-3.224m	-8.282m
-0.20V	-3.741m	-2.154m	-5.584m
-0.10V	-1.885m	-1.080m	-2.825m
0.00V	1.898p	1.419p	1.871p
0.10V	1.857m	1.057m	2.800m
0.20V	3.630m	2.064m	5.482m
0.30V	5.323m	3.023m	8.052m
0.40V	6.936m	3.935m	10.508m
0.50V	8.467m	4.798m	12.849m
0.60V	9.915m	5.611m	15.073m
0.70V	11.275m	6.371m	17.176m
0.80V	12.546m	7.078m	19.155m
0.90V	13.723m	7.726m	21.011m
1.00V	36.925m	20.745m	56.704m
1.10V	39.391m	22.074m	60.708m
1.20V	41.612m	23.244m	64.383m
1.30V	43.585m	24.247m	67.726m
1.40V	45.305m	25.079m	70.735m
1.50V	46.773m	25.741m	73.414m

# Freescale Semiconductor, Inc.

IBIS Model

1.60V	47.997m	26.251m	75.766m
1.70V	48.985m	26.633m	77.783m
1.80V	49.733m	26.905m	79.441m
1.90V	50.257m	27.092m	80.724m
2.00V	50.612m	27.223m	81.651m
2.10V	50.858m	27.321m	82.294m
2.20V	51.040m	27.399m	82.744m
2.30V	51.182m	27.465m	83.074m
2.40V	51.302m	27.522m	83.332m
2.50V	51.405m	27.572m	83.543m
2.60V	51.497m	27.618m	83.724m
2.70V	51.581m	27.657m	83.884m
2.80V	51.658m	27.674m	84.030m
2.90V	51.727m	27.587m	84.165m
3.00V	51.757m	27.577m	84.290m
3.10V	51.229m	28.700m	84.409m
3.20V	49.190m	30.042m	84.515m
3.30V	49.441m	31.171m	84.491m
3.40V	51.034m	32.199m	81.077m
3.50V	54.363m	33.153m	79.736m
3.60V	57.165m	34.039m	80.276m
3.70V	58.834m	34.872m	82.430m
3.80V	60.328m	35.686m	85.482m
3.90V	61.725m	36.495m	91.743m
4.00V	63.035m	37.291m	94.219m
4.10V	64.319m	38.051m	96.276m
4.20V	65.598m	38.755m	98.249m
4.30V	66.836m	39.394m	100.059m
4.40V	67.999m	39.962m	101.849m
4.50V	69.069m	40.453m	103.628m
4.60V	70.046m	40.840m	105.345m
4.70V	70.938m	41.065m	106.956m
4.80V	71.751m	40.952m	108.448m
4.90V	72.476m	40.067m	109.826m
5.00V	73.089m	39.395m	111.106m
5.10V	73.531m	39.313m	112.297m
5.20V	73.651m	39.358m	113.400m
5.30V	72.901m	39.410m	114.401m
5.40V	71.005m	39.460m	115.267m
5.50V	70.389m	39.508m	115.917m
5.60V	70.321m	39.552m	116.139m
5.70V	70.361m	39.595m	114.582m
5.80V	70.422m	39.634m	111.344m
5.90V	70.489m	39.672m	110.612m
6.00V	70.557m	39.708m	110.449m
6.10V	70.624m	39.743m	110.455m
6.20V	70.690m	39.777m	110.515m
6.30V	70.753m	39.812m	110.595m
6.40V	70.817m	39.848m	110.686m
6.50V	70.881m	39.886m	110.783m
6.60V	70.949m	39.929m	110.885m

# Freescale Semiconductor, Inc.

## IBIS Model

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[Pullup]			
pullup in the table = pullup subtract power_clamp			
Voltage	I(typ)	I(min)	I(max)
-3.30V	75.797u	7.914u	161.477u
-3.20V	90.464u	17.699u	181.779u
-3.10V	105.160u	27.445u	202.314u
-3.00V	119.836u	37.119u	223.007u
-2.90V	134.451u	46.694u	243.785u
-2.80V	148.966u	56.144u	264.581u
-2.70V	163.342u	65.447u	285.332u
-2.60V	177.543u	74.582u	305.982u
-2.50V	191.536u	83.527u	326.474u
-2.40V	205.285u	92.262u	346.757u
-2.30V	218.754u	100.766u	366.776u
-2.20V	231.907u	109.016u	386.478u
-2.10V	244.706u	116.988u	405.807u
-2.00V	257.106u	124.659u	424.699u
-1.90V	269.061u	131.998u	443.089u
-1.80V	280.519u	138.978u	460.899u
-1.70V	291.423u	145.565u	478.046u
-1.60V	301.710u	151.723u	494.457u
-1.50V	311.348u	157.417u	521.406u
-1.40V	729.899u	162.626u	1.612m
-1.30V	10.510m	445.517u	14.832m
-1.20V	9.629m	6.444m	13.576m
-1.10V	8.670m	5.833m	12.231m
-1.00V	7.693m	5.190m	10.854m
-0.90V	6.732m	4.551m	9.483m
-0.80V	5.825m	3.942m	8.169m
-0.70V	5.004m	3.382m	6.971m
-0.60V	4.261m	2.869m	5.921m
-0.50V	3.549m	2.381m	4.953m
-0.40V	2.841m	1.902m	3.978m
-0.30V	2.135m	1.426m	2.987m
-0.20V	1.437m	951.489u	2.003m
-0.10V	722.340u	478.341u	1.005m
-0.00V	22.329p	36.936p	24.081p
0.10V	-708.556u	-465.927u	-990.647u
0.20V	-1.377m	-903.637u	-1.943m
0.30V	-2.007m	-1.319m	-2.832m
0.40V	-2.614m	-1.710m	-3.702m
0.50V	-3.192m	-2.079m	-4.537m
0.60V	-3.738m	-2.423m	-5.336m
0.70V	-4.253m	-2.742m	-6.096m
0.80V	-4.736m	-3.037m	-6.817m
0.90V	-5.185m	-3.305m	-7.499m
1.00V	-5.600m	-3.547m	-8.139m
1.10V	-5.980m	-3.762m	-8.737m
1.20V	-6.324m	-3.948m	-9.292m
1.30V	-6.631m	-17.709m	-9.802m
1.40V	-29.730m	-18.279m	-10.265m

# Freescale Semiconductor, Inc.

IBIS Model

1.50V	-30.749m	-18.747m	-45.983m
1.60V	-31.630m	-19.131m	-47.620m
1.70V	-32.393m	-19.454m	-49.086m
1.80V	-33.055m	-19.730m	-50.392m
1.90V	-33.632m	-19.973m	-51.551m
2.00V	-34.135m	-20.188m	-52.571m
2.10V	-34.575m	-20.381m	-53.463m
2.20V	-34.960m	-20.556m	-54.240m
2.30V	-35.302m	-20.715m	-54.917m
2.40V	-35.608m	-20.861m	-55.510m
2.50V	-35.884m	-20.997m	-56.035m
2.60V	-36.137m	-21.123m	-56.505m
2.70V	-36.370m	-21.241m	-56.932m
2.80V	-36.586m	-21.352m	-57.322m
2.90V	-36.788m	-21.457m	-57.683m
3.00V	-36.978m	-21.556m	-58.019m
3.10V	-37.157m	-21.650m	-58.334m
3.20V	-37.327m	-21.741m	-58.631m
3.30V	-37.489m	-21.827m	-58.913m
3.40V	-37.643m	-21.909m	-59.181m
3.50V	-37.791m	-21.989m	-59.436m
3.60V	-37.933m	-22.067m	-59.681m
3.70V	-38.070m	-22.143m	-59.916m
3.80V	-38.202m	-22.216m	-60.142m
3.90V	-38.332m	-22.284m	-60.361m
4.00V	-38.460m	-22.352m	-60.573m
4.10V	-38.590m	-22.420m	-60.780m
4.20V	-38.714m	-22.490m	-60.986m
4.30V	-38.828m	-22.561m	-61.194m
4.40V	-38.949m	-22.635m	-61.406m
4.50V	-39.076m	-22.713m	-61.623m
4.60V	-39.211m	-22.798m	-61.819m
4.70V	-39.357m	-22.892m	-62.024m
4.80V	-39.516m	-22.997m	-62.254m
4.90V	-39.693m	-23.116m	-62.506m
5.00V	-39.893m	-23.253m	-62.785m
5.10V	-40.121m	-23.411m	-63.098m
5.20V	-40.384m	-23.595m	-63.453m
5.30V	-40.689m	-23.801m	-63.860m
5.40V	-41.043m	-24.032m	-64.330m
5.50V	-41.444m	-24.288m	-64.874m
5.60V	-41.886m	-24.570m	-65.505m
5.70V	-42.370m	-24.880m	-66.214m
5.80V	-42.899m	-25.217m	-66.983m
5.90V	-43.473m	-25.585m	-67.815m
6.00V	-44.095m	-25.983m	-68.711m
6.10V	-44.769m	-26.415m	-69.678m
6.20V	-45.498m	-26.884m	-70.721m
6.30V	-46.287m	-27.390m	-71.848m
6.40V	-47.140m	-27.929m	-73.065m
6.50V	-48.049m	-28.487m	-74.374m
6.60V	-48.990m	-29.080m	-75.748m

# Freescale Semiconductor, Inc.

## IBIS Model

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[GND_clamp]			
Voltage	I(typ)	I(min)	I(max)
-3.30V	-1.875	-1.074	-2.155
-3.20V	-1.793	-1.029	-2.059
-3.10V	-1.711	-983.765m	-1.963
-2.90V	-1.548	-893.931m	-1.771
-2.80V	-1.466	-849.071m	-1.675
-2.70V	-1.385	-804.256m	-1.579
-2.60V	-1.303	-759.489m	-1.483
-2.50V	-1.221	-714.777m	-1.388
-2.40V	-1.140	-670.127m	-1.292
-2.30V	-1.059	-625.548m	-1.197
-2.20V	-977.735m	-581.048m	-1.102
-2.10V	-896.773m	-536.642m	-1.007
-1.90V	-735.446m	-448.177m	-817.634m
-1.80V	-655.171m	-404.164m	-723.409m
-1.70V	-575.242m	-360.342m	-629.587m
-1.60V	-495.760m	-316.758m	-536.295m
-1.50V	-416.878m	-273.482m	-443.730m
-1.40V	-338.839m	-230.618m	-352.222m
-1.30V	-262.067m	-188.327m	-262.384m
-1.20V	-187.395m	-146.891m	-175.533m
-1.10V	-116.756m	-106.839m	-95.231m
-0.90V	-16.024m	-37.029m	-6.612m
-0.80V	-2.254m	-14.319m	-2.370m
-0.70V	-476.015u	-2.883m	-845.181u
-0.60V	-85.877u	-295.354u	-147.930u
-0.50V	-8.033u	-33.637u	-9.999u
-0.40V	-432.304n	-3.576u	-310.975n
-0.30V	-20.874n	-340.944n	-8.593n
-0.20V	-964.564p	-30.895n	-258.649p
-0.10V	-72.583p	-2.560n	-43.910p
0.00V	-33.685p	-210.508p	-34.610p
0.10V	-27.665p	-30.628p	-29.748p
0.20V	-22.754p	13.546p	-25.110p
0.30V	-18.303p	48.356p	-20.906p
0.40V	-14.129p	81.869p	-16.971p
0.50V	-9.979p	114.849p	-13.050p
0.60V	-5.833p	147.499p	-9.130p
0.70V	-1.689p	179.924p	-5.210p
0.80V	2.454p	212.188p	-1.291p
0.90V	6.596p	244.335p	2.628p
1.10V	14.877p	308.388p	10.466p
1.20V	19.017p	340.335p	14.384p
1.30V	23.157p	372.250p	18.302p
1.40V	27.297p	404.143p	22.221p
1.50V	31.436p	436.027p	26.139p
1.60V	35.576p	467.910p	30.057p
1.70V	39.715p	499.805p	33.974p
1.80V	43.855p	531.722p	37.892p
1.90V	47.995p	563.675p	41.810p

**Freescale Semiconductor, Inc.****IBIS Model**

2.10V	56.277p	627.761p	49.646p
2.20V	60.418p	659.933p	53.564p
2.30V	64.561p	692.106p	57.482p
2.40V	68.706p	723.142p	61.400p
2.50V	72.847p	751.973p	65.319p
2.60V	76.869p	780.264p	69.237p
2.70V	80.074p	808.442p	73.156p
2.80V	82.499p	835.513p	77.065p
2.90V	84.837p	860.391p	80.794p
3.10V	89.018p	1.265n	86.195p
3.20V	89.573p	1.305n	88.344p
3.30V	103.108p	1.593n	90.478p
[POWER_clamp]			
Voltage	I(typ)	I(min)	I(max)
3.30V	-33.685p	-340.944n	-20.906p
3.40V	-72.583p	-3.576u	-25.110p
3.50V	-964.564p	-33.637u	-29.748p
3.60V	-20.874n	-295.354u	-34.610p
3.70V	-432.304n	-2.883m	-43.910p
3.80V	-8.033u	-14.319m	-258.649p
3.90V	-85.877u	-37.029m	-8.593n
4.10V	-2.254m	-106.839m	-9.999u
4.20V	-16.024m	-146.891m	-147.930u
4.30V	-55.636m	-188.327m	-845.181u
4.40V	-116.756m	-230.618m	-2.370m
4.50V	-187.395m	-273.482m	-6.612m
4.60V	-262.067m	-316.758m	-33.199m
4.70V	-338.839m	-360.342m	-95.231m
4.80V	-416.878m	-404.164m	-175.533m
4.90V	-495.760m	-448.177m	-262.384m
5.10V	-655.171m	-536.642m	-443.730m
5.20V	-735.446m	-581.048m	-536.295m
5.30V	-815.997m	-625.548m	-629.587m
5.40V	-896.773m	-670.127m	-723.409m
5.50V	-977.735m	-714.777m	-817.634m
5.60V	-1.059	-759.489m	-912.174m
5.70V	-1.140	-804.256m	-1.007
5.80V	-1.221	-849.071m	-1.102
5.90V	-1.303	-893.931m	-1.197
6.10V	-1.466	-983.765m	-1.388
6.20V	-1.548	-1.029	-1.483
6.30V	-1.630	-1.074	-1.579
6.40V	-1.711	-1.119	-1.675
6.50V	-1.793	-1.164	-1.771
6.60V	-1.875	-1.209	-1.867
[Ramp]			
Voltage	I(typ)	I(min)	I(max)
dV/dt_f	2.04/134.002p	1.86/235.405p	2.23/85.874p

# Freescale Semiconductor, Inc.

## IBIS Model

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|
dv/dt_r      2.05/194.838p 1.86/341.412p 2.23/118.822p
R_load=10000ohms
| R_load was connected to ground for Ramp_up test and power for Ramp_dn
test
|
|End model
[Model]          ipada_3st           |   "
Model_type       3-state
| variable      typ      min      max
C_comp          2.32p    2.17p    2.48p
| variable      typ      min      max
[Temperature Range] 40.0      0.0     120.0
| variable      typ      min      max
[Voltage Range]   3.30V    3.00V    3.60V
|
[Pulldown]
| pulldown in the table = pulldown subtract gnd_clamp
|Voltage        I(typ)    I(min)   I(max)
|
-3.30V         -157.134u  -99.256u  -219.000u
-3.20V         -165.037u  -104.127u  -230.250u
-3.10V         -173.749u  -109.479u  -242.685u
-3.00V         -183.400u  -115.386u  -256.500u
-2.90V         -194.148u  -121.936u  -271.934u
-2.80V         -206.189u  -129.240u  -289.286u
-2.70V         -219.766u  -137.431u  -308.933u
-2.60V         -235.190u  -146.680u  -331.355u
-2.50V         -252.856u  -157.199u  -357.176u
-2.40V         -273.283u  -169.265u  -387.219u
-2.30V         -297.162u  -183.236u  -422.595u
-2.20V         -325.427u  -199.590u  -464.837u
-2.10V         -359.384u  -218.976u  -516.117u
-2.00V         -400.901u  -242.299u  -579.623u
-1.90V         -452.750u  -270.851u  -660.217u
-1.80V         -519.217u  -306.549u  -765.681u
-1.70V         -607.277u  -352.346u  -909.270u
-1.60V         -729.045u  -413.024u  -1.115m
-1.50V         -907.407u  -496.811u  -1.434m
-1.40V          -1.191m   -619.011u  -1.987m
-1.30V          -1.699m   -811.079u  -3.133m
-1.20V          -2.799m   -1.146m   -6.243m
-1.10V          -5.689m   -1.822m   -12.974m
-1.00V          -10.416m  -3.302m   -17.948m
-0.90V          -12.342m  -5.449m   -17.964m
-0.80V          -11.672m  -6.479m   -16.692m
-0.70V          -10.528m  -6.146m   -15.152m
-0.60V          -9.204m   -5.387m   -13.338m
-0.50V          -7.770m   -4.535m   -11.313m
-0.40V          -6.286m   -3.652m   -9.190m
-0.30V          -4.766m   -2.754m   -6.999m
-0.20V          -3.214m   -1.846m   -4.740m
-0.10V          -1.627m   -928.990u  -2.410m

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# Freescale Semiconductor, Inc.

IBIS Model

0.00V	32.871e-18	18.541e-18	-1.607f
0.10V	1.604m	910.814u	2.391m
0.20V	3.124m	1.775m	4.661m
0.30V	4.566m	2.595m	6.817m
0.40V	5.928m	3.372m	8.858m
0.50V	7.210m	4.105m	10.784m
0.60V	8.411m	4.792m	12.593m
0.70V	9.529m	5.432m	14.284m
0.80V	10.562m	6.023m	15.855m
0.90V	11.508m	6.563m	17.306m
1.00V	12.367m	7.051m	18.639m
1.10V	13.138m	7.486m	19.856m
1.20V	13.821m	7.865m	20.957m
1.30V	14.417m	8.189m	21.944m
1.40V	14.930m	64.562m	22.817m
1.50V	117.094m	66.208m	23.575m
1.60V	119.708m	67.513m	184.138m
1.70V	121.667m	68.498m	187.874m
1.80V	123.055m	69.206m	190.647m
1.90V	124.020m	69.710m	192.621m
2.00V	124.711m	70.083m	194.017m
2.10V	125.232m	70.374m	195.034m
2.20V	125.650m	70.612m	195.815m
2.30V	126.000m	70.814m	196.447m
2.40V	126.305m	70.992m	196.983m
2.50V	126.577m	71.151m	197.453m
2.60V	126.823m	71.296m	197.876m
2.70V	127.050m	71.428m	198.263m
2.80V	127.260m	71.551m	198.622m
2.90V	127.457m	71.666m	198.958m
3.00V	127.643m	71.774m	199.275m
3.10V	127.818m	71.876m	199.576m
3.20V	127.986m	71.973m	199.863m
3.30V	128.147m	72.066m	200.138m
3.40V	128.304m	72.156m	200.405m
3.50V	128.458m	72.245m	200.667m
3.60V	128.614m	72.335m	200.928m
3.70V	128.776m	72.428m	201.194m
3.80V	128.948m	72.527m	201.472m
3.90V	129.140m	72.638m	201.774m
4.00V	129.361m	72.764m	202.113m
4.10V	129.621m	72.914m	202.503m
4.20V	129.934m	73.093m	202.966m
4.30V	130.316m	73.311m	203.524m
4.40V	130.784m	73.579m	204.203m
4.50V	131.358m	73.906m	205.033m
4.60V	132.060m	74.304m	206.045m
4.70V	132.912m	74.787m	207.276m
4.80V	133.939m	75.368m	208.763m
4.90V	135.166m	76.060m	210.544m
5.00V	136.619m	76.878m	212.659m
5.10V	138.324m	77.836m	215.149m
5.20V	140.308m	78.948m	218.056m

# Freescale Semiconductor, Inc.

## IBIS Model

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Voltage	I(typ)	I(min)	I(max)
<b>[Pullup]</b>			
pullup in the table = pullup subtract power_clamp			
-3.30V	132.979u	100.794u	170.075u
-3.20V	138.984u	105.115u	178.000u
-3.10V	145.559u	109.825u	186.702u
-3.00V	152.789u	114.981u	196.300u
-2.90V	160.778u	120.648u	206.941u
-2.80V	169.651u	126.906u	218.803u
-2.70V	179.562u	133.852u	232.110u
-2.60V	190.706u	141.605u	247.141u
-2.50V	203.326u	150.317u	264.253u
-2.40V	217.736u	160.174u	283.910u
-2.30V	234.344u	171.418u	306.723u
-2.20V	253.692u	184.362u	333.513u
-2.10V	276.513u	199.421u	365.415u
-2.00V	303.830u	217.155u	404.033u
-1.90V	337.102u	238.340u	451.722u
-1.80V	378.494u	264.081u	512.067u
-1.70V	431.351u	296.004u	590.810u
-1.60V	501.113u	336.601u	697.730u
-1.50V	597.240u	389.880u	850.877u
-1.40V	737.641u	462.700u	1.087m
-1.30V	960.395u	567.748u	1.497m
-1.20V	1.361m	731.012u	2.348m
-1.10V	2.237m	1.013m	4.712m
-1.00V	4.644m	1.583m	10.148m
-0.90V	8.090m	2.907m	12.062m
-0.80V	8.032m	4.727m	11.029m
-0.70V	7.118m	4.754m	9.778m
-0.60V	6.128m	4.128m	8.443m
-0.50V	5.109m	3.441m	7.052m
-0.40V	4.082m	2.746m	5.644m
-0.30V	3.056m	2.053m	4.233m
-0.20V	2.033m	1.363m	2.821m
-0.10V	1.014m	678.856u	1.410m
-0.00V	58.687e-18	58.622e-18	117.504e-18

# Freescale Semiconductor, Inc.

IBIS Model

0.10V	-987.106u	-655.604u	-1.381m
0.20V	-1.928m	-1.274m	-2.709m
0.30V	-2.828m	-1.859m	-3.988m
0.40V	-3.685m	-2.412m	-5.216m
0.50V	-4.499m	-2.931m	-6.392m
0.60V	-5.269m	-3.416m	-7.516m
0.70V	-5.994m	-3.866m	-8.587m
0.80V	-6.673m	-4.280m	-9.602m
0.90V	-7.306m	-4.658m	-10.561m
1.00V	-7.890m	-4.999m	-11.461m
1.10V	-8.424m	-5.301m	-12.302m
1.20V	-8.907m	-5.563m	-13.081m
1.30V	-9.339m	-65.539m	-13.798m
1.40V	-110.103m	-67.611m	-154.438m
1.50V	-113.807m	-69.311m	-170.370m
1.60V	-117.010m	-70.713m	-176.323m
1.70V	-119.783m	-71.893m	-181.647m
1.80V	-122.195m	-72.910m	-186.387m
1.90V	-124.297m	-73.804m	-190.581m
2.00V	-126.131m	-74.599m	-194.261m
2.10V	-127.733m	-75.311m	-197.468m
2.20V	-129.139m	-75.954m	-200.255m
2.30V	-130.384m	-76.540m	-202.683m
2.40V	-131.498m	-77.077m	-204.814m
2.50V	-132.504m	-77.575m	-206.704m
2.60V	-133.423m	-78.037m	-208.399m
2.70V	-134.270m	-78.470m	-209.937m
2.80V	-135.057m	-78.877m	-211.346m
2.90V	-135.792m	-79.261m	-212.650m
3.00V	-136.483m	-79.625m	-213.864m
3.10V	-137.136m	-79.971m	-215.004m
3.20V	-137.756m	-80.302m	-216.079m
3.30V	-138.345m	-80.617m	-217.098m
3.40V	-138.908m	-80.920m	-218.067m
3.50V	-139.447m	-81.210m	-218.993m
3.60V	-139.964m	-81.490m	-219.880m
3.70V	-140.462m	-81.761m	-220.732m
3.80V	-140.943m	-82.022m	-221.552m
3.90V	-141.408m	-82.277m	-222.344m
4.00V	-141.860m	-82.525m	-223.112m
4.10V	-142.300m	-82.769m	-223.858m
4.20V	-142.733m	-83.010m	-224.586m
4.30V	-143.159m	-83.250m	-225.300m
4.40V	-143.585m	-83.493m	-226.006m
4.50V	-144.013m	-83.740m	-226.709m
4.60V	-144.449m	-83.996m	-227.417m
4.70V	-144.899m	-84.265m	-228.137m
4.80V	-145.370m	-84.551m	-228.879m
4.90V	-145.871m	-84.861m	-229.656m
5.00V	-146.411m	-85.200m	-230.481m
5.10V	-147.001m	-85.575m	-231.368m
5.20V	-147.652m	-85.993m	-232.336m
5.30V	-148.379m	-86.464m	-233.404m

# Freescale Semiconductor, Inc.

## IBIS Model

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5.40V	-149.195m	-86.995m	-234.592m
5.50V	-150.115m	-87.597m	-235.924m
5.60V	-151.157m	-88.280m	-237.426m
5.70V	-152.339m	-89.054m	-239.124m
5.80V	-153.678m	-89.930m	-241.046m
5.90V	-155.194m	-90.921m	-243.223m
6.00V	-156.907m	-92.038m	-245.685m
6.10V	-158.839m	-93.294m	-248.465m
6.20V	-161.011m	-94.701m	-251.595m
6.30V	-163.444m	-96.273m	-255.109m
6.40V	-166.160m	-98.023m	-259.041m
6.50V	-169.182m	-99.963m	-263.425m
6.60V	-172.531m	-102.106m	-268.293m
[GND_clamp]			
Voltage	I(typ)	I(min)	I(max)
-3.30V	-2.637	-1.514	-3.063
-3.20V	-2.521	-1.451	-2.926
-3.10V	-2.406	-1.387	-2.789
-2.90V	-2.174	-1.259	-2.515
-2.80V	-2.059	-1.195	-2.378
-2.70V	-1.943	-1.132	-2.242
-2.60V	-1.828	-1.068	-2.105
-2.50V	-1.713	-1.004	-1.969
-2.40V	-1.598	-941.073m	-1.833
-2.30V	-1.483	-877.750m	-1.697
-2.20V	-1.368	-814.544m	-1.561
-2.10V	-1.254	-751.475m	-1.425
-1.90V	-1.026	-625.847m	-1.155
-1.80V	-912.311m	-563.357m	-1.021
-1.70V	-799.377m	-501.149m	-886.904m
-1.60V	-687.103m	-439.297m	-753.859m
-1.50V	-575.715m	-377.904m	-621.897m
-1.40V	-465.583m	-317.129m	-491.519m
-1.30V	-357.354m	-257.221m	-363.667m
-1.20V	-252.314m	-198.614m	-240.395m
-1.10V	-153.494m	-142.138m	-127.373m
-0.90V	-19.457m	-45.305m	-11.215m
-0.80V	-3.535m	-16.226m	-4.650m
-0.70V	-877.640u	-3.288m	-1.613m
-0.60V	-156.838u	-397.909u	-271.662u
-0.50V	-14.514u	-53.601u	-18.044u
-0.40V	-780.351n	-6.086u	-560.308n
-0.30V	-37.668n	-598.098n	-15.437n
-0.20V	-1.699n	-55.739n	-411.332p
-0.10V	-92.071p	-5.410n	-29.683p
0.00V	-27.709p	-1.212n	-18.939p
0.10V	-22.802p	-890.771p	-16.163p
0.20V	-19.598p	-810.054p	-13.516p
0.30V	-16.468p	-745.765p	-10.874p
0.40V	-13.353p	-683.799p	-8.234p

# Freescale Semiconductor, Inc.

IBIS Model

0.50V	-10.247p	-622.802p	-5.595p
0.60V	-7.147p	-562.404p	-2.956p
0.70V	-4.050p	-502.414p	-318.962f
0.80V	-955.896f	-442.712p	2.318p
0.90V	2.136p	-383.217p	4.954p
1.10V	8.315p	-264.634p	10.227p
1.20V	11.404p	-205.467p	12.862p
1.30V	14.492p	-146.346p	15.498p
1.40V	17.579p	-87.245p	18.133p
1.50V	20.666p	-28.141p	20.768p
1.60V	23.754p	30.987p	23.404p
1.70V	26.841p	90.164p	26.039p
1.80V	29.929p	149.414p	28.674p
1.90V	33.018p	208.769p	31.310p
2.10V	39.198p	327.949p	36.581p
2.20V	42.291p	387.873p	39.216p
2.30V	45.385p	448.012p	41.852p
2.40V	48.483p	507.296p	44.489p
2.50V	51.583p	563.856p	47.125p
2.60V	54.673p	619.785p	49.762p
2.70V	57.468p	676.156p	52.401p
2.80V	59.647p	733.868p	55.040p
2.90V	61.717p	807.258p	57.675p
3.10V	65.859p	5.906n	61.928p
3.20V	68.003p	59.801n	63.585p
3.30V	72.601p	620.266n	65.236p
[POWER_clamp]			
Voltage	I(typ)	I(min)	I(max)
3.30V	-27.709p	-598.098n	-10.874p
3.40V	-92.071p	-6.086u	-13.516p
3.50V	-1.699n	-53.601u	-16.163p
3.60V	-37.668n	-397.909u	-18.939p
3.70V	-780.351n	-3.288m	-29.683p
3.80V	-14.514u	-16.226m	-411.332p
3.90V	-156.838u	-45.305m	-15.437n
4.10V	-3.535m	-142.138m	-18.044u
4.20V	-19.457m	-198.614m	-271.662u
4.30V	-69.631m	-257.221m	-1.613m
4.40V	-153.494m	-317.129m	-4.650m
4.50V	-252.314m	-377.904m	-11.215m
4.60V	-357.354m	-439.297m	-43.562m
4.70V	-465.583m	-501.149m	-127.373m
4.80V	-575.715m	-563.357m	-240.395m
4.90V	-687.103m	-625.847m	-363.667m
5.10V	-912.311m	-751.475m	-621.897m
5.20V	-1.026	-814.544m	-753.859m
5.30V	-1.140	-877.750m	-886.904m
5.40V	-1.254	-941.073m	-1.021
5.50V	-1.368	-1.004	-1.155
5.60V	-1.483	-1.068	-1.290

# Freescale Semiconductor, Inc.

## IBIS Model

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5.70V      -1.598    -1.132    -1.425
5.80V      -1.713    -1.195    -1.561
5.90V      -1.828    -1.259    -1.697
6.10V      -2.059    -1.387    -1.969
6.20V      -2.174    -1.451    -2.105
6.30V      -2.290    -1.514    -2.242
6.40V      -2.406    -1.578    -2.378
6.50V      -2.521    -1.642    -2.515
6.60V      -2.637    -1.706    -2.652
|
[Ramp]
|Voltage      I(typ)     I(min)     I(max)
|
dV/dt_f    1.99/110.010p 1.81/184.463p 2.17/69.974p
|
dV/dt_r    2.04/120.172p 1.85/212.126p 2.21/73.179p
R_load=10000ohms
|R_load was connected to ground for Ramp_up test and power for Ramp_dn
test
|
|End model
[Model]          ipadd_io           |   "
Model_type      I/O
Vinl = 0.8
Vinh = 2
| variable      typ        min        max
C_comp          2.34p     2.21p     2.52p
| variable      typ        min        max
[Temperature Range] 40.0     0.0      120.0
| variable      typ        min        max
[Voltage Range]   3.30V     3.00V     3.60V
|
[Pulldown]
| pulldown in the table = pulldown subtract gnd_clamp
|Voltage      I(typ)     I(min)     I(max)
|
-3.30V      -157.134u  -99.256u  -219.000u
-3.20V      -165.037u  -104.127u  -230.250u
-3.10V      -173.749u  -109.479u  -242.685u
-3.00V      -183.400u  -115.386u  -256.500u
-2.90V      -194.148u  -121.936u  -271.934u
-2.80V      -206.189u  -129.240u  -289.286u
-2.70V      -219.766u  -137.431u  -308.933u
-2.60V      -235.190u  -146.680u  -331.355u
-2.50V      -252.856u  -157.199u  -357.176u
-2.40V      -273.283u  -169.265u  -387.219u
-2.30V      -297.162u  -183.236u  -422.595u
-2.20V      -325.427u  -199.590u  -464.837u
-2.10V      -359.384u  -218.976u  -516.117u
-2.00V      -400.901u  -242.299u  -579.623u
-1.90V      -452.750u  -270.851u  -660.217u
-1.80V      -519.217u  -306.549u  -765.681u
-1.70V      -607.277u  -352.346u  -909.270u

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-1.60V	-729.045u	-413.024u	-1.115m
-1.50V	-907.407u	-496.811u	-1.434m
-1.40V	-1.191m	-619.011u	-1.987m
-1.30V	-1.699m	-811.079u	-3.133m
-1.20V	-2.799m	-1.146m	-6.243m
-1.10V	-5.689m	-1.822m	-12.974m
-1.00V	-10.416m	-3.302m	-17.948m
-0.90V	-12.342m	-5.449m	-17.964m
-0.80V	-11.672m	-6.479m	-16.692m
-0.70V	-10.528m	-6.146m	-15.152m
-0.60V	-9.204m	-5.387m	-13.338m
-0.50V	-7.770m	-4.535m	-11.313m
-0.40V	-6.286m	-3.652m	-9.190m
-0.30V	-4.766m	-2.754m	-6.999m
-0.20V	-3.214m	-1.846m	-4.740m
-0.10V	-1.627m	-928.990u	-2.410m
0.00V	32.871e-18	18.540e-18	-1.607f
0.10V	1.604m	910.814u	2.391m
0.20V	3.124m	1.775m	4.661m
0.30V	4.566m	2.595m	6.817m
0.40V	5.928m	3.372m	8.858m
0.50V	7.210m	4.105m	10.784m
0.60V	8.411m	4.792m	12.593m
0.70V	9.529m	5.432m	14.284m
0.80V	10.562m	6.023m	15.855m
0.90V	11.508m	6.563m	17.306m
1.00V	12.367m	7.051m	18.639m
1.10V	13.138m	7.486m	19.856m
1.20V	13.821m	7.865m	20.957m
1.30V	14.417m	8.189m	21.944m
1.40V	14.930m	64.562m	22.817m
1.50V	117.094m	66.208m	23.575m
1.60V	119.708m	67.513m	184.138m
1.70V	121.667m	68.498m	187.874m
1.80V	123.055m	69.206m	190.647m
1.90V	124.020m	69.710m	192.621m
2.00V	124.711m	70.083m	194.017m
2.10V	125.232m	70.374m	195.034m
2.20V	125.650m	70.612m	195.815m
2.30V	126.000m	70.814m	196.447m
2.40V	126.305m	70.992m	196.983m
2.50V	126.577m	71.151m	197.453m
2.60V	126.823m	71.296m	197.876m
2.70V	127.050m	71.428m	198.263m
2.80V	127.260m	71.551m	198.622m
2.90V	127.457m	71.666m	198.958m
3.00V	127.643m	71.774m	199.275m
3.10V	127.818m	71.876m	199.576m
3.20V	127.986m	71.973m	199.863m
3.30V	128.147m	72.066m	200.138m
3.40V	128.304m	72.156m	200.405m
3.50V	128.458m	72.245m	200.667m
3.60V	128.614m	72.335m	200.928m

# Freescale Semiconductor, Inc.

## IBIS Model

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3.70V	128.776m	72.428m	201.194m
3.80V	128.948m	72.527m	201.472m
3.90V	129.140m	72.638m	201.774m
4.00V	129.361m	72.764m	202.113m
4.10V	129.621m	72.914m	202.503m
4.20V	129.934m	73.093m	202.966m
4.30V	130.316m	73.311m	203.524m
4.40V	130.784m	73.579m	204.203m
4.50V	131.358m	73.906m	205.033m
4.60V	132.060m	74.304m	206.045m
4.70V	132.912m	74.787m	207.276m
4.80V	133.939m	75.368m	208.763m
4.90V	135.166m	76.060m	210.544m
5.00V	136.619m	76.878m	212.659m
5.10V	138.324m	77.836m	215.149m
5.20V	140.308m	78.948m	218.056m
5.30V	142.597m	80.230m	221.419m
5.40V	145.217m	81.694m	225.277m
5.50V	148.192m	83.355m	229.669m
5.60V	151.545m	85.224m	234.630m
5.70V	155.300m	87.316m	240.194m
5.80V	159.478m	89.640m	246.393m
5.90V	164.097m	92.208m	253.255m
6.00V	169.177m	95.029m	260.806m
6.10V	174.734m	98.112m	269.070m
6.20V	180.781m	101.465m	278.065m
6.30V	187.333m	105.096m	287.810m
6.40V	194.400m	109.009m	298.319m
6.50V	201.993m	113.211m	309.602m
6.60V	210.118m	117.705m	321.670m
<hr/>			
[Pullup]			
pullup in the table = pullup subtract power_clamp			
Voltage	I(typ)	I(min)	I(max)
-3.30V	132.979u	100.794u	170.075u
-3.20V	138.984u	105.115u	178.000u
-3.10V	145.559u	109.825u	186.702u
-3.00V	152.789u	114.981u	196.300u
-2.90V	160.778u	120.648u	206.941u
-2.80V	169.651u	126.906u	218.803u
-2.70V	179.562u	133.852u	232.110u
-2.60V	190.706u	141.605u	247.141u
-2.50V	203.326u	150.317u	264.253u
-2.40V	217.736u	160.174u	283.910u
-2.30V	234.344u	171.418u	306.723u
-2.20V	253.692u	184.362u	333.513u
-2.10V	276.513u	199.421u	365.415u
-2.00V	303.830u	217.155u	404.033u
-1.90V	337.102u	238.340u	451.722u
-1.80V	378.494u	264.081u	512.067u
-1.70V	431.351u	296.004u	590.810u
-1.60V	501.113u	336.601u	697.730u

# Freescale Semiconductor, Inc.

IBIS Model

-1.50V	597.240u	389.880u	850.877u
-1.40V	737.641u	462.700u	1.087m
-1.30V	960.395u	567.748u	1.497m
-1.20V	1.361m	731.012u	2.348m
-1.10V	2.237m	1.013m	4.712m
-1.00V	4.644m	1.583m	10.148m
-0.90V	8.090m	2.907m	12.062m
-0.80V	8.032m	4.727m	11.029m
-0.70V	7.118m	4.754m	9.778m
-0.60V	6.128m	4.128m	8.443m
-0.50V	5.109m	3.441m	7.052m
-0.40V	4.082m	2.746m	5.644m
-0.30V	3.056m	2.053m	4.233m
-0.20V	2.033m	1.363m	2.821m
-0.10V	1.014m	678.856u	1.410m
-0.00V	58.687e-18	58.622e-18	117.504e-18
0.10V	-987.106u	-655.604u	-1.381m
0.20V	-1.928m	-1.274m	-2.709m
0.30V	-2.828m	-1.859m	-3.988m
0.40V	-3.685m	-2.412m	-5.216m
0.50V	-4.499m	-2.931m	-6.392m
0.60V	-5.269m	-3.416m	-7.516m
0.70V	-5.994m	-3.866m	-8.587m
0.80V	-6.673m	-4.280m	-9.602m
0.90V	-7.306m	-4.658m	-10.561m
1.00V	-7.890m	-4.999m	-11.461m
1.10V	-8.424m	-5.301m	-12.302m
1.20V	-8.907m	-5.563m	-13.081m
1.30V	-9.339m	-65.539m	-13.798m
1.40V	-110.103m	-67.611m	-154.438m
1.50V	-113.807m	-69.311m	-170.370m
1.60V	-117.010m	-70.713m	-176.323m
1.70V	-119.783m	-71.893m	-181.647m
1.80V	-122.195m	-72.910m	-186.387m
1.90V	-124.297m	-73.804m	-190.581m
2.00V	-126.131m	-74.599m	-194.261m
2.10V	-127.733m	-75.311m	-197.468m
2.20V	-129.139m	-75.954m	-200.255m
2.30V	-130.384m	-76.540m	-202.683m
2.40V	-131.498m	-77.077m	-204.814m
2.50V	-132.504m	-77.575m	-206.704m
2.60V	-133.423m	-78.037m	-208.399m
2.70V	-134.270m	-78.470m	-209.937m
2.80V	-135.057m	-78.877m	-211.346m
2.90V	-135.792m	-79.261m	-212.650m
3.00V	-136.483m	-79.625m	-213.864m
3.10V	-137.136m	-79.971m	-215.004m
3.20V	-137.756m	-80.302m	-216.079m
3.30V	-138.345m	-80.617m	-217.098m
3.40V	-138.908m	-80.920m	-218.067m
3.50V	-139.447m	-81.210m	-218.993m
3.60V	-139.964m	-81.490m	-219.880m
3.70V	-140.462m	-81.761m	-220.732m

# Freescale Semiconductor, Inc.

## IBIS Model

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3.80V	-140.943m	-82.022m	-221.552m
3.90V	-141.408m	-82.277m	-222.344m
4.00V	-141.860m	-82.525m	-223.112m
4.10V	-142.300m	-82.769m	-223.858m
4.20V	-142.733m	-83.010m	-224.586m
4.30V	-143.159m	-83.250m	-225.300m
4.40V	-143.585m	-83.493m	-226.006m
4.50V	-144.013m	-83.740m	-226.709m
4.60V	-144.449m	-83.996m	-227.417m
4.70V	-144.899m	-84.265m	-228.137m
4.80V	-145.370m	-84.551m	-228.879m
4.90V	-145.871m	-84.861m	-229.656m
5.00V	-146.411m	-85.200m	-230.481m
5.10V	-147.001m	-85.575m	-231.368m
5.20V	-147.652m	-85.993m	-232.336m
5.30V	-148.379m	-86.464m	-233.404m
5.40V	-149.195m	-86.995m	-234.592m
5.50V	-150.115m	-87.597m	-235.924m
5.60V	-151.157m	-88.280m	-237.426m
5.70V	-152.339m	-89.054m	-239.124m
5.80V	-153.678m	-89.930m	-241.046m
5.90V	-155.194m	-90.921m	-243.223m
6.00V	-156.907m	-92.038m	-245.685m
6.10V	-158.839m	-93.294m	-248.465m
6.20V	-161.011m	-94.701m	-251.595m
6.30V	-163.444m	-96.273m	-255.109m
6.40V	-166.160m	-98.023m	-259.041m
6.50V	-169.182m	-99.963m	-263.425m
6.60V	-172.531m	-102.106m	-268.293m
<hr/>			
[GND_clamp]			
<hr/>			
Voltage	I(typ)	I(min)	I(max)
-3.30V	-2.637	-1.514	-3.063
-3.20V	-2.521	-1.451	-2.926
-3.10V	-2.406	-1.387	-2.789
-2.90V	-2.174	-1.259	-2.515
-2.80V	-2.059	-1.195	-2.378
-2.70V	-1.943	-1.132	-2.242
-2.60V	-1.828	-1.068	-2.105
-2.50V	-1.713	-1.004	-1.969
-2.40V	-1.598	-941.073m	-1.833
-2.30V	-1.483	-877.750m	-1.697
-2.20V	-1.368	-814.544m	-1.561
-2.10V	-1.254	-751.475m	-1.425
-1.90V	-1.026	-625.847m	-1.155
-1.80V	-912.311m	-563.357m	-1.021
-1.70V	-799.377m	-501.149m	-886.904m
-1.60V	-687.103m	-439.297m	-753.859m
-1.50V	-575.715m	-377.904m	-621.897m
-1.40V	-465.583m	-317.129m	-491.519m
-1.30V	-357.354m	-257.221m	-363.667m

# Freescale Semiconductor, Inc.

IBIS Model

Freescale Semiconductor, Inc.

-1.20V	-252.314m	-198.614m	-240.395m
-1.10V	-153.494m	-142.138m	-127.373m
-0.90V	-19.457m	-45.305m	-11.215m
-0.80V	-3.535m	-16.226m	-4.650m
-0.70V	-877.640u	-3.288m	-1.613m
-0.60V	-156.838u	-397.909u	-271.662u
-0.50V	-14.514u	-53.601u	-18.044u
-0.40V	-780.351n	-6.086u	-560.308n
-0.30V	-37.668n	-598.098n	-15.437n
-0.20V	-1.699n	-55.739n	-411.332p
-0.10V	-92.071p	-5.410n	-29.683p
0.00V	-27.709p	-1.212n	-18.939p
0.10V	-22.802p	-890.771p	-16.163p
0.20V	-19.598p	-810.054p	-13.516p
0.30V	-16.468p	-745.765p	-10.874p
0.40V	-13.353p	-683.799p	-8.234p
0.50V	-10.247p	-622.802p	-5.595p
0.60V	-7.147p	-562.404p	-2.956p
0.70V	-4.050p	-502.414p	-318.962f
0.80V	-955.896f	-442.712p	2.318p
0.90V	2.136p	-383.217p	4.954p
1.10V	8.315p	-264.634p	10.227p
1.20V	11.404p	-205.467p	12.862p
1.30V	14.492p	-146.346p	15.498p
1.40V	17.579p	-87.245p	18.133p
1.50V	20.666p	-28.141p	20.768p
1.60V	23.754p	30.987p	23.404p
1.70V	26.841p	90.164p	26.039p
1.80V	29.929p	149.414p	28.674p
1.90V	33.018p	208.769p	31.310p
2.10V	39.198p	327.949p	36.581p
2.20V	42.291p	387.873p	39.216p
2.30V	45.385p	448.012p	41.852p
2.40V	48.483p	507.296p	44.489p
2.50V	51.583p	563.856p	47.125p
2.60V	54.673p	619.785p	49.762p
2.70V	57.468p	676.156p	52.401p
2.80V	59.647p	733.868p	55.040p
2.90V	61.717p	807.258p	57.675p
3.10V	65.859p	5.906n	61.928p
3.20V	68.003p	59.801n	63.585p
3.30V	72.601p	620.266n	65.236p

| [POWER\_clamp]

Voltage	I(typ)	I(min)	I(max)
3.30V	-27.709p	-598.098n	-10.874p
3.40V	-92.071p	-6.086u	-13.516p
3.50V	-1.699n	-53.601u	-16.163p
3.60V	-37.668n	-397.909u	-18.939p
3.70V	-780.351n	-3.288m	-29.683p
3.80V	-14.514u	-16.226m	-411.332p

# Freescale Semiconductor, Inc.

## IBIS Model

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3.90V      -156.838u  -45.305m  -15.437n
4.10V      -3.535m   -142.138m  -18.044u
4.20V      -19.457m   -198.614m  -271.662u
4.30V      -69.631m   -257.221m  -1.613m
4.40V      -153.494m   -317.129m  -4.650m
4.50V      -252.314m   -377.904m  -11.215m
4.60V      -357.354m   -439.297m  -43.562m
4.70V      -465.583m   -501.149m  -127.373m
4.80V      -575.715m   -563.357m  -240.395m
4.90V      -687.103m   -625.847m  -363.667m
5.10V      -912.311m   -751.475m  -621.897m
5.20V      -1.026    -814.544m  -753.859m
5.30V      -1.140    -877.750m  -886.904m
5.40V      -1.254    -941.073m  -1.021
5.50V      -1.368     -1.004    -1.155
5.60V      -1.483     -1.068    -1.290
5.70V      -1.598     -1.132    -1.425
5.80V      -1.713     -1.195    -1.561
5.90V      -1.828     -1.259    -1.697
6.10V      -2.059     -1.387    -1.969
6.20V      -2.174     -1.451    -2.105
6.30V      -2.290     -1.514    -2.242
6.40V      -2.406     -1.578    -2.378
6.50V      -2.521     -1.642    -2.515
6.60V      -2.637     -1.706    -2.652
|
[Ramp]
|Voltage      I(typ)      I(min)      I(max)
|
dV/dt_f    1.99/104.603p 1.81/183.924p 2.18/69.643p
|
dV/dt_r    2.04/123.810p 1.85/215.062p 2.20/73.602p
R_load=10000ohms
|R_load was connected to ground for Ramp_up test and power for Ramp_dn
test
|
|End model
[Model]          ipadex_i           |   "
Model_type     Input
Vinl = 0.8
Vinh = 2
| variable      typ        min        max
C_comp          2.92p     2.78p     2.96p
| variable      typ        min        max
[Temperature Range] 40.0       0.0      120.0
| variable      typ        min        max
[Voltage Range]  3.30V     3.00V     3.60V
|
[GND_clamp]
|
|Voltage      I(typ)      I(min)      I(max)
|
-3.30V      -831.819m  -473.616m  -909.150m

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# Freescale Semiconductor, Inc.

IBIS Model

Freescale Semiconductor, Inc.

-3.20V	-796.528m	-454.528m	-869.534m
-3.10V	-761.255m	-435.451m	-829.938m
-2.90V	-690.773m	-397.335m	-750.811m
-2.80V	-655.569m	-378.299m	-711.286m
-2.70V	-620.391m	-359.279m	-671.789m
-2.60V	-585.244m	-340.277m	-632.324m
-2.50V	-550.131m	-321.295m	-592.895m
-2.40V	-515.057m	-302.336m	-553.507m
-2.30V	-480.027m	-283.402m	-514.167m
-2.20V	-445.047m	-264.496m	-474.880m
-2.10V	-410.126m	-245.624m	-435.657m
-1.90V	-340.501m	-207.998m	-357.451m
-1.80V	-305.826m	-189.259m	-318.503m
-1.70V	-271.273m	-170.582m	-279.692m
-1.60V	-236.871m	-151.981m	-241.057m
-1.50V	-202.665m	-133.474m	-202.657m
-1.40V	-168.722m	-115.088m	-164.583m
-1.30V	-135.151m	-96.861m	-126.991m
-1.20V	-102.140m	-78.852m	-90.181m
-1.10V	-70.064m	-61.160m	-54.834m
-0.90V	-14.097m	-27.650m	-2.799m
-0.80V	-1.307m	-13.160m	-53.501u
-0.70V	-36.639u	-3.159m	-768.589n
-0.60V	-903.944n	-256.975u	-10.997n
-0.50V	-22.242n	-13.934u	-172.415p
-0.40V	-567.014p	-730.372n	-16.888p
-0.30V	-32.976p	-38.990n	-13.767p
-0.20V	-18.575p	-2.810n	-12.822p
-0.10V	-16.945p	-867.431p	-11.909p
0.00V	-15.630p	-713.428p	-10.996p
0.10V	-14.322p	-652.886p	-10.084p
0.20V	-13.014p	-597.227p	-9.171p
0.30V	-11.707p	-541.823p	-8.258p
0.40V	-10.399p	-486.432p	-7.345p
0.50V	-9.092p	-431.043p	-6.432p
0.60V	-7.784p	-375.653p	-5.520p
0.70V	-6.477p	-320.263p	-4.607p
0.80V	-5.169p	-264.873p	-3.694p
0.90V	-3.862p	-209.483p	-2.781p
1.10V	-1.246p	-98.704p	-955.508f
1.20V	61.165f	-43.314p	-42.711f
1.30V	1.369p	12.076p	870.085f
1.40V	2.676p	67.466p	1.783p
1.50V	3.984p	122.856p	2.696p
1.60V	5.291p	178.246p	3.609p
1.70V	6.599p	233.635p	4.521p
1.80V	7.906p	289.025p	5.434p
1.90V	9.214p	344.415p	6.347p
2.10V	11.829p	455.195p	8.173p
2.20V	13.137p	510.585p	9.085p
2.30V	14.444p	565.974p	9.998p
2.40V	15.752p	621.364p	10.911p
2.50V	17.059p	676.754p	11.824p

# Freescale Semiconductor, Inc.

## IBIS Model

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2.60V      18.367p  732.144p  12.736p
2.70V      19.674p  787.535p  13.649p
2.80V      20.982p  842.946p  14.562p
2.90V      22.290p  898.735p  15.475p
3.10V      24.905p   1.163n   17.301p
3.20V      26.212p   4.019n   18.213p
3.30V      27.520p   57.671n  19.126p
|
|[POWER_clamp]
|
|Voltage    I(typ)     I(min)     I(max)
|
3.30V      -15.630p  -38.990n  -8.258p
3.40V      -16.945p  -730.372n  -9.171p
3.50V      -18.575p  -13.934u  -10.084p
3.60V      -32.976p  -256.975u  -10.996p
3.70V      -567.014p  -3.159m  -11.909p
3.80V      -22.242n  -13.160m  -12.822p
3.90V      -903.944n  -27.650m  -13.767p
4.10V      -1.307m   -61.160m  -172.415p
4.20V      -14.097m  -78.852m  -10.997n
4.30V      -39.803m  -96.861m  -768.589n
4.40V      -70.064m  -115.088m  -53.501u
4.50V      -102.140m  -133.474m  -2.799m
4.60V      -135.151m  -151.981m  -22.990m
4.70V      -168.722m  -170.582m  -54.834m
4.80V      -202.665m  -189.259m  -90.181m
4.90V      -236.871m  -207.998m  -126.991m
5.10V      -305.826m  -245.624m  -202.657m
5.20V      -340.501m  -264.496m  -241.057m
5.30V      -375.273m  -283.402m  -279.692m
5.40V      -410.126m  -302.336m  -318.503m
5.50V      -445.047m  -321.295m  -357.451m
5.60V      -480.027m  -340.277m  -396.509m
5.70V      -515.057m  -359.279m  -435.657m
5.80V      -550.131m  -378.299m  -474.880m
5.90V      -585.244m  -397.335m  -514.167m
6.10V      -655.569m  -435.451m  -592.895m
6.20V      -690.773m  -454.528m  -632.324m
6.30V      -726.003m  -473.616m  -671.789m
6.40V      -761.255m  -492.715m  -711.286m
6.50V      -796.528m  -511.823m  -750.811m
6.60V      -831.819m  -530.941m  -790.363m
|
|End model
[Model]          ipadm_3st           |   "
Model_type       3-state
|
| variable       typ        min        max
C_comp          1.99p     1.86p     2.15p
| variable       typ        min        max
[Temperature Range] 40.0      0.0      120.0
| variable       typ        min        max
[Voltage Range]  3.30V     3.00V     3.60V

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**Freescale Semiconductor, Inc.****IBIS Model**


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[Pulldown]			
pulldown in the table = pulldown subtract gnd_clamp			
Voltage	I(typ)	I(min)	I(max)
-3.30V	-157.134u	-99.256u	-219.000u
-3.20V	-165.037u	-104.127u	-230.250u
-3.10V	-173.749u	-109.479u	-242.685u
-3.00V	-183.400u	-115.386u	-256.500u
-2.90V	-194.148u	-121.936u	-271.934u
-2.80V	-206.189u	-129.240u	-289.286u
-2.70V	-219.766u	-137.431u	-308.933u
-2.60V	-235.190u	-146.680u	-331.355u
-2.50V	-252.856u	-157.199u	-357.176u
-2.40V	-273.283u	-169.265u	-387.219u
-2.30V	-297.162u	-183.236u	-422.595u
-2.20V	-325.427u	-199.590u	-464.837u
-2.10V	-359.384u	-218.976u	-516.117u
-2.00V	-400.901u	-242.299u	-579.623u
-1.90V	-452.750u	-270.851u	-660.217u
-1.80V	-519.217u	-306.549u	-765.681u
-1.70V	-607.277u	-352.346u	-909.270u
-1.60V	-729.045u	-413.024u	-1.115m
-1.50V	-907.407u	-496.811u	-1.434m
-1.40V	-1.191m	-619.011u	-1.987m
-1.30V	-1.699m	-811.079u	-3.133m
-1.20V	-2.799m	-1.146m	-6.243m
-1.10V	-5.689m	-1.822m	-12.974m
-1.00V	-10.416m	-3.302m	-17.948m
-0.90V	-12.342m	-5.449m	-17.964m
-0.80V	-11.672m	-6.479m	-16.692m
-0.70V	-10.528m	-6.146m	-15.152m
-0.60V	-9.204m	-5.387m	-13.338m
-0.50V	-7.770m	-4.535m	-11.313m
-0.40V	-6.286m	-3.652m	-9.190m
-0.30V	-4.766m	-2.754m	-6.999m
-0.20V	-3.214m	-1.846m	-4.740m
-0.10V	-1.627m	-928.990u	-2.410m
0.00V	32.755e-18	18.548e-18	-1.607f
0.10V	1.604m	910.814u	2.391m
0.20V	3.124m	1.775m	4.661m
0.30V	4.566m	2.595m	6.817m
0.40V	5.928m	3.372m	8.858m
0.50V	7.210m	4.105m	10.784m
0.60V	8.411m	4.792m	12.593m
0.70V	9.529m	5.432m	14.284m
0.80V	10.562m	6.023m	15.855m
0.90V	11.508m	6.563m	17.306m
1.00V	12.367m	7.051m	18.639m
1.10V	13.138m	7.486m	19.856m
1.20V	13.821m	7.865m	20.957m
1.30V	14.417m	8.189m	21.944m
1.40V	14.930m	47.725m	22.817m

**Freescale Semiconductor, Inc.****IBIS Model**

1.50V	86.564m	48.943m	23.575m
1.60V	88.497m	49.908m	136.139m
1.70V	89.946m	50.637m	138.902m
1.80V	90.974m	51.160m	140.954m
1.90V	91.689m	51.534m	142.415m
2.00V	92.200m	51.810m	143.449m
2.10V	92.586m	52.024m	144.201m
2.20V	92.895m	52.201m	144.779m
2.30V	93.154m	52.351m	145.246m
2.40V	93.380m	52.482m	145.642m
2.50V	93.581m	52.600m	145.990m
2.60V	93.764m	52.706m	146.303m
2.70V	93.931m	52.804m	146.590m
2.80V	94.087m	52.895m	146.855m
2.90V	94.233m	52.980m	147.104m
3.00V	94.370m	53.060m	147.338m
3.10V	94.500m	53.135m	147.560m
3.20V	94.624m	53.207m	147.772m
3.30V	94.744m	53.276m	147.976m
3.40V	94.859m	53.343m	148.174m
3.50V	94.974m	53.408m	148.367m
3.60V	95.089m	53.475m	148.560m
3.70V	95.208m	53.543m	148.757m
3.80V	95.336m	53.617m	148.963m
3.90V	95.478m	53.699m	149.186m
4.00V	95.641m	53.792m	149.436m
4.10V	95.833m	53.902m	149.725m
4.20V	96.065m	54.035m	150.067m
4.30V	96.347m	54.196m	150.479m
4.40V	96.693m	54.394m	150.981m
4.50V	97.117m	54.635m	151.594m
4.60V	97.636m	54.930m	152.342m
4.70V	98.266m	55.287m	153.252m
4.80V	99.024m	55.716m	154.350m
4.90V	99.931m	56.227m	155.666m
5.00V	101.005m	56.831m	157.230m
5.10V	102.264m	57.539m	159.070m
5.20V	103.730m	58.361m	161.218m
5.30V	105.422m	59.308m	163.704m
5.40V	107.357m	60.391m	166.555m
5.50V	109.556m	61.618m	169.801m
5.60V	112.034m	63.000m	173.468m
5.70V	114.809m	64.545m	177.581m
5.80V	117.897m	66.263m	182.163m
5.90V	121.311m	68.160m	187.235m
6.00V	125.066m	70.245m	192.816m
6.10V	129.172m	72.524m	198.924m
6.20V	133.642m	75.002m	205.573m
6.30V	138.485m	77.685m	212.776m
6.40V	143.709m	80.578m	220.544m
6.50V	149.320m	83.683m	228.885m
6.60V	155.326m	87.004m	237.805m

**Freescale Semiconductor, Inc.****IBIS Model**

[Pullup]			
Voltage	I(typ)	I(min)	I(max)
-3.30V	132.979u	100.794u	170.075u
-3.20V	138.984u	105.115u	178.000u
-3.10V	145.559u	109.825u	186.702u
-3.00V	152.789u	114.981u	196.300u
-2.90V	160.778u	120.648u	206.941u
-2.80V	169.651u	126.906u	218.803u
-2.70V	179.562u	133.852u	232.110u
-2.60V	190.706u	141.605u	247.141u
-2.50V	203.326u	150.317u	264.253u
-2.40V	217.736u	160.174u	283.910u
-2.30V	234.344u	171.418u	306.723u
-2.20V	253.692u	184.362u	333.513u
-2.10V	276.513u	199.421u	365.415u
-2.00V	303.830u	217.155u	404.033u
-1.90V	337.102u	238.340u	451.722u
-1.80V	378.494u	264.081u	512.067u
-1.70V	431.351u	296.004u	590.810u
-1.60V	501.113u	336.601u	697.730u
-1.50V	597.240u	389.880u	850.877u
-1.40V	737.641u	462.700u	1.087m
-1.30V	960.396u	567.748u	1.497m
-1.20V	1.361m	731.012u	2.348m
-1.10V	2.237m	1.013m	4.712m
-1.00V	4.644m	1.583m	10.148m
-0.90V	8.090m	2.907m	12.062m
-0.80V	8.032m	4.727m	11.029m
-0.70V	7.118m	4.754m	9.778m
-0.60V	6.128m	4.128m	8.443m
-0.50V	5.109m	3.441m	7.052m
-0.40V	4.082m	2.746m	5.644m
-0.30V	3.056m	2.053m	4.233m
-0.20V	2.033m	1.363m	2.821m
-0.10V	1.014m	678.856u	1.410m
-0.00V	58.687e-18	58.622e-18	117.504e-18
0.10V	-987.106u	-655.604u	-1.381m
0.20V	-1.928m	-1.274m	-2.709m
0.30V	-2.828m	-1.859m	-3.988m
0.40V	-3.685m	-2.412m	-5.216m
0.50V	-4.499m	-2.931m	-6.392m
0.60V	-5.269m	-3.416m	-7.516m
0.70V	-5.994m	-3.866m	-8.587m
0.80V	-6.673m	-4.280m	-9.602m
0.90V	-7.306m	-4.658m	-10.561m
1.00V	-7.890m	-4.999m	-11.461m
1.10V	-8.424m	-5.301m	-12.302m
1.20V	-8.907m	-5.563m	-13.081m
1.30V	-9.339m	-47.451m	-13.837m
1.40V	-79.705m	-48.954m	-118.519m
1.50V	-82.391m	-50.187m	-123.324m

**Freescale Semiconductor, Inc.****IBIS Model**

1.60V	-84.713m	-51.203m	-127.640m
1.70V	-86.724m	-52.057m	-131.501m
1.80V	-88.472m	-52.794m	-134.939m
1.90V	-89.996m	-53.442m	-137.982m
2.00V	-91.327m	-54.017m	-140.655m
2.10V	-92.489m	-54.533m	-142.987m
2.20V	-93.511m	-54.999m	-145.014m
2.30V	-94.415m	-55.424m	-146.781m
2.40V	-95.224m	-55.814m	-148.333m
2.50V	-95.955m	-56.174m	-149.709m
2.60V	-96.623m	-56.510m	-150.943m
2.70V	-97.238m	-56.824m	-152.063m
2.80V	-97.809m	-57.119m	-153.088m
2.90V	-98.343m	-57.398m	-154.036m
3.00V	-98.846m	-57.662m	-154.920m
3.10V	-99.320m	-57.913m	-155.749m
3.20V	-99.770m	-58.152m	-156.531m
3.30V	-100.198m	-58.381m	-157.272m
3.40V	-100.607m	-58.601m	-157.977m
3.50V	-100.998m	-58.812m	-158.650m
3.60V	-101.374m	-59.015m	-159.295m
3.70V	-101.735m	-59.211m	-159.914m
3.80V	-102.084m	-59.401m	-160.510m
3.90V	-102.422m	-59.585m	-161.086m
4.00V	-102.750m	-59.766m	-161.644m
4.10V	-103.070m	-59.942m	-162.186m
4.20V	-103.384m	-60.117m	-162.715m
4.30V	-103.694m	-60.291m	-163.234m
4.40V	-104.002m	-60.467m	-163.747m
4.50V	-104.313m	-60.647m	-164.257m
4.60V	-104.629m	-60.832m	-164.770m
4.70V	-104.955m	-61.027m	-165.293m
4.80V	-105.296m	-61.234m	-165.831m
4.90V	-105.659m	-61.459m	-166.394m
5.00V	-106.050m	-61.704m	-166.991m
5.10V	-106.477m	-61.975m	-167.634m
5.20V	-106.949m	-62.278m	-168.334m
5.30V	-107.474m	-62.619m	-169.106m
5.40V	-108.064m	-63.003m	-169.965m
5.50V	-108.730m	-63.439m	-170.928m
5.60V	-109.483m	-63.932m	-172.012m
5.70V	-110.337m	-64.492m	-173.239m
5.80V	-111.305m	-65.126m	-174.627m
5.90V	-112.401m	-65.843m	-176.199m
6.00V	-113.640m	-66.651m	-177.978m
6.10V	-115.036m	-67.560m	-179.986m
6.20V	-116.606m	-68.578m	-182.247m
6.30V	-118.365m	-69.715m	-184.785m
6.40V	-120.329m	-70.981m	-187.626m
6.50V	-122.513m	-72.384m	-190.793m
6.60V	-124.935m	-73.935m	-194.311m

|  
[GND\_clamp]

# Freescale Semiconductor, Inc.

IBIS Model

Voltage	I(typ)	I(min)	I(max)
-3.30V	-2.165	-1.242	-2.500
-3.20V	-2.070	-1.190	-2.388
-3.10V	-1.975	-1.138	-2.277
-2.90V	-1.786	-1.033	-2.054
-2.80V	-1.691	-981.185m	-1.942
-2.70V	-1.597	-929.174m	-1.831
-2.60V	-1.503	-877.220m	-1.720
-2.50V	-1.408	-825.330m	-1.609
-2.40V	-1.314	-773.514m	-1.498
-2.30V	-1.220	-721.779m	-1.387
-2.20V	-1.126	-670.140m	-1.276
-2.10V	-1.032	-618.610m	-1.166
-1.90V	-845.771m	-515.958m	-945.908m
-1.80V	-752.887m	-464.892m	-836.403m
-1.70V	-660.410m	-414.052m	-727.373m
-1.60V	-568.461m	-363.494m	-618.970m
-1.50V	-477.221m	-313.301m	-511.430m
-1.40V	-386.980m	-263.597m	-405.149m
-1.30V	-298.248m	-214.579m	-300.867m
-1.20V	-212.028m	-166.582m	-200.187m
-1.10V	-130.668m	-120.248m	-107.496m
-0.90V	-17.375m	-40.029m	-8.803m
-0.80V	-2.837m	-14.886m	-3.451m
-0.70V	-656.331u	-3.014m	-1.195m
-0.60V	-116.521u	-336.317u	-201.636u
-0.50V	-10.789u	-41.964u	-13.420u
-0.40V	-580.051n	-4.632u	-416.799n
-0.30V	-27.994n	-450.005n	-11.484n
-0.20V	-1.269n	-41.862n	-311.158p
-0.10V	-74.463p	-4.218n	-27.092p
0.00V	-26.215p	-1.078n	-18.737p
0.10V	-22.114p	-826.325p	-16.303p
0.20V	-19.278p	-754.146p	-13.966p
0.30V	-16.497p	-694.188p	-11.632p
0.40V	-13.726p	-635.953p	-9.300p
0.50V	-10.963p	-578.437p	-6.968p
0.60V	-8.203p	-521.365p	-4.637p
0.70V	-5.446p	-464.595p	-2.307p
0.80V	-2.691p	-408.039p	22.980f
0.90V	62.079f	-351.636p	2.353p
1.10V	5.566p	-239.133p	7.011p
1.20V	8.316p	-182.975p	9.340p
1.30V	11.067p	-126.851p	11.669p
1.40V	13.817p	-70.743p	13.998p
1.50V	16.567p	-14.634p	16.327p
1.60V	19.317p	41.493p	18.656p
1.70V	22.067p	97.654p	20.985p
1.80V	24.817p	153.868p	23.313p
1.90V	27.568p	210.159p	25.642p
2.10V	33.072p	323.083p	30.300p

# Freescale Semiconductor, Inc.

## IBIS Model

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2.20V	35.825p	379.789p	32.629p
2.30V	38.581p	436.650p	34.958p
2.40V	41.339p	492.867p	37.288p
2.50V	44.098p	547.026p	39.618p
2.60V	46.849p	600.695p	41.948p
2.70V	49.356p	654.682p	44.279p
2.80V	51.378p	709.650p	46.611p
2.90V	53.315p	776.122p	48.939p
3.10V	57.193p	4.552n	52.772p
3.20V	59.183p	44.522n	54.319p
3.30V	62.959p	466.732n	55.861p
   [POWER_clamp]   			
Voltage	I(typ)	I(min)	I(max)
3.30V	-26.215p	-450.005n	-11.632p
3.40V	-74.463p	-4.632u	-13.966p
3.50V	-1.269n	-41.964u	-16.303p
3.60V	-27.994n	-336.317u	-18.737p
3.70V	-580.051n	-3.014m	-27.092p
3.80V	-10.789u	-14.886m	-311.158p
3.90V	-116.521u	-40.029m	-11.484n
4.10V	-2.837m	-120.248m	-13.420u
4.20V	-17.375m	-166.582m	-201.636u
4.30V	-60.888m	-214.579m	-1.195m
4.40V	-130.668m	-263.597m	-3.451m
4.50V	-212.028m	-313.301m	-8.803m
4.60V	-298.248m	-363.494m	-37.420m
4.70V	-386.980m	-414.052m	-107.496m
4.80V	-477.221m	-464.892m	-200.187m
4.90V	-568.461m	-515.958m	-300.867m
5.10V	-752.887m	-618.610m	-511.430m
5.20V	-845.771m	-670.140m	-618.970m
5.30V	-938.979m	-721.779m	-727.373m
5.40V	-1.032	-773.514m	-836.403m
5.50V	-1.126	-825.330m	-945.908m
5.60V	-1.220	-877.220m	-1.056
5.70V	-1.314	-929.174m	-1.166
5.80V	-1.408	-981.185m	-1.276
5.90V	-1.503	-1.033	-1.387
6.10V	-1.691	-1.138	-1.609
6.20V	-1.786	-1.190	-1.720
6.30V	-1.881	-1.242	-1.831
6.40V	-1.975	-1.294	-1.942
6.50V	-2.070	-1.346	-2.054
6.60V	-2.165	-1.399	-2.165
   [Ramp]   			
Voltage	I(typ)	I(min)	I(max)
dV/dt_f	1.99/116.478p	1.81/206.384p	2.17/80.687p

**Freescale Semiconductor, Inc.****IBIS Model**

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dV/dt_r      2.02/147.722p 1.84/253.853p 2.19/93.030p
R_load=10000ohms
| R_load was connected to ground for Ramp_up test and power for Ramp_dn
test
|
|End model
[Model]          ipadn_io           |   "
Model_type       I/O
Vinl = 0.8
Vinh = 2
| variable      typ        min        max
C_comp          2.03p     1.90p     2.18p
| variable      typ        min        max
[Temperature Range] 40.0      0.0      120.0
| variable      typ        min        max
[Voltage Range]   3.30V     3.00V     3.60V
|
[Pulldown]
| pulldown in the table = pulldown subtract gnd_clamp
|Voltage    I(typ)    I(min)    I(max)
|
-3.30V    -157.134u   -99.256u   -219.000u
-3.20V    -165.037u   -104.127u   -230.250u
-3.10V    -173.749u   -109.479u   -242.685u
-3.00V    -183.400u   -115.386u   -256.500u
-2.90V    -194.148u   -121.936u   -271.934u
-2.80V    -206.189u   -129.240u   -289.286u
-2.70V    -219.766u   -137.431u   -308.933u
-2.60V    -235.190u   -146.680u   -331.355u
-2.50V    -252.856u   -157.199u   -357.176u
-2.40V    -273.283u   -169.265u   -387.219u
-2.30V    -297.162u   -183.236u   -422.595u
-2.20V    -325.427u   -199.590u   -464.837u
-2.10V    -359.384u   -218.976u   -516.117u
-2.00V    -400.901u   -242.299u   -579.623u
-1.90V    -452.750u   -270.851u   -660.217u
-1.80V    -519.217u   -306.549u   -765.681u
-1.70V    -607.277u   -352.346u   -909.270u
-1.60V    -729.045u   -413.024u   -1.115m
-1.50V    -907.407u   -496.811u   -1.434m
-1.40V    -1.191m    -619.011u   -1.987m
-1.30V    -1.699m    -811.079u   -3.133m
-1.20V    -2.799m    -1.146m    -6.243m
-1.10V    -5.689m    -1.822m    -12.974m
-1.00V    -10.416m   -3.302m    -17.948m
-0.90V    -12.342m   -5.449m    -17.964m
-0.80V    -11.672m   -6.479m    -16.692m
-0.70V    -10.528m   -6.146m    -15.152m
-0.60V    -9.204m    -5.387m    -13.338m
-0.50V    -7.770m    -4.535m    -11.313m
-0.40V    -6.286m    -3.652m    -9.190m
-0.30V    -4.766m    -2.754m    -6.999m
-0.20V    -3.214m    -1.846m    -4.740m

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**Freescale Semiconductor, Inc.****IBIS Model**

-0.10V	-1.627m	-928.990u	-2.410m
0.00V	32.755e-18	18.548e-18	-1.607f
0.10V	1.604m	910.814u	2.391m
0.20V	3.124m	1.775m	4.661m
0.30V	4.566m	2.595m	6.817m
0.40V	5.928m	3.372m	8.858m
0.50V	7.210m	4.105m	10.784m
0.60V	8.411m	4.792m	12.593m
0.70V	9.529m	5.432m	14.284m
0.80V	10.562m	6.023m	15.855m
0.90V	11.508m	6.563m	17.306m
1.00V	12.367m	7.051m	18.639m
1.10V	13.138m	7.486m	19.856m
1.20V	13.821m	7.865m	20.957m
1.30V	14.417m	8.189m	21.944m
1.40V	14.930m	47.725m	22.817m
1.50V	86.564m	48.943m	23.575m
1.60V	88.497m	49.908m	136.139m
1.70V	89.946m	50.637m	138.902m
1.80V	90.974m	51.160m	140.954m
1.90V	91.689m	51.534m	142.415m
2.00V	92.200m	51.810m	143.449m
2.10V	92.586m	52.024m	144.201m
2.20V	92.895m	52.201m	144.779m
2.30V	93.154m	52.351m	145.246m
2.40V	93.380m	52.482m	145.642m
2.50V	93.581m	52.600m	145.990m
2.60V	93.764m	52.706m	146.303m
2.70V	93.931m	52.804m	146.590m
2.80V	94.087m	52.895m	146.855m
2.90V	94.233m	52.980m	147.104m
3.00V	94.370m	53.060m	147.338m
3.10V	94.500m	53.135m	147.560m
3.20V	94.624m	53.207m	147.772m
3.30V	94.744m	53.276m	147.976m
3.40V	94.859m	53.343m	148.174m
3.50V	94.974m	53.408m	148.367m
3.60V	95.089m	53.475m	148.560m
3.70V	95.208m	53.543m	148.757m
3.80V	95.336m	53.617m	148.963m
3.90V	95.478m	53.699m	149.186m
4.00V	95.641m	53.792m	149.436m
4.10V	95.833m	53.902m	149.725m
4.20V	96.065m	54.035m	150.067m
4.30V	96.347m	54.196m	150.479m
4.40V	96.693m	54.394m	150.981m
4.50V	97.117m	54.635m	151.594m
4.60V	97.636m	54.930m	152.342m
4.70V	98.266m	55.287m	153.252m
4.80V	99.024m	55.716m	154.350m
4.90V	99.931m	56.227m	155.666m
5.00V	101.005m	56.831m	157.230m
5.10V	102.264m	57.539m	159.070m

**Freescale Semiconductor, Inc.****IBIS Model**

5.20V	103.730m	58.361m	161.218m
5.30V	105.422m	59.308m	163.704m
5.40V	107.357m	60.391m	166.555m
5.50V	109.556m	61.618m	169.801m
5.60V	112.034m	63.000m	173.468m
5.70V	114.809m	64.545m	177.581m
5.80V	117.897m	66.263m	182.163m
5.90V	121.311m	68.160m	187.235m
6.00V	125.066m	70.245m	192.816m
6.10V	129.172m	72.524m	198.924m
6.20V	133.642m	75.002m	205.573m
6.30V	138.485m	77.685m	212.776m
6.40V	143.709m	80.578m	220.544m
6.50V	149.320m	83.683m	228.885m
6.60V	155.326m	87.004m	237.805m
[Pullup]			
pullup in the table = pullup subtract power_clamp			
Voltage	I(typ)	I(min)	I(max)
-3.30V	132.979u	100.794u	170.075u
-3.20V	138.984u	105.115u	178.000u
-3.10V	145.559u	109.825u	186.702u
-3.00V	152.789u	114.981u	196.300u
-2.90V	160.778u	120.648u	206.941u
-2.80V	169.651u	126.906u	218.803u
-2.70V	179.562u	133.852u	232.110u
-2.60V	190.706u	141.605u	247.141u
-2.50V	203.326u	150.317u	264.253u
-2.40V	217.736u	160.174u	283.910u
-2.30V	234.344u	171.418u	306.723u
-2.20V	253.692u	184.362u	333.513u
-2.10V	276.513u	199.421u	365.415u
-2.00V	303.830u	217.155u	404.033u
-1.90V	337.102u	238.340u	451.722u
-1.80V	378.494u	264.081u	512.067u
-1.70V	431.351u	296.004u	590.810u
-1.60V	501.113u	336.601u	697.730u
-1.50V	597.240u	389.880u	850.877u
-1.40V	737.641u	462.700u	1.087m
-1.30V	960.396u	567.748u	1.497m
-1.20V	1.361m	731.012u	2.348m
-1.10V	2.237m	1.013m	4.712m
-1.00V	4.644m	1.583m	10.148m
-0.90V	8.090m	2.907m	12.062m
-0.80V	8.032m	4.727m	11.029m
-0.70V	7.118m	4.754m	9.778m
-0.60V	6.128m	4.128m	8.443m
-0.50V	5.109m	3.441m	7.052m
-0.40V	4.082m	2.746m	5.644m
-0.30V	3.056m	2.053m	4.233m
-0.20V	2.033m	1.363m	2.821m
-0.10V	1.014m	678.856u	1.410m

# Freescale Semiconductor, Inc.

## IBIS Model

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-0.00V	58.687e-18	58.622e-18	117.504e-18
0.10V	-987.106u	-655.604u	-1.381m
0.20V	-1.928m	-1.274m	-2.709m
0.30V	-2.828m	-1.859m	-3.988m
0.40V	-3.685m	-2.412m	-5.216m
0.50V	-4.499m	-2.931m	-6.392m
0.60V	-5.269m	-3.416m	-7.516m
0.70V	-5.994m	-3.866m	-8.587m
0.80V	-6.673m	-4.280m	-9.602m
0.90V	-7.306m	-4.658m	-10.561m
1.00V	-7.890m	-4.999m	-11.461m
1.10V	-8.424m	-5.301m	-12.302m
1.20V	-8.907m	-5.563m	-13.081m
1.30V	-9.339m	-47.451m	-13.901m
1.40V	-79.705m	-48.954m	-118.519m
1.50V	-82.391m	-50.187m	-123.324m
1.60V	-84.713m	-51.203m	-127.640m
1.70V	-86.724m	-52.057m	-131.501m
1.80V	-88.472m	-52.794m	-134.939m
1.90V	-89.996m	-53.442m	-137.982m
2.00V	-91.327m	-54.017m	-140.655m
2.10V	-92.489m	-54.533m	-142.987m
2.20V	-93.511m	-54.999m	-145.014m
2.30V	-94.415m	-55.424m	-146.781m
2.40V	-95.224m	-55.814m	-148.333m
2.50V	-95.955m	-56.174m	-149.709m
2.60V	-96.623m	-56.510m	-150.943m
2.70V	-97.238m	-56.824m	-152.063m
2.80V	-97.809m	-57.119m	-153.088m
2.90V	-98.343m	-57.398m	-154.036m
3.00V	-98.846m	-57.662m	-154.920m
3.10V	-99.320m	-57.913m	-155.749m
3.20V	-99.770m	-58.152m	-156.531m
3.30V	-100.198m	-58.381m	-157.272m
3.40V	-100.607m	-58.601m	-157.977m
3.50V	-100.998m	-58.812m	-158.650m
3.60V	-101.374m	-59.015m	-159.295m
3.70V	-101.735m	-59.211m	-159.914m
3.80V	-102.084m	-59.401m	-160.510m
3.90V	-102.422m	-59.585m	-161.086m
4.00V	-102.750m	-59.766m	-161.644m
4.10V	-103.070m	-59.942m	-162.186m
4.20V	-103.384m	-60.117m	-162.715m
4.30V	-103.694m	-60.291m	-163.234m
4.40V	-104.002m	-60.467m	-163.747m
4.50V	-104.313m	-60.647m	-164.257m
4.60V	-104.629m	-60.832m	-164.770m
4.70V	-104.955m	-61.027m	-165.293m
4.80V	-105.296m	-61.234m	-165.831m
4.90V	-105.659m	-61.459m	-166.394m
5.00V	-106.050m	-61.704m	-166.991m
5.10V	-106.477m	-61.975m	-167.634m
5.20V	-106.949m	-62.278m	-168.334m

# Freescale Semiconductor, Inc.

IBIS Model

5.30V	-107.474m	-62.619m	-169.106m
5.40V	-108.064m	-63.003m	-169.965m
5.50V	-108.730m	-63.439m	-170.928m
5.60V	-109.483m	-63.932m	-172.012m
5.70V	-110.337m	-64.492m	-173.239m
5.80V	-111.305m	-65.126m	-174.627m
5.90V	-112.401m	-65.843m	-176.199m
6.00V	-113.640m	-66.651m	-177.978m
6.10V	-115.036m	-67.560m	-179.986m
6.20V	-116.606m	-68.578m	-182.247m
6.30V	-118.365m	-69.715m	-184.785m
6.40V	-120.329m	-70.981m	-187.626m
6.50V	-122.513m	-72.384m	-190.793m
6.60V	-124.935m	-73.935m	-194.311m
[GND_clamp]			
Voltage	I(typ)	I(min)	I(max)
-3.30V	-2.165	-1.242	-2.500
-3.20V	-2.070	-1.190	-2.388
-3.10V	-1.975	-1.138	-2.277
-2.90V	-1.786	-1.033	-2.054
-2.80V	-1.691	-981.185m	-1.942
-2.70V	-1.597	-929.174m	-1.831
-2.60V	-1.503	-877.220m	-1.720
-2.50V	-1.408	-825.330m	-1.609
-2.40V	-1.314	-773.514m	-1.498
-2.30V	-1.220	-721.779m	-1.387
-2.20V	-1.126	-670.140m	-1.276
-2.10V	-1.032	-618.610m	-1.166
-1.90V	-845.771m	-515.958m	-945.908m
-1.80V	-752.887m	-464.892m	-836.403m
-1.70V	-660.410m	-414.052m	-727.373m
-1.60V	-568.461m	-363.494m	-618.970m
-1.50V	-477.221m	-313.301m	-511.430m
-1.40V	-386.980m	-263.597m	-405.149m
-1.30V	-298.248m	-214.579m	-300.867m
-1.20V	-212.028m	-166.582m	-200.187m
-1.10V	-130.668m	-120.248m	-107.496m
-0.90V	-17.375m	-40.029m	-8.803m
-0.80V	-2.837m	-14.886m	-3.451m
-0.70V	-656.331u	-3.014m	-1.195m
-0.60V	-116.521u	-336.317u	-201.636u
-0.50V	-10.789u	-41.964u	-13.420u
-0.40V	-580.051n	-4.632u	-416.799n
-0.30V	-27.994n	-450.005n	-11.484n
-0.20V	-1.269n	-41.862n	-311.158p
-0.10V	-74.463p	-4.218n	-27.092p
0.00V	-26.215p	-1.078n	-18.737p
0.10V	-22.114p	-826.325p	-16.303p
0.20V	-19.278p	-754.146p	-13.966p
0.30V	-16.497p	-694.188p	-11.632p

# Freescale Semiconductor, Inc.

## IBIS Model

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0.40V	-13.726p	-635.953p	-9.300p
0.50V	-10.963p	-578.437p	-6.968p
0.60V	-8.203p	-521.365p	-4.637p
0.70V	-5.446p	-464.595p	-2.307p
0.80V	-2.691p	-408.039p	22.980f
0.90V	62.079f	-351.636p	2.353p
1.10V	5.566p	-239.133p	7.011p
1.20V	8.316p	-182.975p	9.340p
1.30V	11.067p	-126.851p	11.669p
1.40V	13.817p	-70.743p	13.998p
1.50V	16.567p	-14.634p	16.327p
1.60V	19.317p	41.493p	18.656p
1.70V	22.067p	97.654p	20.985p
1.80V	24.817p	153.868p	23.313p
1.90V	27.568p	210.159p	25.642p
2.10V	33.072p	323.083p	30.300p
2.20V	35.825p	379.789p	32.629p
2.30V	38.581p	436.650p	34.958p
2.40V	41.339p	492.867p	37.288p
2.50V	44.098p	547.026p	39.618p
2.60V	46.849p	600.695p	41.948p
2.70V	49.356p	654.682p	44.279p
2.80V	51.378p	709.650p	46.611p
2.90V	53.315p	776.122p	48.939p
3.10V	57.193p	4.552n	52.772p
3.20V	59.183p	44.522n	54.319p
3.30V	62.959p	466.732n	55.861p

[POWER\_clamp]

Voltage	I(typ)	I(min)	I(max)
3.30V	-26.215p	-450.005n	-11.632p
3.40V	-74.463p	-4.632u	-13.966p
3.50V	-1.269n	-41.964u	-16.303p
3.60V	-27.994n	-336.317u	-18.737p
3.70V	-580.051n	-3.014m	-27.092p
3.80V	-10.789u	-14.886m	-311.158p
3.90V	-116.521u	-40.029m	-11.484n
4.10V	-2.837m	-120.248m	-13.420u
4.20V	-17.375m	-166.582m	-201.636u
4.30V	-60.888m	-214.579m	-1.195m
4.40V	-130.668m	-263.597m	-3.451m
4.50V	-212.028m	-313.301m	-8.803m
4.60V	-298.248m	-363.494m	-37.420m
4.70V	-386.980m	-414.052m	-107.496m
4.80V	-477.221m	-464.892m	-200.187m
4.90V	-568.461m	-515.958m	-300.867m
5.10V	-752.887m	-618.610m	-511.430m
5.20V	-845.771m	-670.140m	-618.970m
5.30V	-938.979m	-721.779m	-727.373m
5.40V	-1.032	-773.514m	-836.403m
5.50V	-1.126	-825.330m	-945.908m

**Freescale Semiconductor, Inc.****IBIS Model**

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5.60V      -1.220 -877.220m    -1.056
5.70V      -1.314 -929.174m    -1.166
5.80V      -1.408 -981.185m    -1.276
5.90V      -1.503   -1.033    -1.387
6.10V      -1.691   -1.138    -1.609
6.20V      -1.786   -1.190    -1.720
6.30V      -1.881   -1.242    -1.831
6.40V      -1.975   -1.294    -1.942
6.50V      -2.070   -1.346    -2.054
6.60V      -2.165   -1.399    -2.165
|
[Ramp]
|Voltage      I(typ)      I(min)      I(max)
|
dV/dt_f     2.00/112.556p 1.82/199.937p 2.17/74.356p
|
dV/dt_r     2.02/146.245p 1.84/252.851p 2.20/93.872p
R_load=10000ohms
|R_load was connected to ground for Ramp_up test and power for Ramp_dn
test
|
|End model
[Model]          ipadni_io           |   "
Model_type      I/O
Vinl = 0.8
Vinh = 2
| variable      typ      min      max
C_comp          2.01p    1.89p    2.17p
| variable      typ      min      max
[Temperature Range] 40.0      0.0      120.0
| variable      typ      min      max
[Voltage Range]   3.30V    3.00V    3.60V
|
[Pulldown]
| pulldown in the table = pulldown subtract gnd_clamp
|Voltage      I(typ)      I(min)      I(max)
|
-3.30V      -157.134u  -99.256u  -219.000u
-3.20V      -165.037u  -104.127u  -230.250u
-3.10V      -173.749u  -109.479u  -242.685u
-3.00V      -183.400u  -115.386u  -256.500u
-2.90V      -194.148u  -121.936u  -271.934u
-2.80V      -206.189u  -129.240u  -289.286u
-2.70V      -219.766u  -137.431u  -308.933u
-2.60V      -235.190u  -146.680u  -331.355u
-2.50V      -252.856u  -157.199u  -357.176u
-2.40V      -273.283u  -169.265u  -387.219u
-2.30V      -297.162u  -183.236u  -422.595u
-2.20V      -325.427u  -199.590u  -464.837u
-2.10V      -359.384u  -218.976u  -516.117u
-2.00V      -400.901u  -242.299u  -579.623u
-1.90V      -452.750u  -270.851u  -660.217u
-1.80V      -519.217u  -306.549u  -765.681u

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# Freescale Semiconductor, Inc.

## IBIS Model

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-1.70V	-607.277u	-352.346u	-909.270u
-1.60V	-729.045u	-413.024u	-1.115m
-1.50V	-907.407u	-496.811u	-1.434m
-1.40V	-1.191m	-619.011u	-1.987m
-1.30V	-1.699m	-811.079u	-3.133m
-1.20V	-2.799m	-1.146m	-6.243m
-1.10V	-5.689m	-1.822m	-12.974m
-1.00V	-10.416m	-3.302m	-17.948m
-0.90V	-12.342m	-5.449m	-17.964m
-0.80V	-11.672m	-6.479m	-16.692m
-0.70V	-10.528m	-6.146m	-15.152m
-0.60V	-9.204m	-5.387m	-13.338m
-0.50V	-7.770m	-4.535m	-11.313m
-0.40V	-6.286m	-3.652m	-9.190m
-0.30V	-4.766m	-2.754m	-6.999m
-0.20V	-3.214m	-1.846m	-4.740m
-0.10V	-1.627m	-928.990u	-2.410m
0.00V	32.755e-18	18.548e-18	-1.607f
0.10V	1.604m	910.814u	2.391m
0.20V	3.124m	1.775m	4.661m
0.30V	4.566m	2.595m	6.817m
0.40V	5.928m	3.372m	8.858m
0.50V	7.210m	4.105m	10.784m
0.60V	8.411m	4.792m	12.593m
0.70V	9.529m	5.432m	14.284m
0.80V	10.562m	6.023m	15.855m
0.90V	11.508m	6.563m	17.306m
1.00V	12.367m	7.051m	18.639m
1.10V	13.138m	7.486m	19.856m
1.20V	13.821m	7.865m	20.957m
1.30V	14.417m	8.189m	21.944m
1.40V	14.930m	47.725m	22.817m
1.50V	86.564m	48.943m	23.575m
1.60V	88.497m	49.908m	136.139m
1.70V	89.946m	50.637m	138.902m
1.80V	90.974m	51.160m	140.954m
1.90V	91.689m	51.534m	142.415m
2.00V	92.200m	51.810m	143.449m
2.10V	92.586m	52.024m	144.201m
2.20V	92.895m	52.201m	144.779m
2.30V	93.154m	52.351m	145.246m
2.40V	93.380m	52.482m	145.642m
2.50V	93.581m	52.600m	145.990m
2.60V	93.764m	52.706m	146.303m
2.70V	93.931m	52.804m	146.590m
2.80V	94.087m	52.895m	146.855m
2.90V	94.233m	52.980m	147.104m
3.00V	94.370m	53.060m	147.338m
3.10V	94.500m	53.135m	147.560m
3.20V	94.624m	53.207m	147.772m
3.30V	94.744m	53.276m	147.976m
3.40V	94.859m	53.343m	148.174m
3.50V	94.974m	53.408m	148.367m

3.60V	95.089m	53.475m	148.560m
3.70V	95.208m	53.543m	148.757m
3.80V	95.336m	53.617m	148.963m
3.90V	95.478m	53.699m	149.186m
4.00V	95.641m	53.792m	149.436m
4.10V	95.833m	53.902m	149.725m
4.20V	96.065m	54.035m	150.067m
4.30V	96.347m	54.196m	150.479m
4.40V	96.693m	54.394m	150.981m
4.50V	97.117m	54.635m	151.594m
4.60V	97.636m	54.930m	152.342m
4.70V	98.266m	55.287m	153.252m
4.80V	99.024m	55.716m	154.350m
4.90V	99.931m	56.227m	155.666m
5.00V	101.005m	56.831m	157.230m
5.10V	102.264m	57.539m	159.070m
5.20V	103.730m	58.361m	161.218m
5.30V	105.422m	59.308m	163.704m
5.40V	107.357m	60.391m	166.555m
5.50V	109.556m	61.618m	169.801m
5.60V	112.034m	63.000m	173.468m
5.70V	114.809m	64.545m	177.581m
5.80V	117.897m	66.263m	182.163m
5.90V	121.311m	68.160m	187.235m
6.00V	125.066m	70.245m	192.816m
6.10V	129.172m	72.524m	198.924m
6.20V	133.642m	75.002m	205.573m
6.30V	138.485m	77.685m	212.776m
6.40V	143.709m	80.578m	220.544m
6.50V	149.320m	83.683m	228.885m
6.60V	155.326m	87.004m	237.805m
[Pullup]			
pullup in the table = pullup subtract power_clamp			
Voltage	I(typ)	I(min)	I(max)
-3.30V	132.979u	100.794u	170.075u
-3.20V	138.984u	105.115u	178.000u
-3.10V	145.559u	109.825u	186.702u
-3.00V	152.789u	114.981u	196.300u
-2.90V	160.778u	120.648u	206.941u
-2.80V	169.651u	126.906u	218.803u
-2.70V	179.562u	133.852u	232.110u
-2.60V	190.706u	141.605u	247.141u
-2.50V	203.326u	150.317u	264.253u
-2.40V	217.736u	160.174u	283.910u
-2.30V	234.344u	171.418u	306.723u
-2.20V	253.692u	184.362u	333.513u
-2.10V	276.513u	199.421u	365.415u
-2.00V	303.830u	217.155u	404.033u
-1.90V	337.102u	238.340u	451.722u
-1.80V	378.494u	264.081u	512.067u
-1.70V	431.351u	296.004u	590.810u

# Freescale Semiconductor, Inc.

## IBIS Model

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-1.60V	501.113u	336.601u	697.730u
-1.50V	597.240u	389.880u	850.877u
-1.40V	737.641u	462.700u	1.087m
-1.30V	960.396u	567.748u	1.497m
-1.20V	1.361m	731.012u	2.348m
-1.10V	2.237m	1.013m	4.712m
-1.00V	4.644m	1.583m	10.148m
-0.90V	8.090m	2.907m	12.062m
-0.80V	8.032m	4.727m	11.029m
-0.70V	7.118m	4.754m	9.778m
-0.60V	6.128m	4.128m	8.443m
-0.50V	5.109m	3.441m	7.052m
-0.40V	4.082m	2.746m	5.644m
-0.30V	3.056m	2.053m	4.233m
-0.20V	2.033m	1.363m	2.821m
-0.10V	1.014m	678.856u	1.410m
-0.00V	58.687e-18	58.622e-18	117.504e-18
0.10V	-987.106u	-655.604u	-1.381m
0.20V	-1.928m	-1.274m	-2.709m
0.30V	-2.828m	-1.859m	-3.988m
0.40V	-3.685m	-2.412m	-5.216m
0.50V	-4.499m	-2.931m	-6.392m
0.60V	-5.269m	-3.416m	-7.516m
0.70V	-5.994m	-3.866m	-8.587m
0.80V	-6.673m	-4.280m	-9.602m
0.90V	-7.306m	-4.658m	-10.561m
1.00V	-7.890m	-4.999m	-11.461m
1.10V	-8.424m	-5.301m	-12.302m
1.20V	-8.907m	-5.563m	-13.081m
1.30V	-9.339m	-47.451m	-13.901m
1.40V	-79.705m	-48.954m	-118.519m
1.50V	-82.391m	-50.187m	-123.324m
1.60V	-84.713m	-51.203m	-127.640m
1.70V	-86.724m	-52.057m	-131.501m
1.80V	-88.472m	-52.794m	-134.939m
1.90V	-89.996m	-53.442m	-137.982m
2.00V	-91.327m	-54.017m	-140.655m
2.10V	-92.489m	-54.533m	-142.987m
2.20V	-93.511m	-54.999m	-145.014m
2.30V	-94.415m	-55.424m	-146.781m
2.40V	-95.224m	-55.814m	-148.333m
2.50V	-95.955m	-56.174m	-149.709m
2.60V	-96.623m	-56.510m	-150.943m
2.70V	-97.238m	-56.824m	-152.063m
2.80V	-97.809m	-57.119m	-153.088m
2.90V	-98.343m	-57.398m	-154.036m
3.00V	-98.846m	-57.662m	-154.920m
3.10V	-99.320m	-57.913m	-155.749m
3.20V	-99.770m	-58.152m	-156.531m
3.30V	-100.198m	-58.381m	-157.272m
3.40V	-100.607m	-58.601m	-157.977m
3.50V	-100.998m	-58.812m	-158.650m
3.60V	-101.374m	-59.015m	-159.295m

**Freescale Semiconductor, Inc.****IBIS Model**

3.70V	-101.735m	-59.211m	-159.914m
3.80V	-102.084m	-59.401m	-160.510m
3.90V	-102.422m	-59.585m	-161.086m
4.00V	-102.750m	-59.766m	-161.644m
4.10V	-103.070m	-59.942m	-162.186m
4.20V	-103.384m	-60.117m	-162.715m
4.30V	-103.694m	-60.291m	-163.234m
4.40V	-104.002m	-60.467m	-163.747m
4.50V	-104.313m	-60.647m	-164.257m
4.60V	-104.629m	-60.832m	-164.770m
4.70V	-104.955m	-61.027m	-165.293m
4.80V	-105.296m	-61.234m	-165.831m
4.90V	-105.659m	-61.459m	-166.394m
5.00V	-106.050m	-61.704m	-166.991m
5.10V	-106.477m	-61.975m	-167.634m
5.20V	-106.949m	-62.278m	-168.334m
5.30V	-107.474m	-62.619m	-169.106m
5.40V	-108.064m	-63.003m	-169.965m
5.50V	-108.730m	-63.439m	-170.928m
5.60V	-109.483m	-63.932m	-172.012m
5.70V	-110.337m	-64.492m	-173.239m
5.80V	-111.305m	-65.126m	-174.627m
5.90V	-112.401m	-65.843m	-176.199m
6.00V	-113.640m	-66.651m	-177.978m
6.10V	-115.036m	-67.560m	-179.986m
6.20V	-116.606m	-68.578m	-182.247m
6.30V	-118.365m	-69.715m	-184.785m
6.40V	-120.329m	-70.981m	-187.626m
6.50V	-122.513m	-72.384m	-190.793m
6.60V	-124.935m	-73.935m	-194.311m
[GND_clamp]			
Voltage	I(typ)	I(min)	I(max)
-3.30V	-2.165	-1.242	-2.500
-3.20V	-2.070	-1.190	-2.388
-3.10V	-1.975	-1.138	-2.277
-2.90V	-1.786	-1.033	-2.054
-2.80V	-1.691	-981.185m	-1.942
-2.70V	-1.597	-929.174m	-1.831
-2.60V	-1.503	-877.220m	-1.720
-2.50V	-1.408	-825.330m	-1.609
-2.40V	-1.314	-773.514m	-1.498
-2.30V	-1.220	-721.779m	-1.387
-2.20V	-1.126	-670.140m	-1.276
-2.10V	-1.032	-618.610m	-1.166
-1.90V	-845.771m	-515.958m	-945.908m
-1.80V	-752.887m	-464.892m	-836.403m
-1.70V	-660.410m	-414.052m	-727.373m
-1.60V	-568.461m	-363.494m	-618.970m
-1.50V	-477.221m	-313.301m	-511.430m
-1.40V	-386.980m	-263.597m	-405.149m

# Freescale Semiconductor, Inc.

## IBIS Model

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-1.30V	-298.248m	-214.579m	-300.867m
-1.20V	-212.028m	-166.582m	-200.187m
-1.10V	-130.668m	-120.248m	-107.496m
-0.90V	-17.375m	-40.029m	-8.803m
-0.80V	-2.837m	-14.886m	-3.451m
-0.70V	-656.331u	-3.014m	-1.195m
-0.60V	-116.521u	-336.317u	-201.636u
-0.50V	-10.789u	-41.964u	-13.420u
-0.40V	-580.051n	-4.632u	-416.799n
-0.30V	-27.994n	-450.005n	-11.484n
-0.20V	-1.269n	-41.862n	-311.158p
-0.10V	-74.463p	-4.218n	-27.092p
0.00V	-26.215p	-1.078n	-18.737p
0.10V	-22.114p	-826.325p	-16.303p
0.20V	-19.278p	-754.146p	-13.966p
0.30V	-16.497p	-694.188p	-11.632p
0.40V	-13.726p	-635.953p	-9.300p
0.50V	-10.963p	-578.437p	-6.968p
0.60V	-8.203p	-521.365p	-4.637p
0.70V	-5.446p	-464.595p	-2.307p
0.80V	-2.691p	-408.039p	22.980f
0.90V	62.079f	-351.636p	2.353p
1.10V	5.566p	-239.133p	7.011p
1.20V	8.316p	-182.975p	9.340p
1.30V	11.067p	-126.851p	11.669p
1.40V	13.817p	-70.743p	13.998p
1.50V	16.567p	-14.634p	16.327p
1.60V	19.317p	41.493p	18.656p
1.70V	22.067p	97.654p	20.985p
1.80V	24.817p	153.868p	23.313p
1.90V	27.568p	210.159p	25.642p
2.10V	33.072p	323.083p	30.300p
2.20V	35.825p	379.789p	32.629p
2.30V	38.581p	436.650p	34.958p
2.40V	41.339p	492.867p	37.288p
2.50V	44.098p	547.026p	39.618p
2.60V	46.849p	600.695p	41.948p
2.70V	49.356p	654.682p	44.279p
2.80V	51.378p	709.650p	46.611p
2.90V	53.315p	776.122p	48.939p
3.10V	57.193p	4.552n	52.772p
3.20V	59.183p	44.522n	54.319p
3.30V	62.959p	466.732n	55.861p
<hr/>			
[POWER_clamp]			
<hr/>			
Voltage	I(typ)	I(min)	I(max)
<hr/>			
3.30V	-26.215p	-450.005n	-11.632p
3.40V	-74.463p	-4.632u	-13.966p
3.50V	-1.269n	-41.964u	-16.303p
3.60V	-27.994n	-336.317u	-18.737p
3.70V	-580.051n	-3.014m	-27.092p

**Freescale Semiconductor, Inc.****IBIS Model**

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3.80V      -10.789u  -14.886m -311.158p
3.90V      -116.521u  -40.029m  -11.484n
4.10V       -2.837m  -120.248m  -13.420u
4.20V      -17.375m  -166.582m  -201.636u
4.30V      -60.888m  -214.579m   -1.195m
4.40V      -130.668m  -263.597m   -3.451m
4.50V      -212.028m  -313.301m   -8.803m
4.60V      -298.248m  -363.494m  -37.420m
4.70V      -386.980m  -414.052m  -107.496m
4.80V      -477.221m  -464.892m  -200.187m
4.90V      -568.461m  -515.958m  -300.867m
5.10V      -752.887m  -618.610m  -511.430m
5.20V      -845.771m  -670.140m  -618.970m
5.30V      -938.979m  -721.779m  -727.373m
5.40V       -1.032   -773.514m  -836.403m
5.50V       -1.126   -825.330m  -945.908m
5.60V       -1.220   -877.220m   -1.056
5.70V       -1.314   -929.174m   -1.166
5.80V       -1.408   -981.185m   -1.276
5.90V       -1.503     -1.033    -1.387
6.10V       -1.691     -1.138    -1.609
6.20V       -1.786     -1.190    -1.720
6.30V       -1.881     -1.242    -1.831
6.40V       -1.975     -1.294    -1.942
6.50V       -2.070     -1.346    -2.054
6.60V       -2.165     -1.399    -2.165
|
[Ramp]
|Voltage      I(typ)      I(min)      I(max)
|
dV/dt_f     2.00/113.266p 1.82/197.371p 2.17/74.028p
|
dV/dt_r     2.02/147.014p 1.84/251.849p 2.20/93.411p
R_load=10000ohms
|R_load was connected to ground for Ramp_up test and power for Ramp_dn
test
|
|End model
[Model]          ipado_3st           |   "
Model_type      3-state
| variable      typ        min        max
C_comp          1.99p     1.86p     2.15p
| variable      typ        min        max
[Temperature Range] 40.0      0.0      120.0
| variable      typ        min        max
[Voltage Range]  3.30V     3.00V     3.60V
|
[Pulldown]
| pulldown in the table = pulldown subtract gnd_clamp
|Voltage      I(typ)      I(min)      I(max)
|
-3.30V      -157.134u  -99.256u -219.000u
-3.20V      -165.037u  -104.127u -230.250u

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# Freescale Semiconductor, Inc.

## IBIS Model

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-3.10V	-173.749u	-109.479u	-242.685u
-3.00V	-183.400u	-115.386u	-256.500u
-2.90V	-194.148u	-121.936u	-271.934u
-2.80V	-206.189u	-129.240u	-289.286u
-2.70V	-219.766u	-137.431u	-308.933u
-2.60V	-235.190u	-146.680u	-331.355u
-2.50V	-252.856u	-157.199u	-357.176u
-2.40V	-273.283u	-169.265u	-387.219u
-2.30V	-297.162u	-183.236u	-422.595u
-2.20V	-325.427u	-199.590u	-464.837u
-2.10V	-359.384u	-218.976u	-516.117u
-2.00V	-400.901u	-242.299u	-579.623u
-1.90V	-452.750u	-270.851u	-660.217u
-1.80V	-519.217u	-306.549u	-765.681u
-1.70V	-607.277u	-352.346u	-909.270u
-1.60V	-729.045u	-413.024u	-1.115m
-1.50V	-907.407u	-496.811u	-1.434m
-1.40V	-1.191m	-619.011u	-1.987m
-1.30V	-1.699m	-811.079u	-3.133m
-1.20V	-2.799m	-1.146m	-6.243m
-1.10V	-5.689m	-1.822m	-12.974m
-1.00V	-10.416m	-3.302m	-17.948m
-0.90V	-12.342m	-5.449m	-17.964m
-0.80V	-11.672m	-6.479m	-16.692m
-0.70V	-10.528m	-6.146m	-15.152m
-0.60V	-9.204m	-5.387m	-13.338m
-0.50V	-7.770m	-4.535m	-11.313m
-0.40V	-6.286m	-3.652m	-9.190m
-0.30V	-4.766m	-2.754m	-6.999m
-0.20V	-3.214m	-1.846m	-4.740m
-0.10V	-1.627m	-928.990u	-2.410m
0.00V	32.755e-18	18.548e-18	-1.607f
0.10V	1.604m	910.814u	2.391m
0.20V	3.124m	1.775m	4.661m
0.30V	4.566m	2.595m	6.817m
0.40V	5.928m	3.372m	8.858m
0.50V	7.210m	4.105m	10.784m
0.60V	8.411m	4.792m	12.593m
0.70V	9.529m	5.432m	14.284m
0.80V	10.562m	6.023m	15.855m
0.90V	11.508m	6.563m	17.306m
1.00V	12.367m	7.051m	18.639m
1.10V	13.138m	7.486m	19.856m
1.20V	13.821m	7.865m	20.957m
1.30V	14.417m	8.189m	21.944m
1.40V	14.930m	47.725m	22.817m
1.50V	86.564m	48.943m	23.575m
1.60V	88.497m	49.908m	136.139m
1.70V	89.946m	50.637m	138.902m
1.80V	90.974m	51.160m	140.954m
1.90V	91.689m	51.534m	142.415m
2.00V	92.200m	51.810m	143.449m
2.10V	92.586m	52.024m	144.201m

# Freescale Semiconductor, Inc.

IBIS Model

Freescale Semiconductor, Inc.

Voltage	I(typ)	I(min)	I(max)
2.20V	92.895m	52.201m	144.779m
2.30V	93.154m	52.351m	145.246m
2.40V	93.380m	52.482m	145.642m
2.50V	93.581m	52.600m	145.990m
2.60V	93.764m	52.706m	146.303m
2.70V	93.931m	52.804m	146.590m
2.80V	94.087m	52.895m	146.855m
2.90V	94.233m	52.980m	147.104m
3.00V	94.370m	53.060m	147.338m
3.10V	94.500m	53.135m	147.560m
3.20V	94.624m	53.207m	147.772m
3.30V	94.744m	53.276m	147.976m
3.40V	94.859m	53.343m	148.174m
3.50V	94.974m	53.408m	148.367m
3.60V	95.089m	53.475m	148.560m
3.70V	95.208m	53.543m	148.757m
3.80V	95.336m	53.617m	148.963m
3.90V	95.478m	53.699m	149.186m
4.00V	95.641m	53.792m	149.436m
4.10V	95.833m	53.902m	149.725m
4.20V	96.065m	54.035m	150.067m
4.30V	96.347m	54.196m	150.479m
4.40V	96.693m	54.394m	150.981m
4.50V	97.117m	54.635m	151.594m
4.60V	97.636m	54.930m	152.342m
4.70V	98.266m	55.287m	153.252m
4.80V	99.024m	55.716m	154.350m
4.90V	99.931m	56.227m	155.666m
5.00V	101.005m	56.831m	157.230m
5.10V	102.264m	57.539m	159.070m
5.20V	103.730m	58.361m	161.218m
5.30V	105.422m	59.308m	163.704m
5.40V	107.357m	60.391m	166.555m
5.50V	109.556m	61.618m	169.801m
5.60V	112.034m	63.000m	173.468m
5.70V	114.809m	64.545m	177.581m
5.80V	117.897m	66.263m	182.163m
5.90V	121.311m	68.160m	187.235m
6.00V	125.066m	70.245m	192.816m
6.10V	129.172m	72.524m	198.924m
6.20V	133.642m	75.002m	205.573m
6.30V	138.485m	77.685m	212.776m
6.40V	143.709m	80.578m	220.544m
6.50V	149.320m	83.683m	228.885m
6.60V	155.326m	87.004m	237.805m
[Pullup]			
pullup in the table = pullup subtract power_clamp			
Voltage	I(typ)	I(min)	I(max)
-3.30V	132.979u	100.794u	170.075u
-3.20V	138.984u	105.115u	178.000u
-3.10V	145.559u	109.825u	186.702u

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-3.00V	152.789u	114.981u	196.300u
-2.90V	160.778u	120.648u	206.941u
-2.80V	169.651u	126.906u	218.803u
-2.70V	179.562u	133.852u	232.110u
-2.60V	190.706u	141.605u	247.141u
-2.50V	203.326u	150.317u	264.253u
-2.40V	217.736u	160.174u	283.910u
-2.30V	234.344u	171.418u	306.723u
-2.20V	253.692u	184.362u	333.513u
-2.10V	276.513u	199.421u	365.415u
-2.00V	303.830u	217.155u	404.033u
-1.90V	337.102u	238.340u	451.722u
-1.80V	378.494u	264.081u	512.067u
-1.70V	431.351u	296.004u	590.810u
-1.60V	501.113u	336.601u	697.730u
-1.50V	597.240u	389.880u	850.877u
-1.40V	737.641u	462.700u	1.087m
-1.30V	960.396u	567.748u	1.497m
-1.20V	1.361m	731.012u	2.348m
-1.10V	2.237m	1.013m	4.712m
-1.00V	4.644m	1.583m	10.148m
-0.90V	8.090m	2.907m	12.062m
-0.80V	8.032m	4.727m	11.029m
-0.70V	7.118m	4.754m	9.778m
-0.60V	6.128m	4.128m	8.443m
-0.50V	5.109m	3.441m	7.052m
-0.40V	4.082m	2.746m	5.644m
-0.30V	3.056m	2.053m	4.233m
-0.20V	2.033m	1.363m	2.821m
-0.10V	1.014m	678.856u	1.410m
-0.00V	58.687e-18	58.622e-18	117.504e-18
0.10V	-987.106u	-655.604u	-1.381m
0.20V	-1.928m	-1.274m	-2.709m
0.30V	-2.828m	-1.859m	-3.988m
0.40V	-3.685m	-2.412m	-5.216m
0.50V	-4.499m	-2.931m	-6.392m
0.60V	-5.269m	-3.416m	-7.516m
0.70V	-5.994m	-3.866m	-8.587m
0.80V	-6.673m	-4.280m	-9.602m
0.90V	-7.306m	-4.658m	-10.561m
1.00V	-7.890m	-4.999m	-11.461m
1.10V	-8.424m	-5.301m	-12.302m
1.20V	-8.907m	-5.563m	-13.081m
1.30V	-9.339m	-47.451m	-13.837m
1.40V	-79.705m	-48.954m	-118.519m
1.50V	-82.391m	-50.187m	-123.324m
1.60V	-84.713m	-51.203m	-127.640m
1.70V	-86.724m	-52.057m	-131.501m
1.80V	-88.472m	-52.794m	-134.939m
1.90V	-89.996m	-53.442m	-137.982m
2.00V	-91.327m	-54.017m	-140.655m
2.10V	-92.489m	-54.533m	-142.987m
2.20V	-93.511m	-54.999m	-145.014m

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2.30V	-94.415m	-55.424m	-146.781m
2.40V	-95.224m	-55.814m	-148.333m
2.50V	-95.955m	-56.174m	-149.709m
2.60V	-96.623m	-56.510m	-150.943m
2.70V	-97.238m	-56.824m	-152.063m
2.80V	-97.809m	-57.119m	-153.088m
2.90V	-98.343m	-57.398m	-154.036m
3.00V	-98.846m	-57.662m	-154.920m
3.10V	-99.320m	-57.913m	-155.749m
3.20V	-99.770m	-58.152m	-156.531m
3.30V	-100.198m	-58.381m	-157.272m
3.40V	-100.607m	-58.601m	-157.977m
3.50V	-100.998m	-58.812m	-158.650m
3.60V	-101.374m	-59.015m	-159.295m
3.70V	-101.735m	-59.211m	-159.914m
3.80V	-102.084m	-59.401m	-160.510m
3.90V	-102.422m	-59.585m	-161.086m
4.00V	-102.750m	-59.766m	-161.644m
4.10V	-103.070m	-59.942m	-162.186m
4.20V	-103.384m	-60.117m	-162.715m
4.30V	-103.694m	-60.291m	-163.234m
4.40V	-104.002m	-60.467m	-163.747m
4.50V	-104.313m	-60.647m	-164.257m
4.60V	-104.629m	-60.832m	-164.770m
4.70V	-104.955m	-61.027m	-165.293m
4.80V	-105.296m	-61.234m	-165.831m
4.90V	-105.659m	-61.459m	-166.394m
5.00V	-106.050m	-61.704m	-166.991m
5.10V	-106.477m	-61.975m	-167.634m
5.20V	-106.949m	-62.278m	-168.334m
5.30V	-107.474m	-62.619m	-169.106m
5.40V	-108.064m	-63.003m	-169.965m
5.50V	-108.730m	-63.439m	-170.928m
5.60V	-109.483m	-63.932m	-172.012m
5.70V	-110.337m	-64.492m	-173.239m
5.80V	-111.305m	-65.126m	-174.627m
5.90V	-112.401m	-65.843m	-176.199m
6.00V	-113.640m	-66.651m	-177.978m
6.10V	-115.036m	-67.560m	-179.986m
6.20V	-116.606m	-68.578m	-182.247m
6.30V	-118.365m	-69.715m	-184.785m
6.40V	-120.329m	-70.981m	-187.626m
6.50V	-122.513m	-72.384m	-190.793m
6.60V	-124.935m	-73.935m	-194.311m
[GND_clamp]			
Voltage	I(typ)	I(min)	I(max)
-3.30V	-2.165	-1.242	-2.500
-3.20V	-2.070	-1.190	-2.388
-3.10V	-1.975	-1.138	-2.277
-2.90V	-1.786	-1.033	-2.054

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-2.80V	-1.691	-981.185m	-1.942
-2.70V	-1.597	-929.174m	-1.831
-2.60V	-1.503	-877.220m	-1.720
-2.50V	-1.408	-825.330m	-1.609
-2.40V	-1.314	-773.514m	-1.498
-2.30V	-1.220	-721.779m	-1.387
-2.20V	-1.126	-670.140m	-1.276
-2.10V	-1.032	-618.610m	-1.166
-1.90V	-845.771m	-515.958m	-945.908m
-1.80V	-752.887m	-464.892m	-836.403m
-1.70V	-660.410m	-414.052m	-727.373m
-1.60V	-568.461m	-363.494m	-618.970m
-1.50V	-477.221m	-313.301m	-511.430m
-1.40V	-386.980m	-263.597m	-405.149m
-1.30V	-298.248m	-214.579m	-300.867m
-1.20V	-212.028m	-166.582m	-200.187m
-1.10V	-130.668m	-120.248m	-107.496m
-0.90V	-17.375m	-40.029m	-8.803m
-0.80V	-2.837m	-14.886m	-3.451m
-0.70V	-656.331u	-3.014m	-1.195m
-0.60V	-116.521u	-336.317u	-201.636u
-0.50V	-10.789u	-41.964u	-13.420u
-0.40V	-580.051n	-4.632u	-416.799n
-0.30V	-27.994n	-450.005n	-11.484n
-0.20V	-1.269n	-41.862n	-311.158p
-0.10V	-74.463p	-4.218n	-27.092p
0.00V	-26.215p	-1.078n	-18.737p
0.10V	-22.114p	-826.325p	-16.303p
0.20V	-19.278p	-754.146p	-13.966p
0.30V	-16.497p	-694.188p	-11.632p
0.40V	-13.726p	-635.953p	-9.300p
0.50V	-10.963p	-578.437p	-6.968p
0.60V	-8.203p	-521.365p	-4.637p
0.70V	-5.446p	-464.595p	-2.307p
0.80V	-2.691p	-408.039p	22.980f
0.90V	62.079f	-351.636p	2.353p
1.10V	5.566p	-239.133p	7.011p
1.20V	8.316p	-182.975p	9.340p
1.30V	11.067p	-126.851p	11.669p
1.40V	13.817p	-70.743p	13.998p
1.50V	16.567p	-14.634p	16.327p
1.60V	19.317p	41.493p	18.656p
1.70V	22.067p	97.654p	20.985p
1.80V	24.817p	153.868p	23.313p
1.90V	27.568p	210.159p	25.642p
2.10V	33.072p	323.083p	30.300p
2.20V	35.825p	379.789p	32.629p
2.30V	38.581p	436.650p	34.958p
2.40V	41.339p	492.867p	37.288p
2.50V	44.098p	547.026p	39.618p
2.60V	46.849p	600.695p	41.948p
2.70V	49.356p	654.682p	44.279p
2.80V	51.378p	709.650p	46.611p

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```

2.90V      53.315p  776.122p  48.939p
3.10V      57.193p   4.552n   52.772p
3.20V      59.183p   44.522n  54.319p
3.30V      62.959p   466.732n 55.861p
|
[POWER_clamp]
|
|Voltage    I(typ)     I(min)     I(max)
|
3.30V      -26.215p  -450.005n  -11.632p
3.40V      -74.463p   -4.632u   -13.966p
3.50V      -1.269n   -41.964u  -16.303p
3.60V      -27.994n  -336.317u  -18.737p
3.70V      -580.051n  -3.014m  -27.092p
3.80V      -10.789u  -14.886m  -311.158p
3.90V      -116.521u  -40.029m  -11.484n
4.10V      -2.837m   -120.248m  -13.420u
4.20V      -17.375m  -166.582m -201.636u
4.30V      -60.888m  -214.579m  -1.195m
4.40V      -130.668m -263.597m  -3.451m
4.50V      -212.028m -313.301m  -8.803m
4.60V      -298.248m -363.494m -37.420m
4.70V      -386.980m -414.052m -107.496m
4.80V      -477.221m -464.892m -200.187m
4.90V      -568.461m -515.958m -300.867m
5.10V      -752.887m -618.610m -511.430m
5.20V      -845.771m -670.140m -618.970m
5.30V      -938.979m -721.779m -727.373m
5.40V      -1.032   -773.514m -836.403m
5.50V      -1.126   -825.330m -945.908m
5.60V      -1.220   -877.220m  -1.056
5.70V      -1.314   -929.174m  -1.166
5.80V      -1.408   -981.185m  -1.276
5.90V      -1.503   -1.033    -1.387
6.10V      -1.691   -1.138    -1.609
6.20V      -1.786   -1.190    -1.720
6.30V      -1.881   -1.242    -1.831
6.40V      -1.975   -1.294    -1.942
6.50V      -2.070   -1.346    -2.054
6.60V      -2.165   -1.399    -2.165
|
[Ramp]
|Voltage    I(typ)     I(min)     I(max)
|
dV/dt_f    1.99/130.331p 1.81/220.000p 2.17/83.712p
|
dV/dt_r    2.03/153.657p 1.84/260.814p 2.20/92.663p
R_load=10000ohms
|R_load was connected to ground for Ramp_up test and power for Ramp_dn
test
|
|End model
[End]

```

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